

Rethinking Memory System Design (for Data-Intensive Computing)

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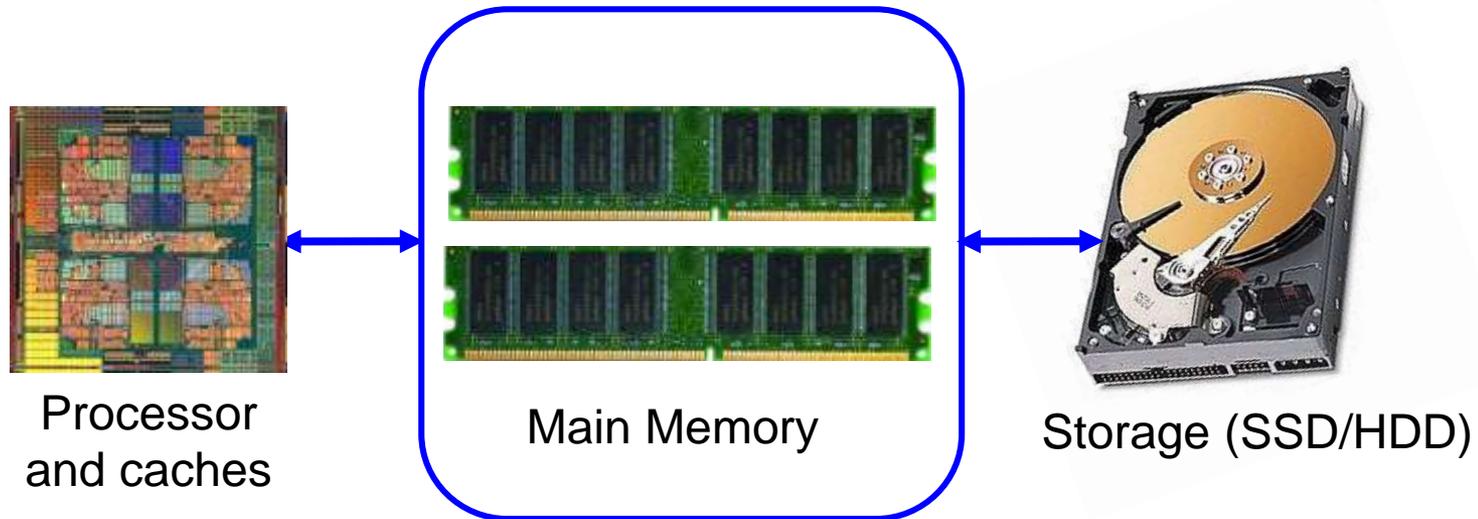
<http://users.ece.cmu.edu/~omutlu/>

October 21, 2015

SBAC-PAD 2015 Keynote

Carnegie Mellon

The Main Memory System



- **Main memory is a critical component of all computing systems:** server, mobile, embedded, desktop, sensor
- **Main memory system must scale** (in *size, technology, efficiency, cost, and management algorithms*) to maintain performance growth and technology scaling benefits

State of the Main Memory System

- Recent technology, architecture, and application trends
 - lead to new requirements
 - exacerbate old requirements
- DRAM and memory controllers, as we know them today, are (will be) unlikely to satisfy all requirements
- Some emerging non-volatile memory technologies (e.g., PCM) enable new opportunities: memory+storage merging
- We need to rethink the main memory system
 - to fix DRAM issues and enable emerging technologies
 - to satisfy all requirements

Agenda

- Major Trends Affecting Main Memory
- The Memory Scaling Problem and Solution Directions
 - New Memory Architectures
 - Enabling Emerging Technologies
- How Can We Do Better?
- Summary

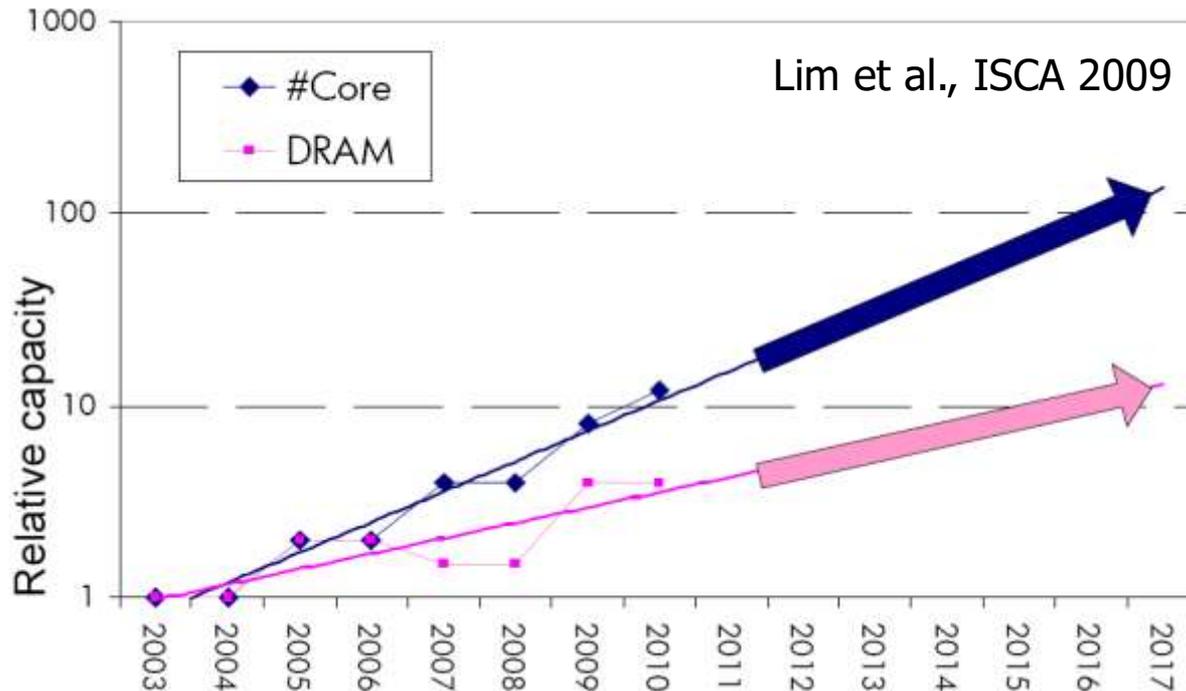
Major Trends Affecting Main Memory (I)

- Need for main memory capacity, bandwidth, QoS increasing
- Main memory energy/power is a key system design concern
- DRAM technology scaling is ending

Example: The Memory Capacity Gap

Core count doubling ~ every 2 years

DRAM DIMM capacity doubling ~ every 3 years



- *Memory capacity per core* expected to drop by 30% every two years
- Trends worse for *memory bandwidth per core*!

Major Trends Affecting Main Memory (III)

- Need for main memory capacity, bandwidth, QoS increasing
- Main memory energy/power is a key system design concern
 - ~40-50% energy spent in off-chip memory hierarchy [Lefurgy, IEEE Computer 2003]
 - DRAM consumes power even when not used (periodic refresh)
- DRAM technology scaling is ending

Major Trends Affecting Main Memory (IV)

- Need for main memory capacity, bandwidth, QoS increasing

- Main memory energy/power is a key system design concern

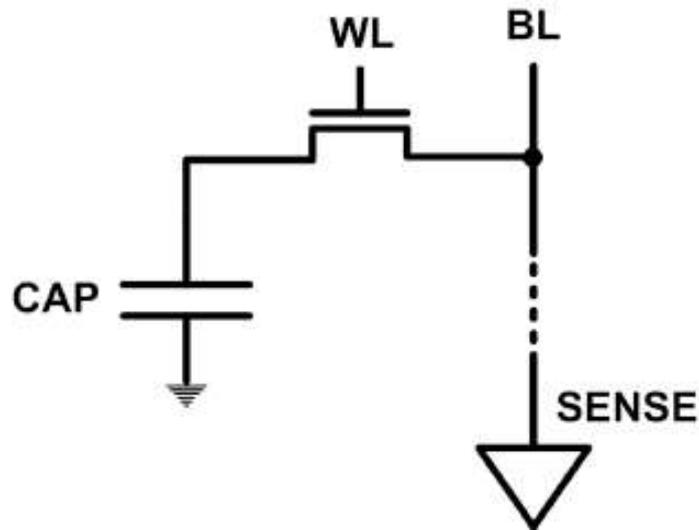
- DRAM technology scaling is ending
 - ITRS projects DRAM will not scale easily below X nm
 - Scaling has provided many benefits:
 - higher capacity (density), lower cost, lower energy

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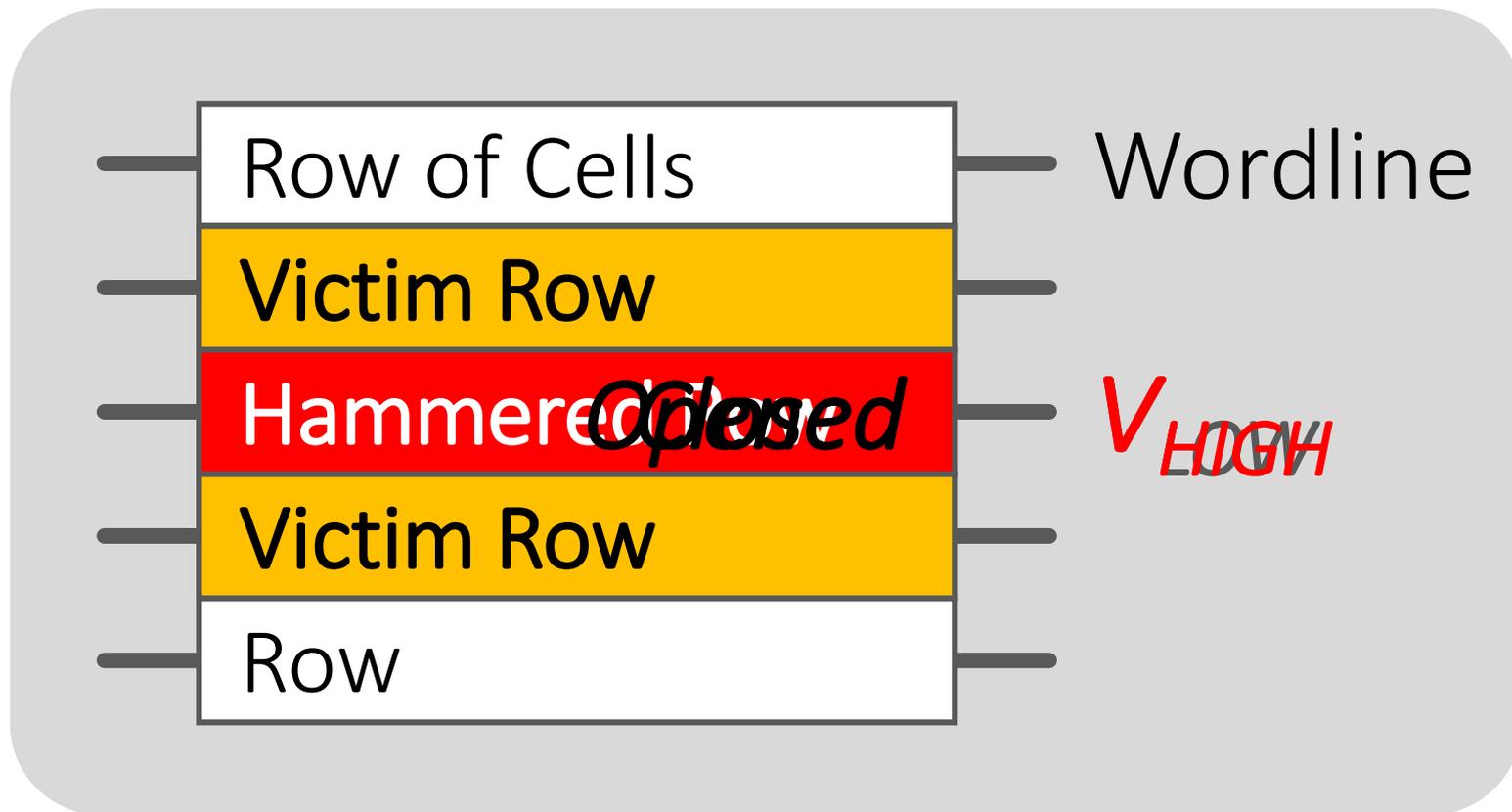
The DRAM Scaling Problem

- DRAM stores charge in a capacitor (charge-based memory)
 - Capacitor must be large enough for reliable sensing
 - Access transistor should be large enough for low leakage and high retention time
 - Scaling beyond 40-35nm (2013) is challenging [ITRS, 2009]



- DRAM capacity, cost, and energy/power hard to scale

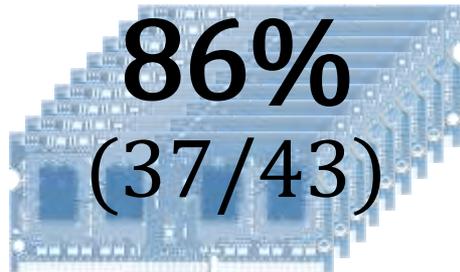
An Example of the DRAM Scaling Problem



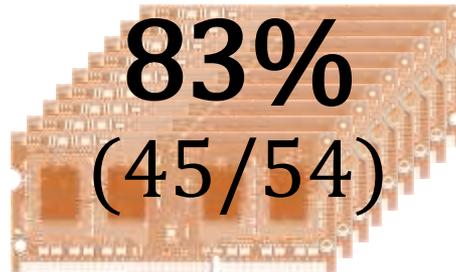
Repeatedly opening and closing a row enough times within a refresh interval induces **disturbance errors** in adjacent rows in **most real DRAM chips you can buy today**

Most DRAM Modules Are at Risk

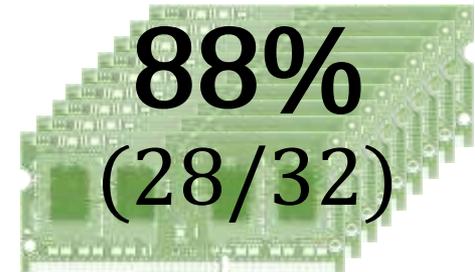
A company



B company



C company

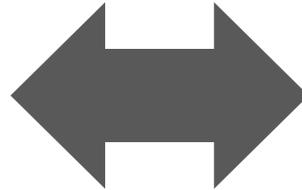


Up to
 1.0×10^7
errors

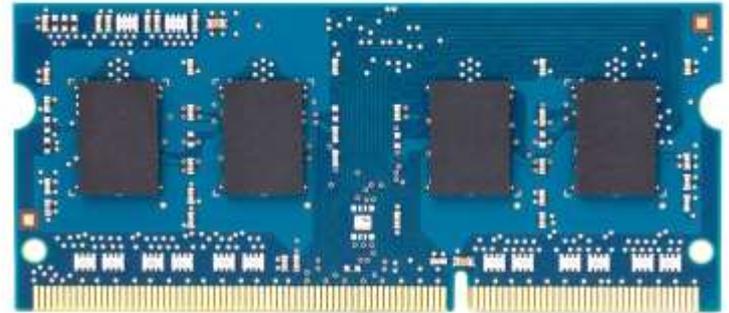
Up to
 2.7×10^6
errors

Up to
 3.3×10^5
errors

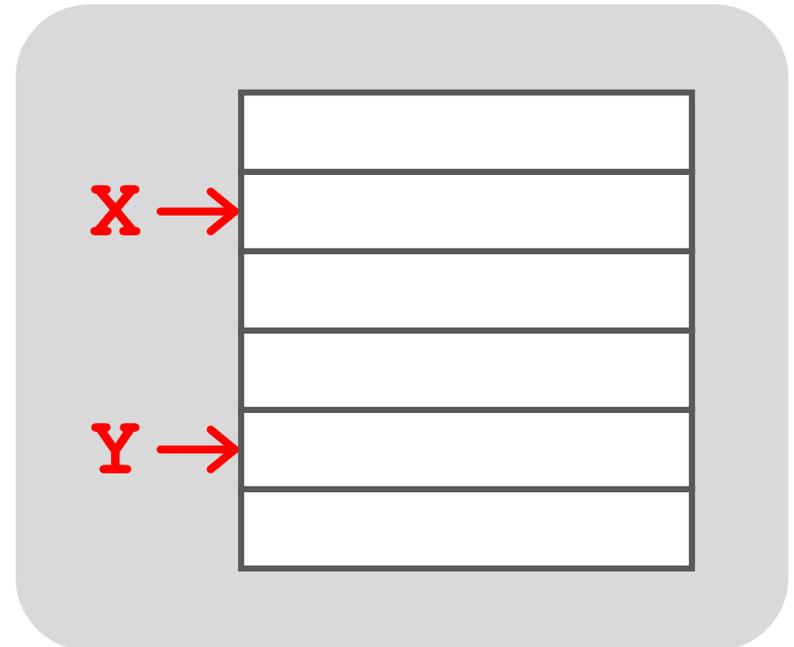
x86 CPU



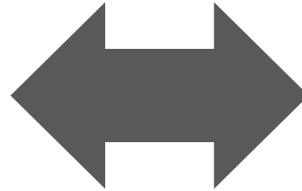
DRAM Module



```
loop:  
  mov (X), %eax  
  mov (Y), %ebx  
  clflush (X)  
  clflush (Y)  
  mfence  
  jmp loop
```



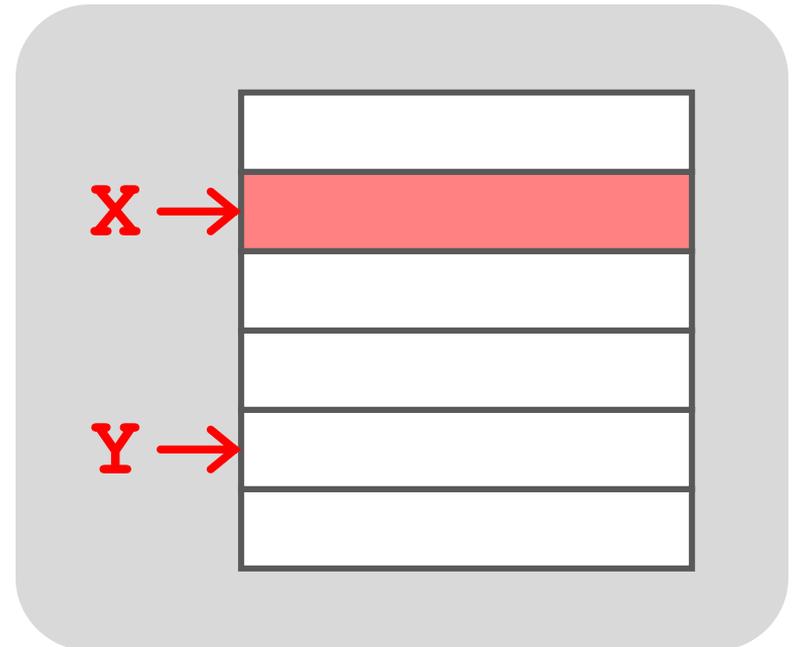
x86 CPU



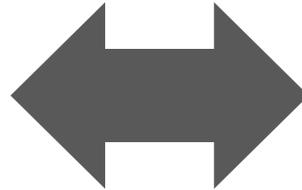
DRAM Module



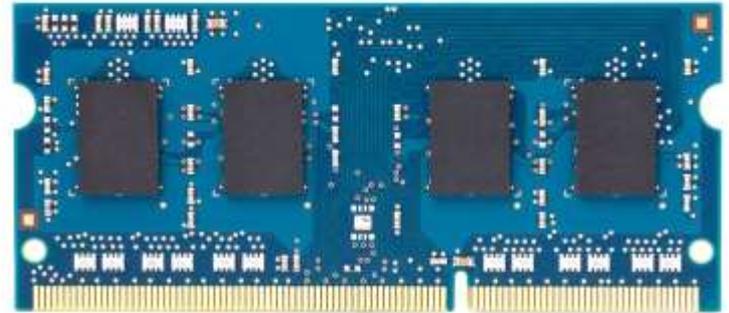
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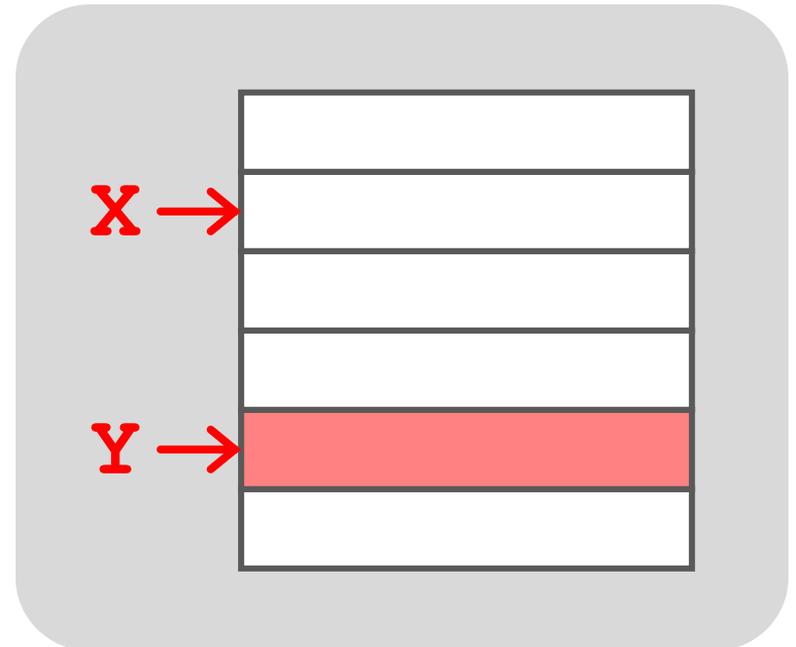
x86 CPU



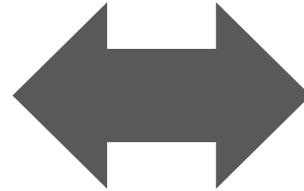
DRAM Module



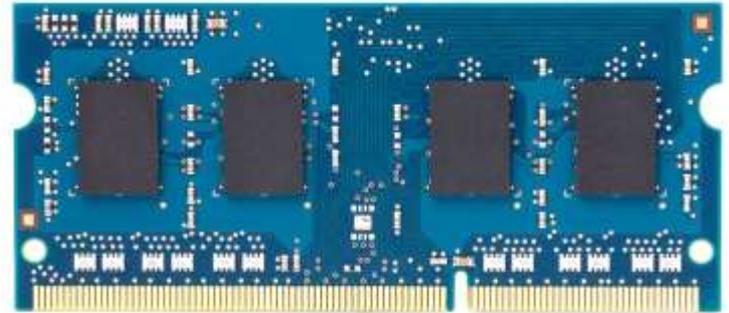
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  clflush (Y)  
  mfence  
  jmp  loop
```



x86 CPU



DRAM Module



```
loop:
```

```
  mov (X), %eax
```

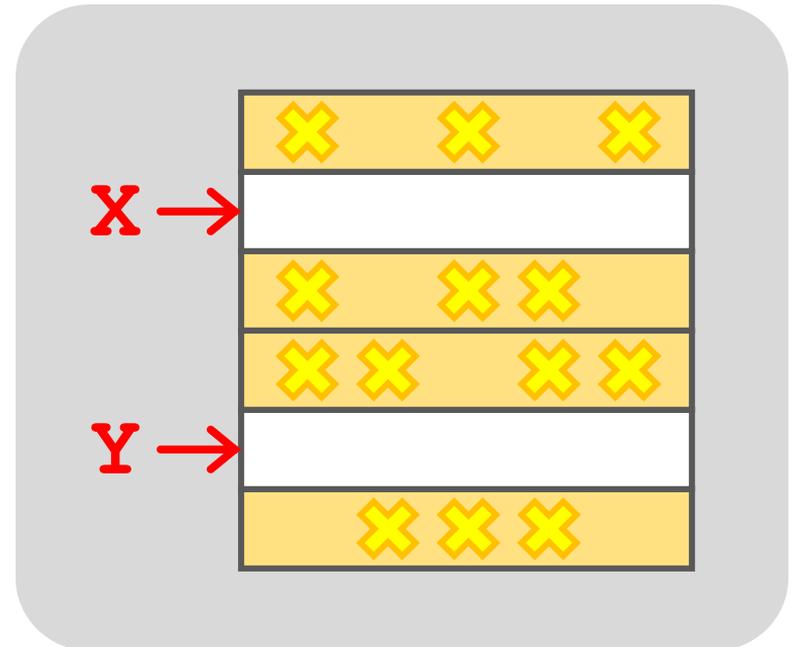
```
  mov (Y), %ebx
```

```
  clflush (X)
```

```
  clflush (Y)
```

```
  mfence
```

```
  jmp loop
```

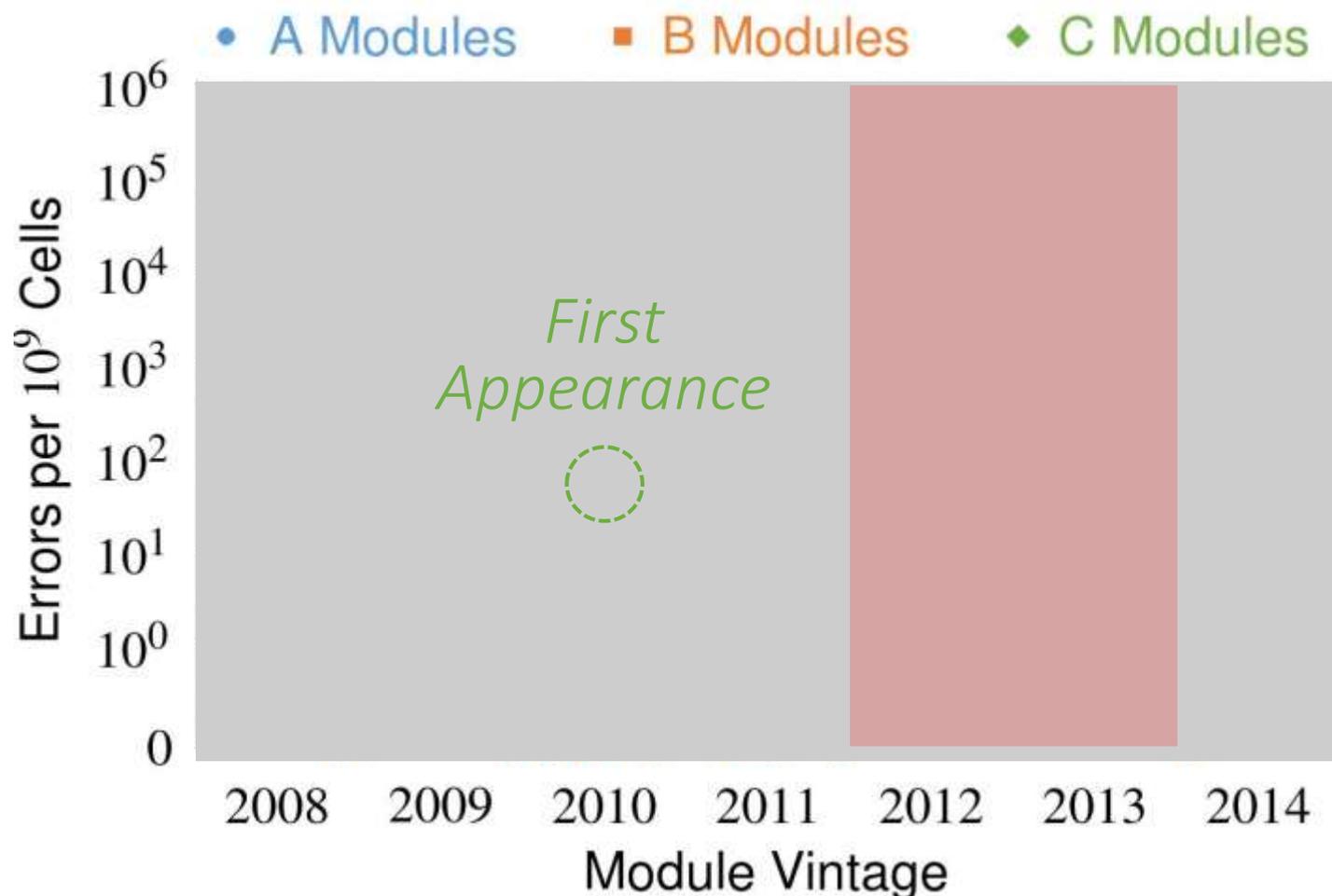


Observed Errors in Real Systems

CPU Architecture	Errors	Access-Rate
Intel Haswell (2013)	22.9K	12.3M/sec
Intel Ivy Bridge (2012)	20.7K	11.7M/sec
Intel Sandy Bridge (2011)	16.1K	11.6M/sec
AMD Piledriver (2012)	59	6.1M/sec

- *A real reliability & security issue*
- *In a more controlled environment, we can induce as many as **ten million** disturbance errors*

Errors *vs.* Vintage



All modules from 2012-2013 are vulnerable

Experimental DRAM Testing Infrastructure



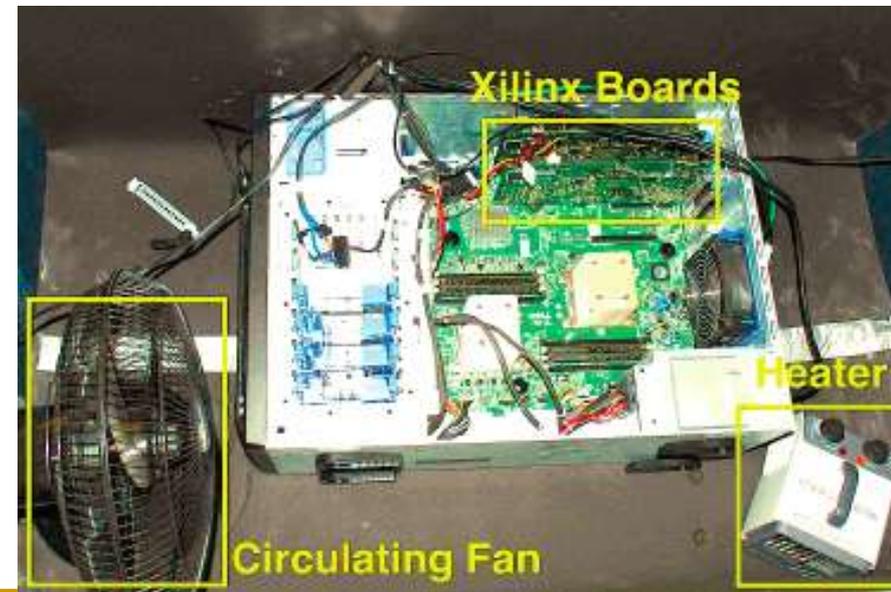
An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms (Liu et al., ISCA 2013)

The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study (Khan et al., SIGMETRICS 2014)

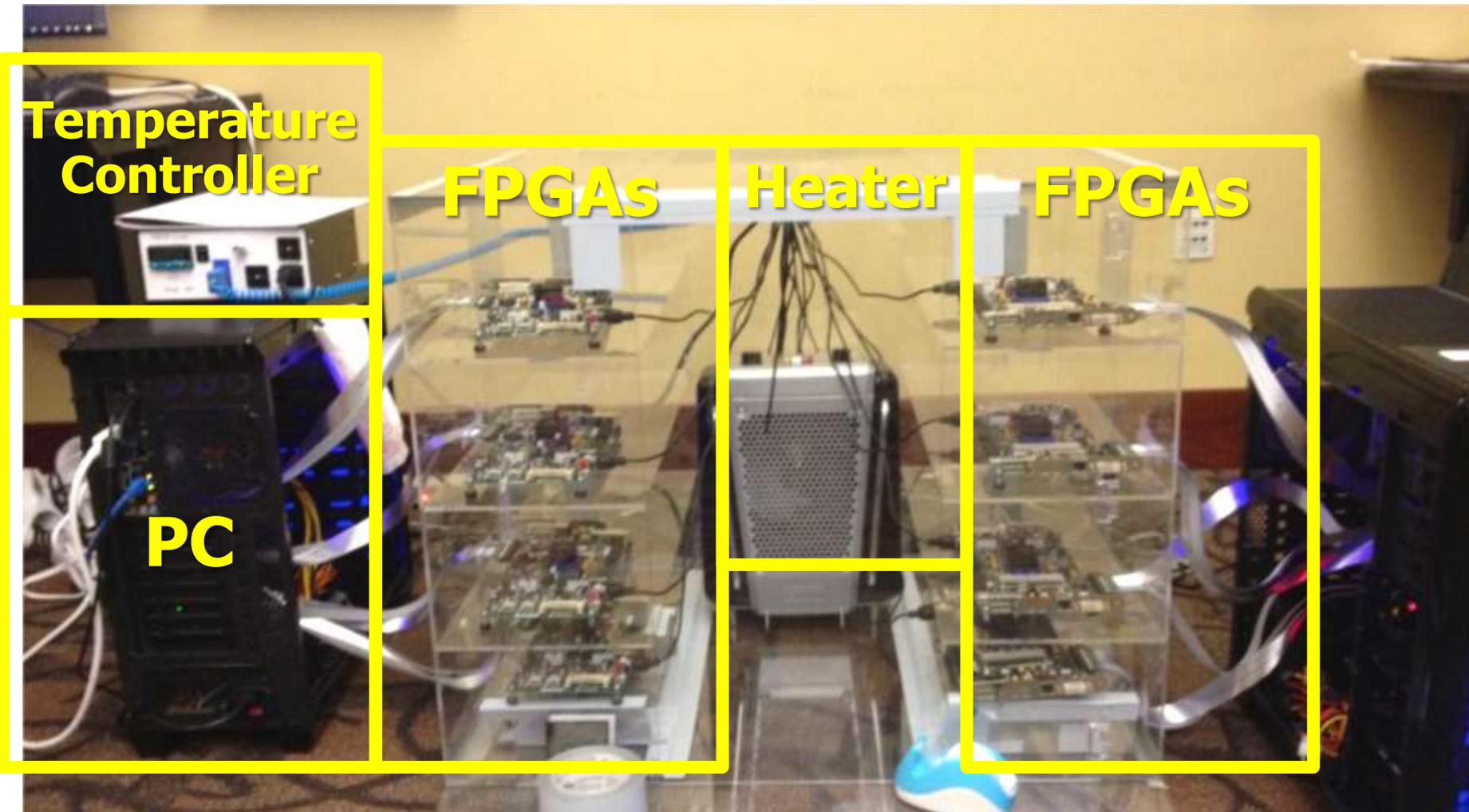
Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)

Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case (Lee et al., HPCA 2015)

AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems (Qureshi et al., DSN 2015)



Experimental Infrastructure (DRAM)



RowHammer Characterization Results

1. Most Modules Are at Risk
2. Errors vs. Vintage
3. Error = Charge Loss
4. Adjacency: Aggressor & Victim
5. Sensitivity Studies
6. Other Results in Paper
7. Solution Space

One Can Take Over an Otherwise-Secure System

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors

Abstract. Memory isolation is a key property of a reliable and secure computing system — an access to one memory address should not have unintended side effects on data stored in other addresses. However, as DRAM process technology

Project Zero

[Flipping Bits in Memory Without Accessing Them:
An Experimental Study of DRAM Disturbance Errors](#)
(Kim et al., ISCA 2014)

News and updates from the Project Zero team at Google

[Exploiting the DRAM rowhammer bug to
gain kernel privileges](#) (Seaborn, 2015)

Monday, March 9, 2015

Exploiting the DRAM rowhammer bug to gain kernel privileges

RowHammer Security Attack Example

- “Rowhammer” is a problem with some recent DRAM devices in which repeatedly accessing a row of memory can cause bit flips in adjacent rows (Kim et al., ISCA 2014).
 - Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)
- We tested a selection of laptops and found that a subset of them exhibited the problem.
- We built two working privilege escalation exploits that use this effect.
 - Exploiting the DRAM rowhammer bug to gain kernel privileges (Seaborn, 2015)
- One exploit uses rowhammer-induced bit flips to gain kernel privileges on x86-64 Linux when run as an unprivileged userland process.
- When run on a machine vulnerable to the rowhammer problem, the process was able to induce bit flips in page table entries (PTEs).
- It was able to use this to gain write access to its own page table, and hence gain read-write access to all of physical memory.

Security Implications



It's like breaking into an apartment by repeatedly slamming a neighbor's door until the vibrations open the door you were after

Recap: The DRAM Scaling Problem

DRAM Process Scaling Challenges

❖ Refresh

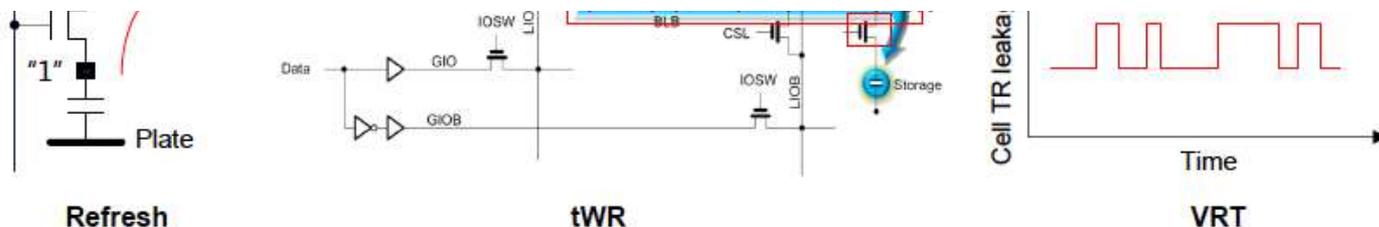
- Difficult to build high-aspect ratio cell capacitors decreasing cell capacitance

THE MEMORY FORUM 2014

Co-Architecting Controllers and DRAM to Enhance DRAM Process Scaling

Uksong Kang, Hak-soo Yu, Churoo Park, *Hongzhong Zheng,
**John Halbert, **Kuljit Bains, SeongJin Jang, and Joo Sun Choi

*Samsung Electronics, Hwasung, Korea / *Samsung Electronics, San Jose / **Intel*



How Do We Solve The Problem?

- **Fix it:** Make DRAM and controllers more intelligent
 - **New interfaces, architectures:** system-DRAM codesign
 - **Eliminate or minimize it:** Replace or (more likely) augment DRAM with a different technology
 - **New technologies and storage**
 - **Embrace it:** Design heterogeneous memories (none of which are perfect) and map applications across them
 - **New models for data management and maybe usage**
-
- Problems
Algorithms
Programs
- User
- Runtime System (VM, OS, MM)
ISA
Microarchitecture
Logic
Devices

Solutions (to memory scaling) require software/hardware/device cooperation

Solution 1: Fix DRAM

- Overcome DRAM shortcomings with
 - ❑ System-DRAM co-design
 - ❑ Novel DRAM architectures, interface, functions
 - ❑ Better waste management (efficient utilization)

- Key issues to tackle
 - ❑ Enable reliability at low cost
 - ❑ Reduce energy
 - ❑ Improve latency and bandwidth
 - ❑ Reduce waste (capacity, bandwidth, latency)
 - ❑ Enable computation close to data

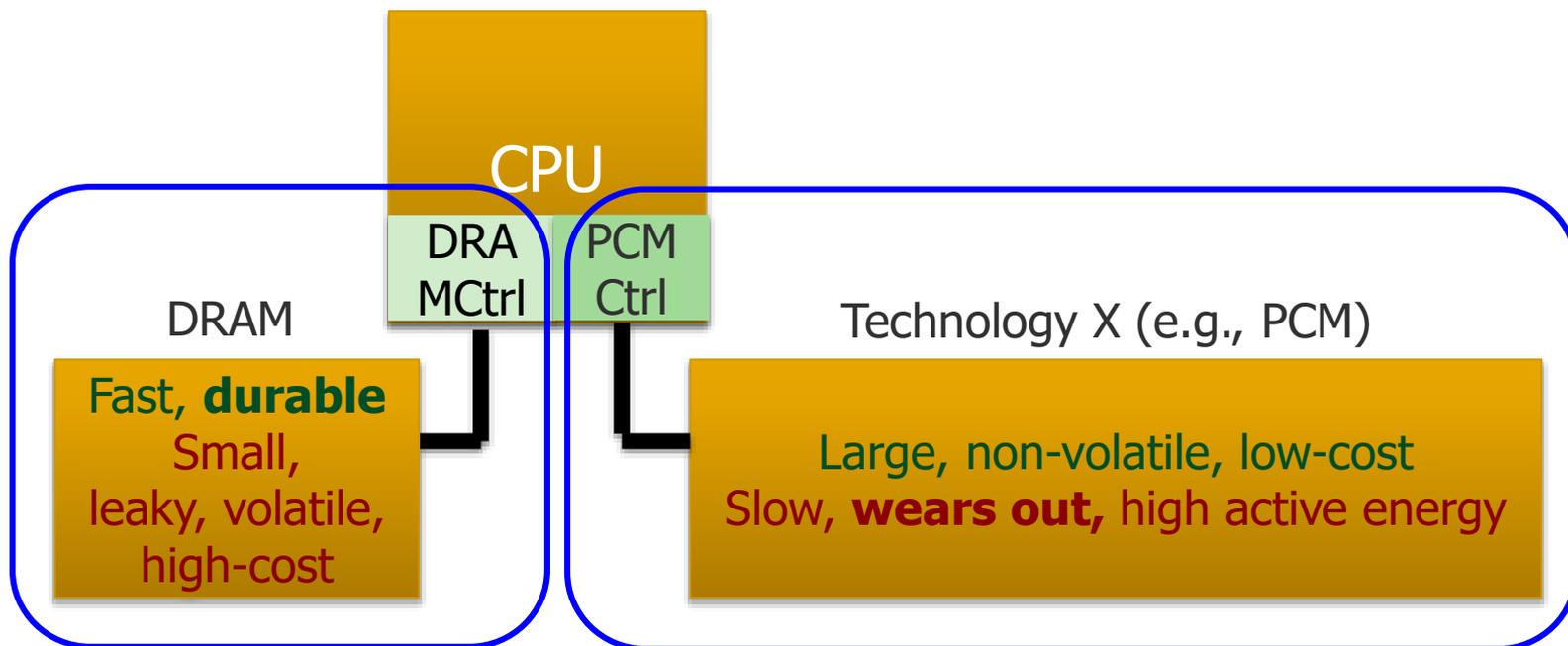
Solution 1: Fix DRAM

- Liu+, "RAIDR: Retention-Aware Intelligent DRAM Refresh," ISCA 2012.
 - Kim+, "A Case for Exploiting Subarray-Level Parallelism in DRAM," ISCA 2012.
 - Lee+, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," HPCA 2013.
 - Liu+, "An Experimental Study of Data Retention Behavior in Modern DRAM Devices," ISCA 2013.
 - Seshadri+, "RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data," MICRO 2013.
 - Pekhimenko+, "Linearly Compressed Pages: A Main Memory Compression Framework," MICRO 2013.
 - Chang+, "Improving DRAM Performance by Parallelizing Refreshes with Accesses," HPCA 2014.
 - Khan+, "The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study," SIGMETRICS 2014.
 - Luo+, "Characterizing Application Memory Error Vulnerability to Optimize Data Center Cost," DSN 2014.
 - Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.
 - Lee+, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," HPCA 2015.
 - Qureshi+, "AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems," DSN 2015.
 - Meza+, "Revisiting Memory Errors in Large-Scale Production Data Centers: Analysis and Modeling of New Trends from the Field," DSN 2015.
 - Kim+, "Ramulator: A Fast and Extensible DRAM Simulator," IEEE CAL 2015.
 - Seshadri+, "Fast Bulk Bitwise AND and OR in DRAM," IEEE CAL 2015.
 - Ahn+, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing," ISCA 2015.
 - Ahn+, "PIM-Enabled Instructions: A Low-Overhead, Locality-Aware Processing-in-Memory Architecture," ISCA 2015.
 - Lee+, "Decoupled Direct Memory Access: Isolating CPU and IO Traffic by Leveraging a Dual-Data-Port DRAM," PACT 2015.
 - Seshadri+, "Gather-Scatter DRAM: In-DRAM Address Translation to Improve the Spatial Locality of Non-unit Strided Accesses," MICRO 2015.
 - Avoid DRAM:
 - Seshadri+, "The Evicted-Address Filter: A Unified Mechanism to Address Both Cache Pollution and Thrashing," PACT 2012.
 - Pekhimenko+, "Base-Delta-Immediate Compression: Practical Data Compression for On-Chip Caches," PACT 2012.
 - Seshadri+, "The Dirty-Block Index," ISCA 2014.
 - Pekhimenko+, "Exploiting Compressed Block Size as an Indicator of Future Reuse," HPCA 2015.
 - Vijaykumar+, "A Case for Core-Assisted Bottleneck Acceleration in GPUs: Enabling Flexible Data Compression with Assist Warps," ISCA 2015.
-

Solution 2: Emerging Memory Technologies

- Some emerging resistive memory technologies seem more scalable than DRAM (and they are non-volatile)
- Example: Phase Change Memory
 - Expected to scale to 9nm (2022 [ITRS])
 - Expected to be denser than DRAM: can store multiple bits/cell
- But, emerging technologies have shortcomings as well
 - **Can they be enabled to replace/augment/surpass DRAM?**
- Lee+, "Architecting Phase Change Memory as a Scalable DRAM Alternative," ISCA'09, CACM'10, Micro'10.
- Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters 2012.
- Yoon, Meza+, "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012.
- Kultursay+, "Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative," ISPASS 2013.
- Meza+, "A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory," WEED 2013.
- Lu+, "Loose Ordering Consistency for Persistent Memory," ICCD 2014.
- Zhao+, "FIRM: Fair and High-Performance Memory Control for Persistent Memory Systems," MICRO 2014.
- Yoon, Meza+, "Efficient Data Mapping and Buffering Techniques for Multi-Level Cell Phase-Change Memories," ACM TACO 2014.
- Ren+, "Dual-Scheme Checkpointing: A Software-Transparent Mechanism for Supporting Crash Consistency in Persistent Memory Systems," MICRO 2015.

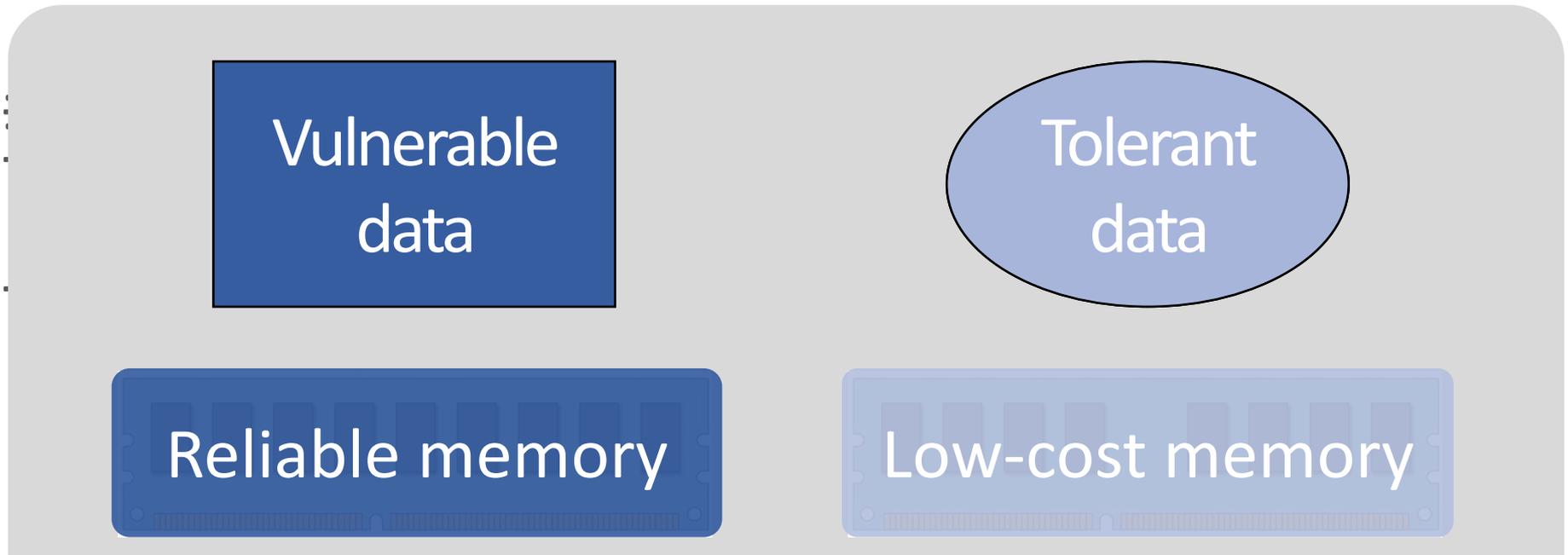
Solution 3: Hybrid Memory Systems



Hardware/software manage data allocation and movement
to achieve the best of multiple technologies

Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters, 2012.
Yoon, Meza et al., "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012 Best Paper Award.

Exploiting Memory Error Tolerance with Hybrid Memory Systems



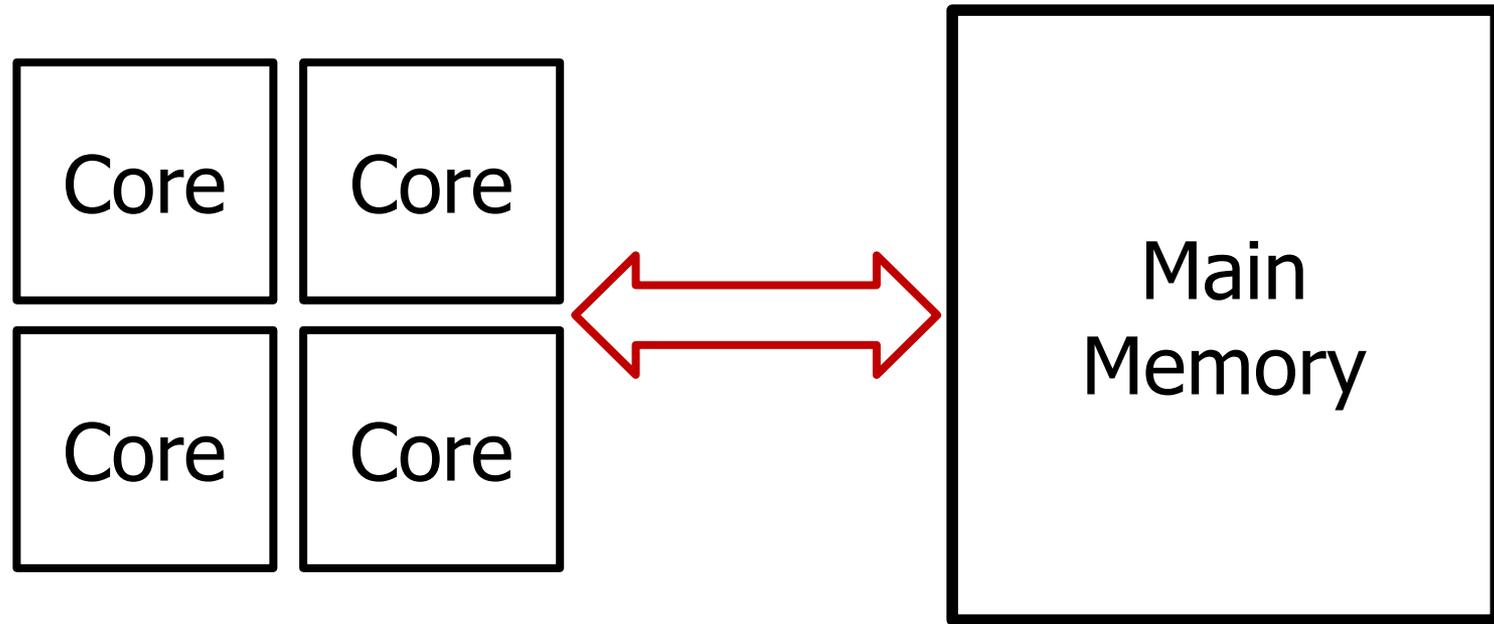
On Microsoft's Web Search workload

Reduces server hardware **cost** by **4.7 %**

Achieves single server **availability** target of **99.90 %**

Heterogeneous-Reliability Memory [DSN 2014]

An Orthogonal Issue: Memory Interference

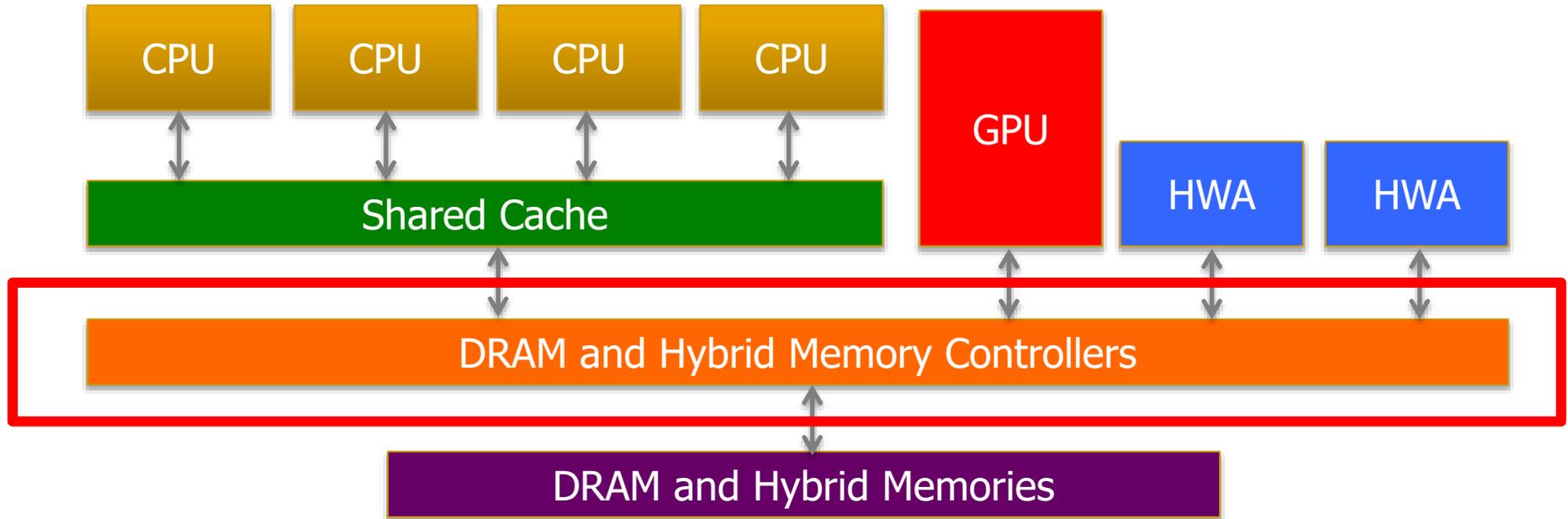


Cores' interfere with each other when accessing shared main memory

An Orthogonal Issue: Memory Interference

- Problem: **Memory interference between cores is uncontrolled**
 - unfairness, starvation, low performance
 - **uncontrollable, unpredictable, vulnerable system**
- Solution: **QoS-Aware Memory Systems**
 - Hardware designed to provide a configurable fairness substrate
 - Application-aware memory scheduling, partitioning, throttling
 - Software designed to configure the resources to satisfy different QoS goals
- QoS-aware memory systems can provide predictable performance and higher efficiency

Goal: Predictable Performance in Complex Systems



- Heterogeneous agents: CPUs, GPUs, and HWAs
- Main memory interference between CPUs, GPUs, HWAs

How to allocate resources to heterogeneous agents to mitigate interference and provide predictable performance?

Strong Memory Service Guarantees

- Goal: **Satisfy performance/SLA requirements** in the presence of shared main memory, heterogeneous agents, and hybrid memory/storage
- Approach:
 - Develop techniques/models to accurately **estimate** the **performance loss** of an application/agent in the presence of resource sharing
 - Develop mechanisms (hardware and software) to **enable** the **resource partitioning/prioritization** needed to achieve the required performance levels for all applications
 - All the while providing **high system performance**
- Subramanian et al., “**MISE: Providing Performance Predictability and Improving Fairness in Shared Main Memory Systems**,” HPCA 2013.
- Subramanian et al., “**The Application Slowdown Model**,” MICRO 2015.

Some Promising Directions

- **New memory architectures**

- Rethinking DRAM and flash memory
- **A lot of hope in fixing DRAM**

- **Enabling emerging NVM technologies**

- Hybrid memory systems
- Single-level memory and storage
- **A lot of hope in hybrid memory systems and single-level stores**

- **System-level memory/storage QoS**

- **A lot of hope in designing a predictable system**

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- The Memory Scaling Problem and Solution Directions
 - [New Memory Architectures](#)
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- How Can We Do Better?
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Rethinking DRAM

- In-Memory Computation
- Refresh
- Reliability
- Latency
- Bandwidth
- Energy
- Memory Compression

Why In-Memory Computation Today?

- **Push from Technology**

- **DRAM Scaling at jeopardy**

- Controllers close to DRAM

- Industry open to new memory architectures

- **Pull from Systems and Applications**

- **Data access is a major system and application bottleneck**

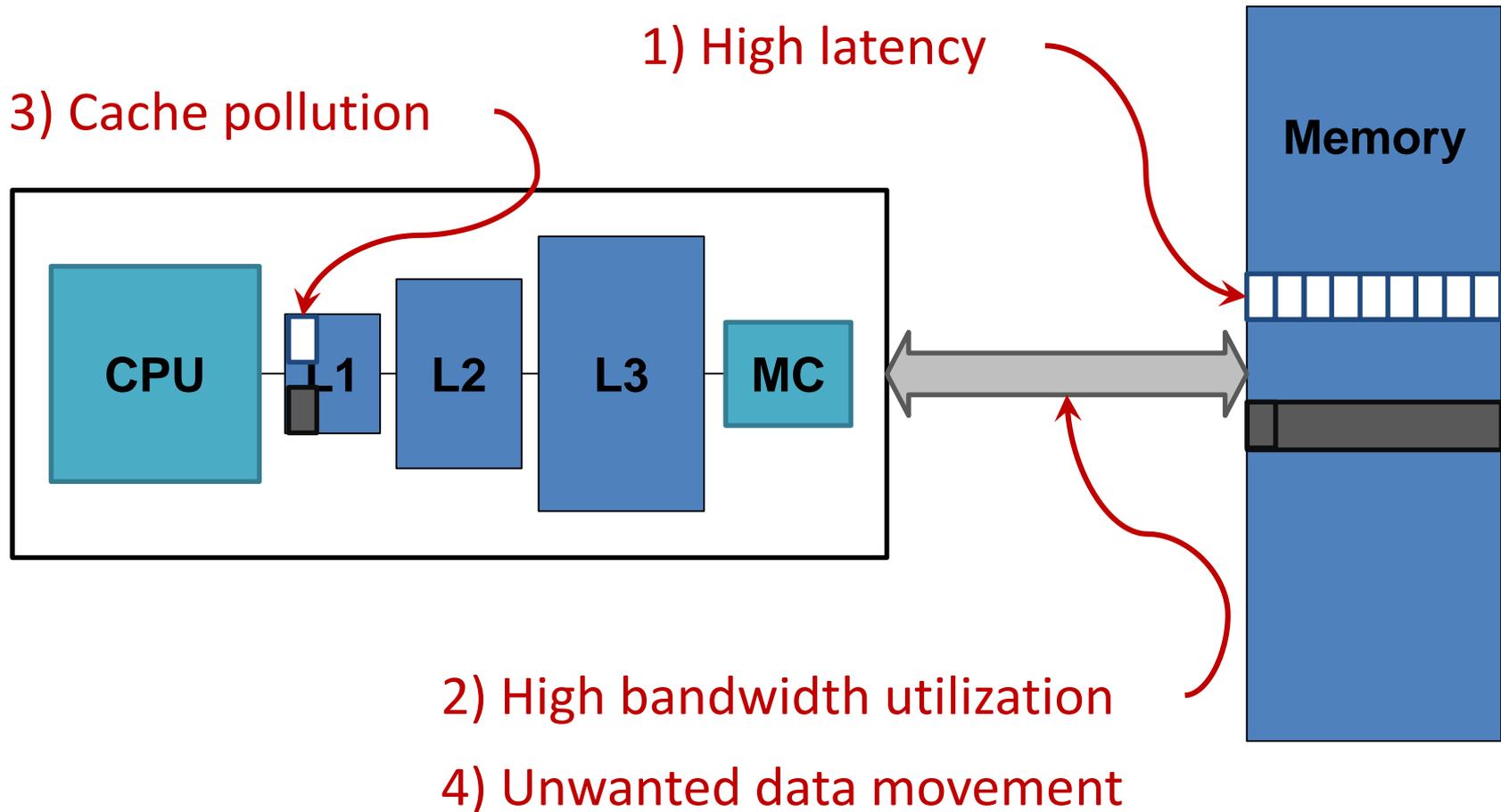
- **Systems are energy limited**

- **Data movement much more energy-hungry than computation**

Two Approaches to In-Memory Processing

- 1. Minimally change DRAM to enable simple yet powerful computation primitives
 - RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data (Seshadri et al., MICRO 2013)
 - Fast Bulk Bitwise AND and OR in DRAM (Seshadri et al., IEEE CAL 2015)
- 2. Exploit the control logic in 3D-stacked memory to enable more comprehensive computation near memory
 - PIM-Enabled Instructions: A Low-Overhead, Locality-Aware Processing-in-Memory Architecture (Ahn et al., ISCA 2015)
 - A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing (Ahn et al., ISCA 2015)

Today's Memory: Bulk Data Copy

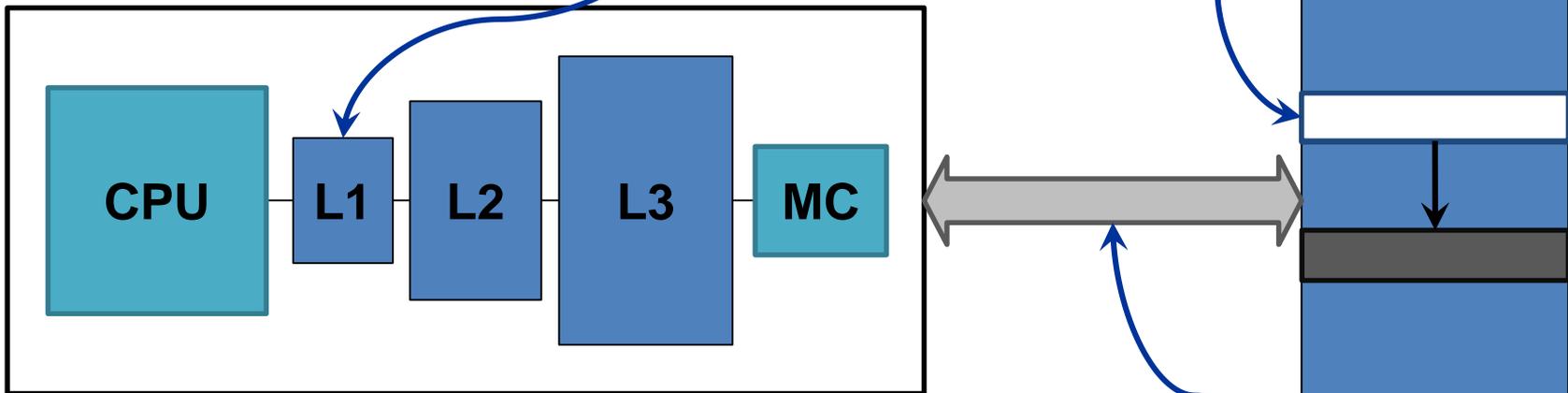


1046ns, 3.6uJ (for 4KB page copy via DMA)

Future: RowClone (In-Memory Copy)

3) No cache pollution

1) Low latency

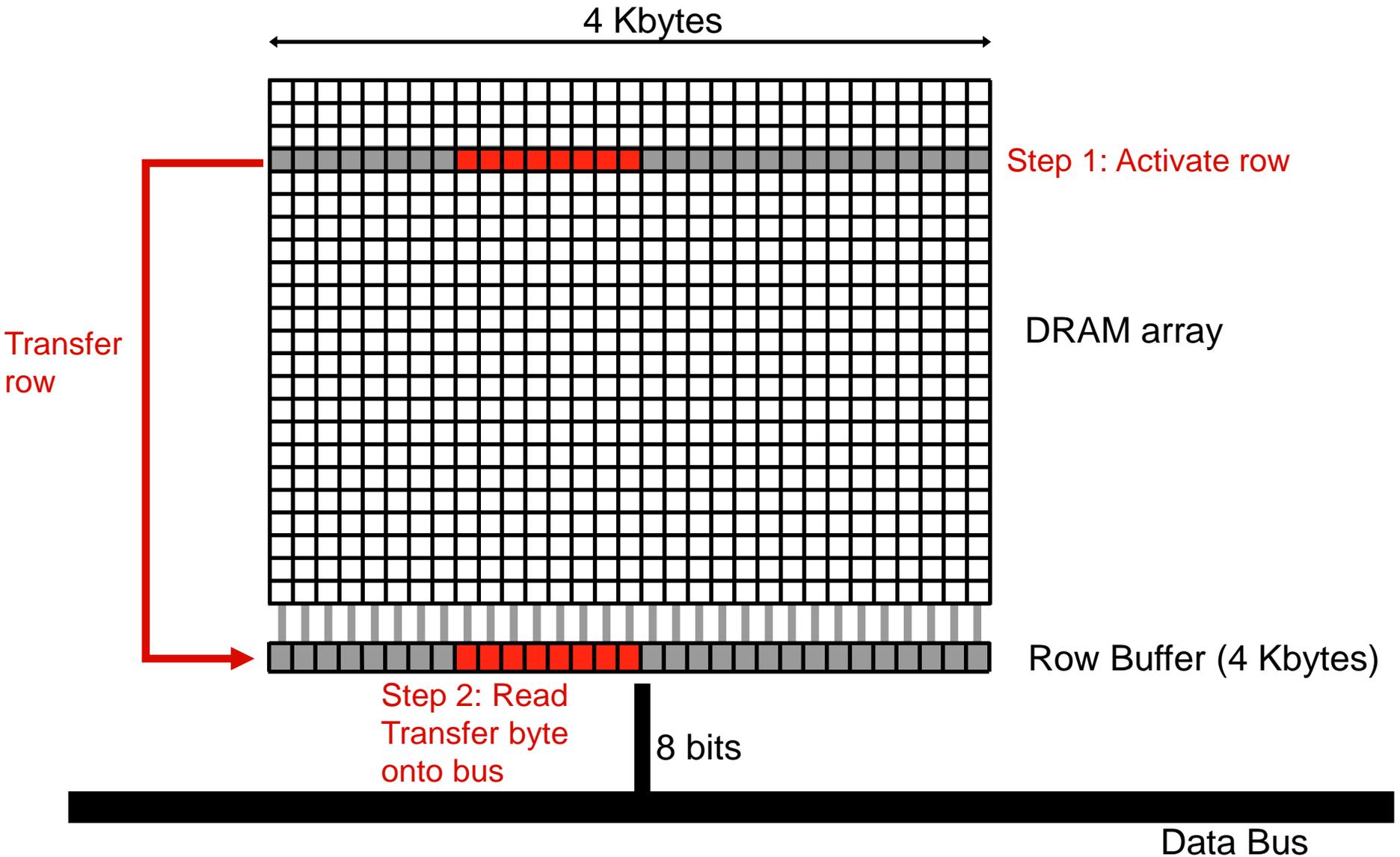


2) Low bandwidth utilization

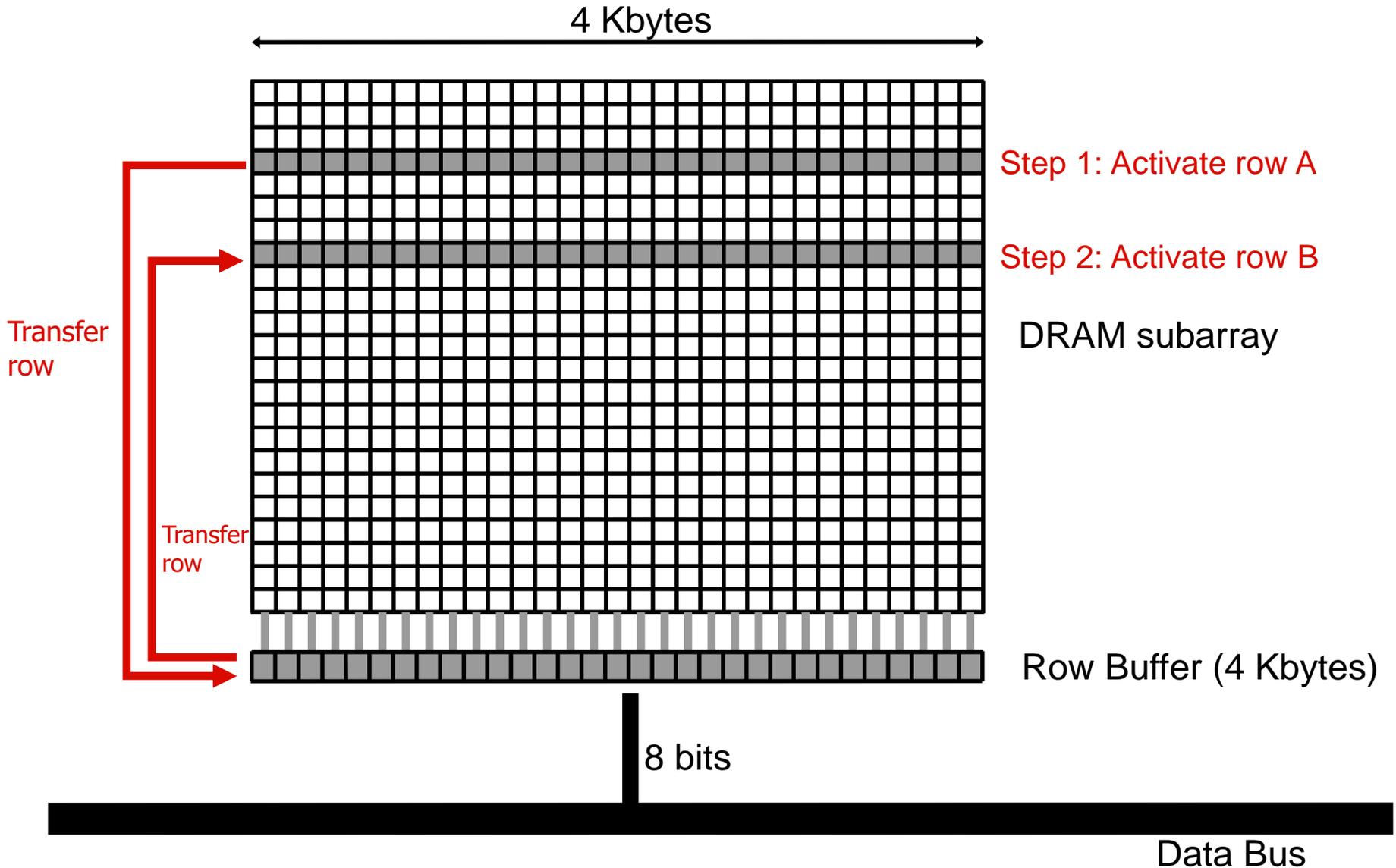
4) No unwanted data movement

1906ns, 0304uJ

DRAM Subarray Operation (load one byte)

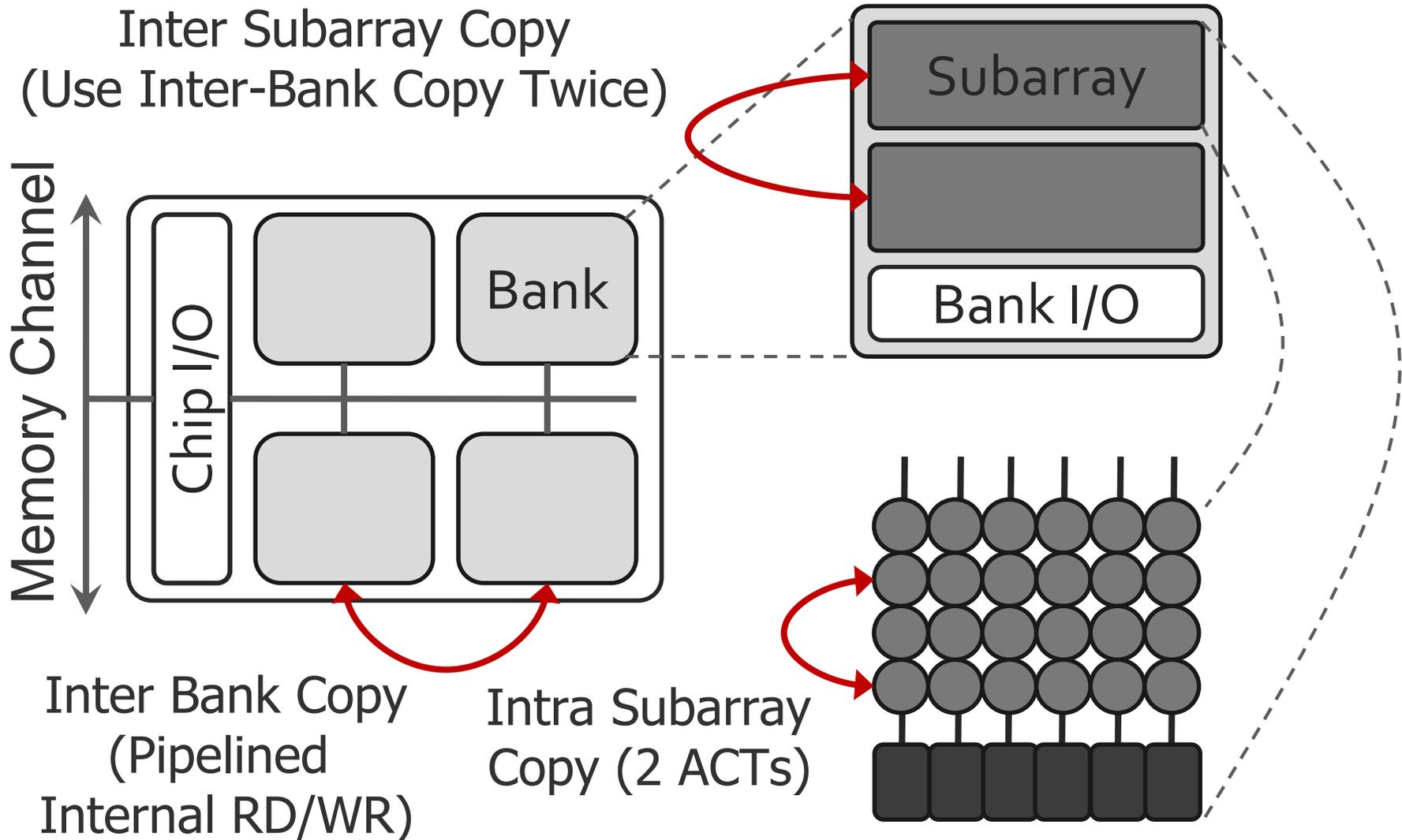


RowClone: In-DRAM Row Copy

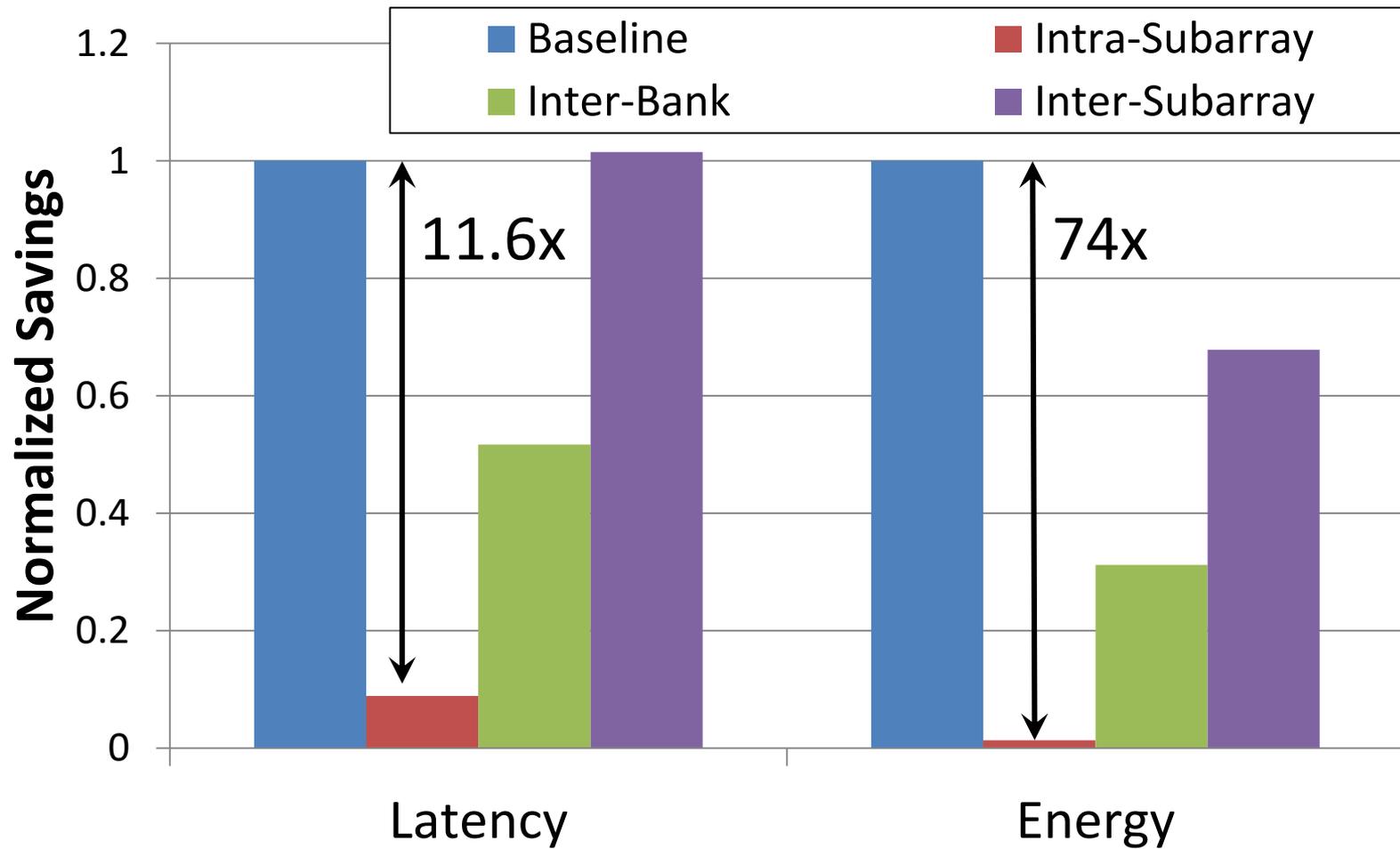


Generalized RowClone

0.01% area cost

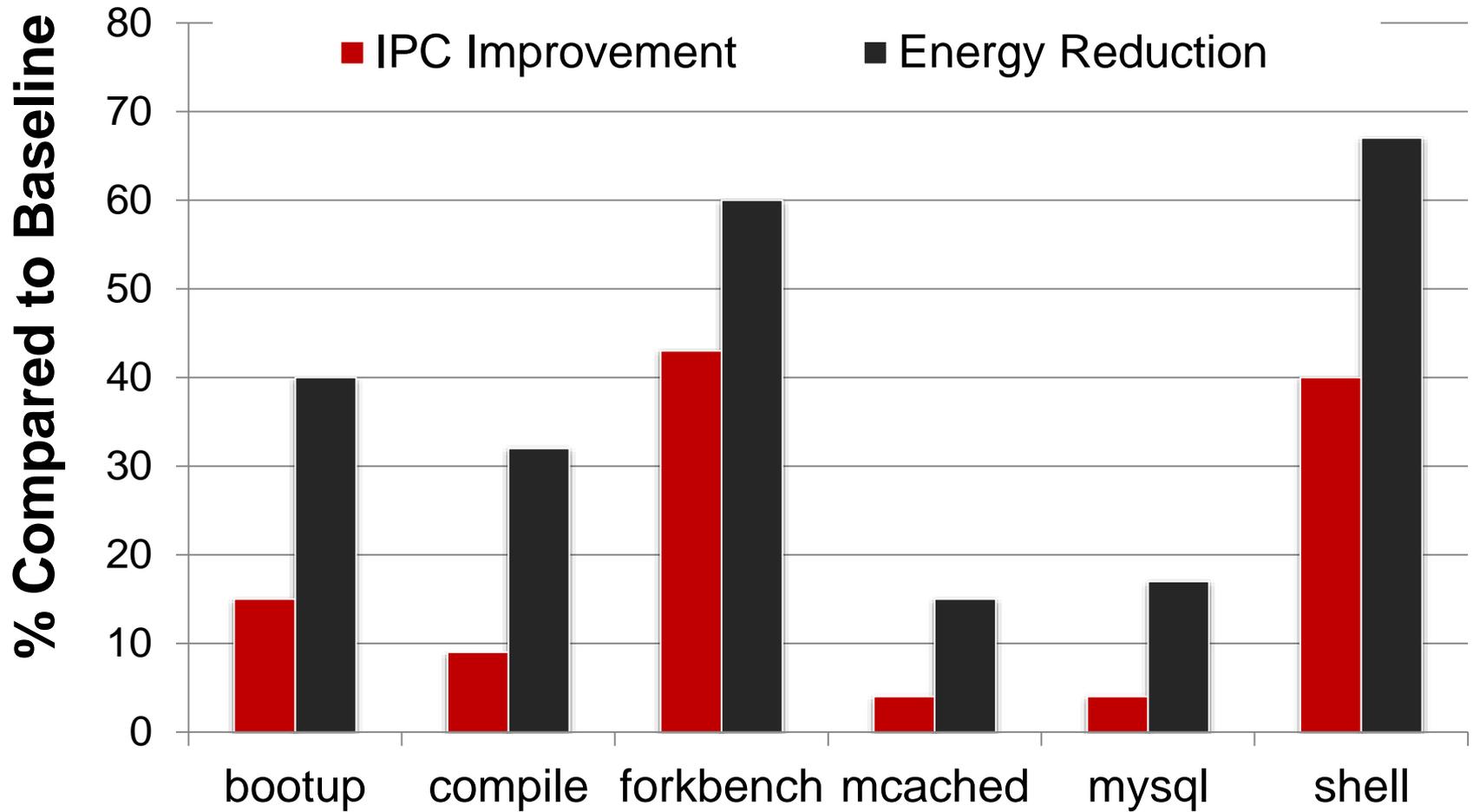


RowClone: Latency and Energy Savings

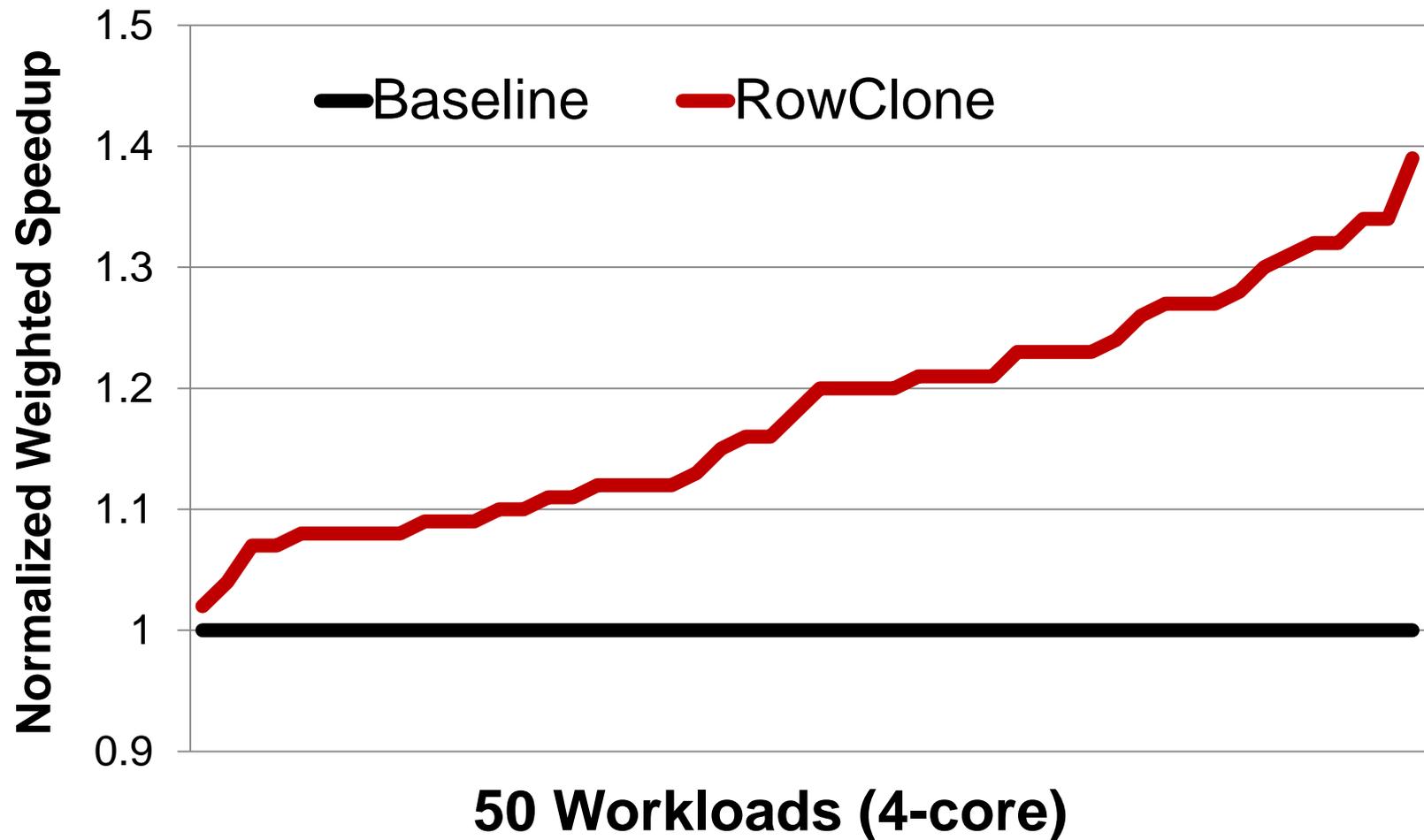


Seshadri et al., "RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data," MICRO 2013.

RowClone: Application Performance



RowClone: Multi-Core Performance



End-to-End System Design

Application

How to communicate occurrences of bulk copy/initialization across layers?

Operating System

How to ensure cache coherence?

ISA

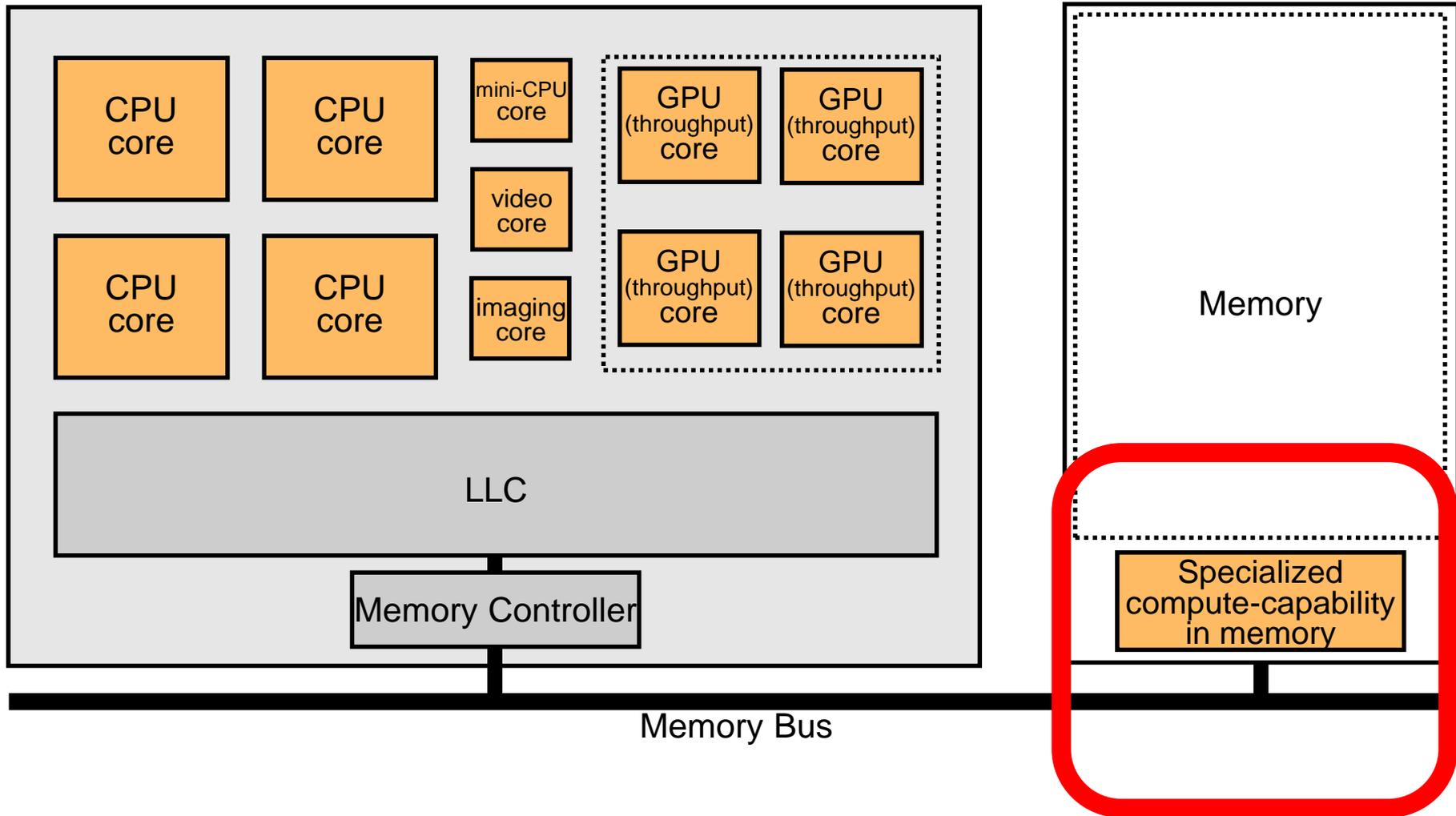
Microarchitecture

How to maximize latency and energy savings?

DRAM (RowClone)

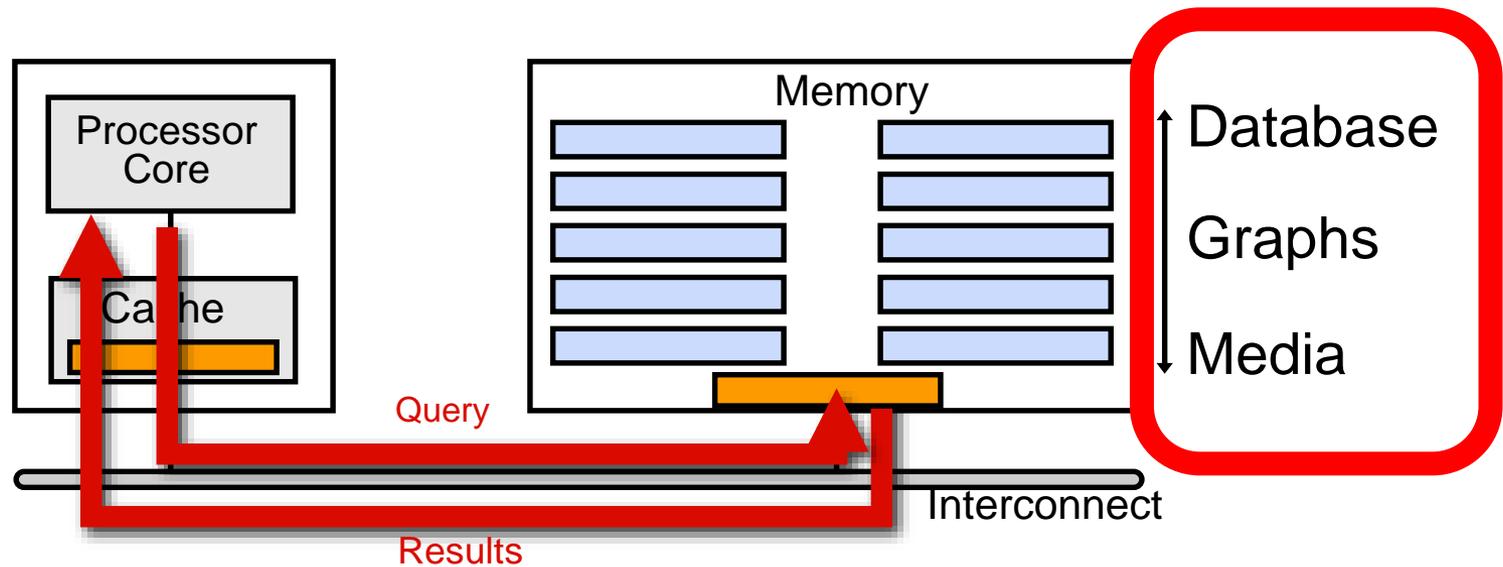
How to handle data reuse?

Goal: Ultra-Efficient Processing Near Data



Memory similar to a "conventional" accelerator

Enabling In-Memory Search

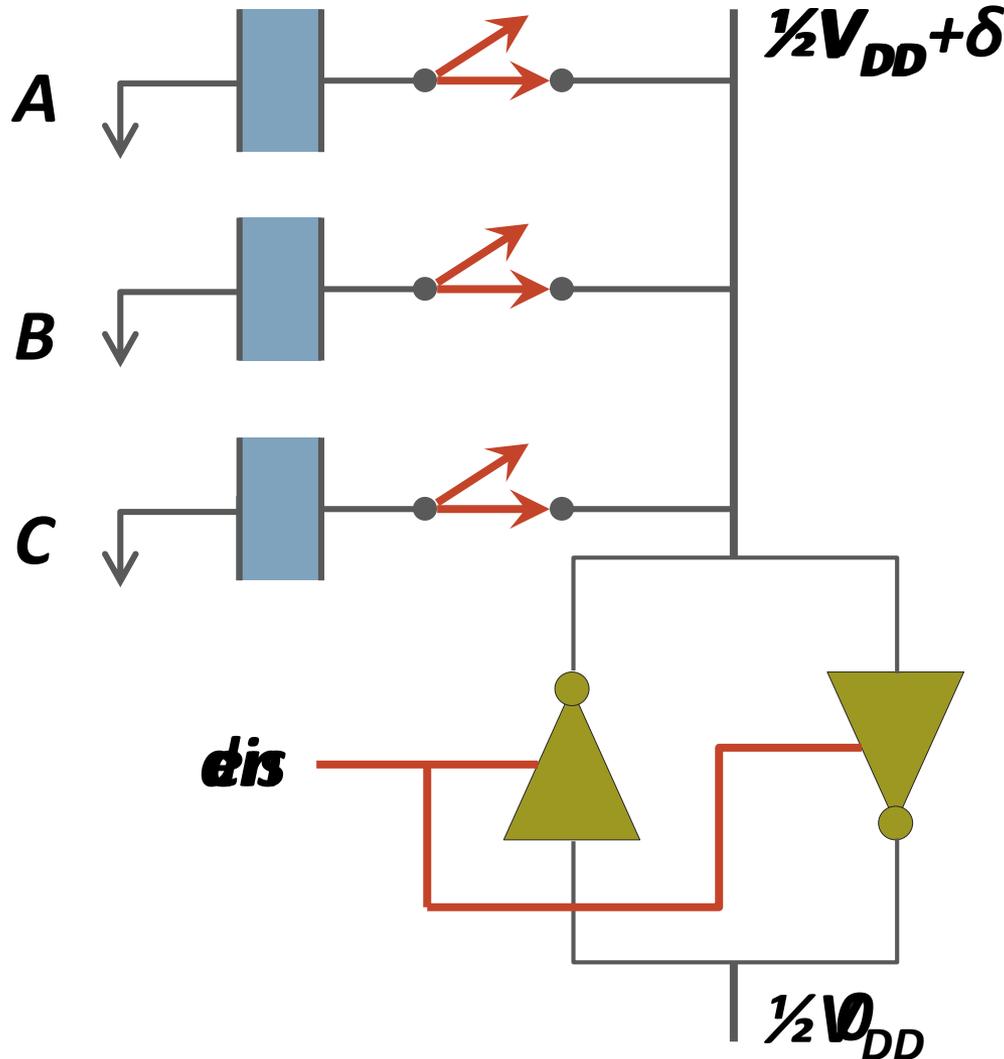


- What is a flexible and scalable memory interface?
- What is the right partitioning of computation capability?
- What is the right low-cost memory substrate?
- What memory technologies are the best enablers?
- How do we rethink/ease search algorithms/applications?

Enabling In-Memory Computation

DRAM Support	Cache Coherence	Virtual Memory Support
RowClone (MICRO 2013)	Dirty-Block Index (ISCA 2014)	Page Overlays (ISCA 2015)
In-DRAM Gather Scatter (MICRO 2015)	Non-contiguous Cache lines	Gathered Pages
In-DRAM Bitwise Operations (IEEE CAL 2015)	?	?

In-DRAM AND/OR: Triple Row Activation



Final State
 $AB + BC + AC$

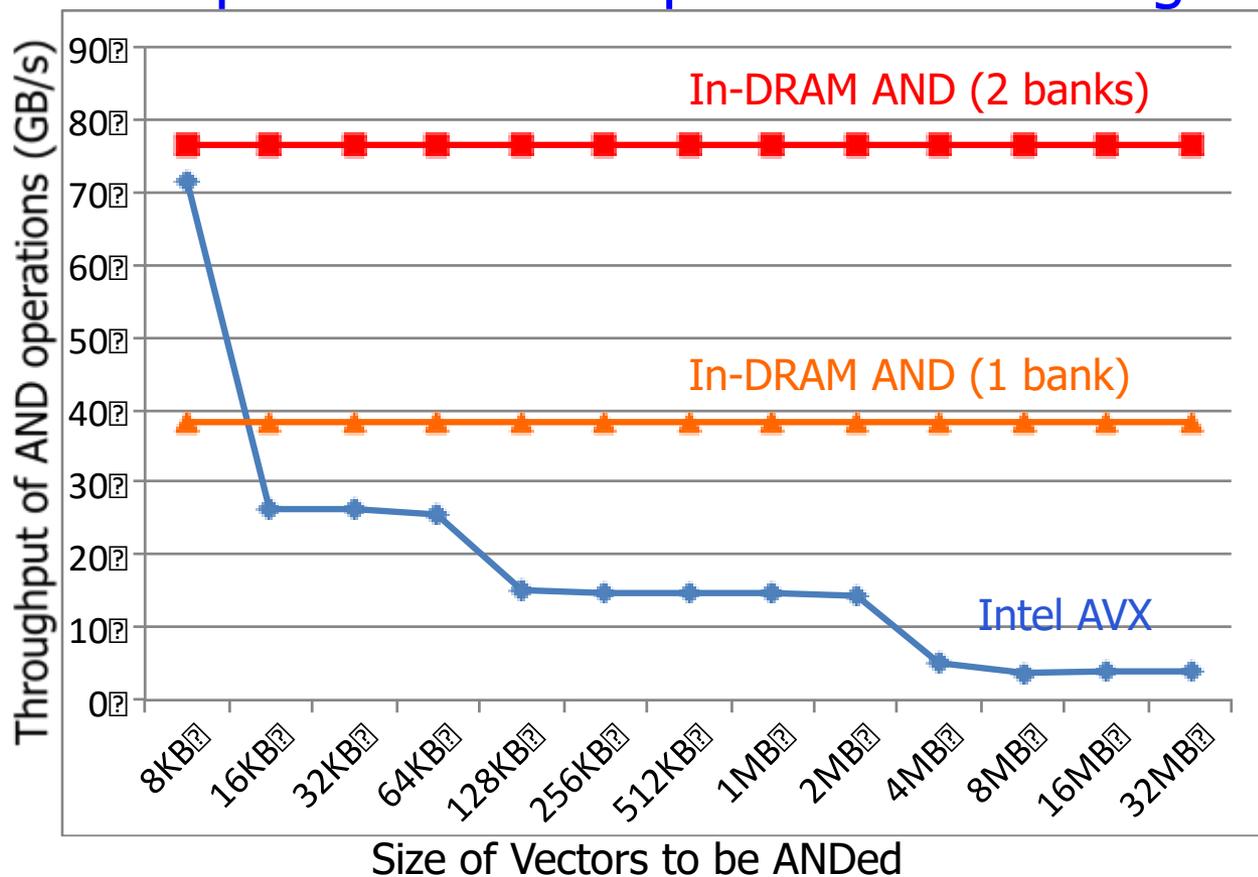
$C(A + B) + \sim C(AB)$

In-DRAM Bulk Bitwise AND/OR Operation

- **BULKAND A, B → C**
 - Semantics: Perform a bitwise AND of two rows A and B and store the result in row C
 - R0 – reserved zero row, R1 – reserved one row
 - D1, D2, D3 – Designated rows for triple activation
1. RowClone A into D1
 2. RowClone B into D2
 3. RowClone R0 into D3
 4. ACTIVATE D1,D2,D3
 5. RowClone Result into C

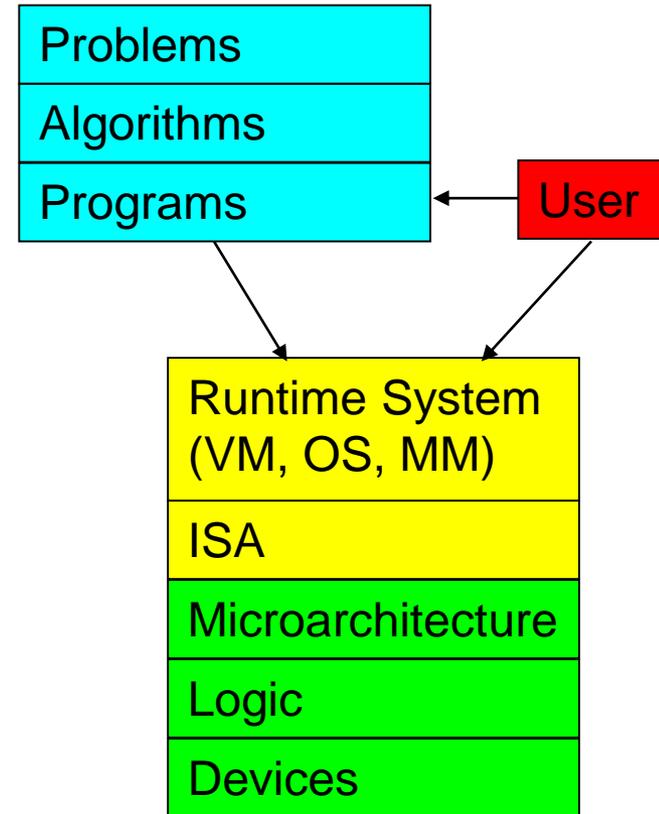
In-DRAM AND/OR Results

- 20X improvement in AND/OR throughput vs. Intel AVX
- 50.5X reduction in memory energy consumption
- At least 30% performance improvement in range queries



Going Forward

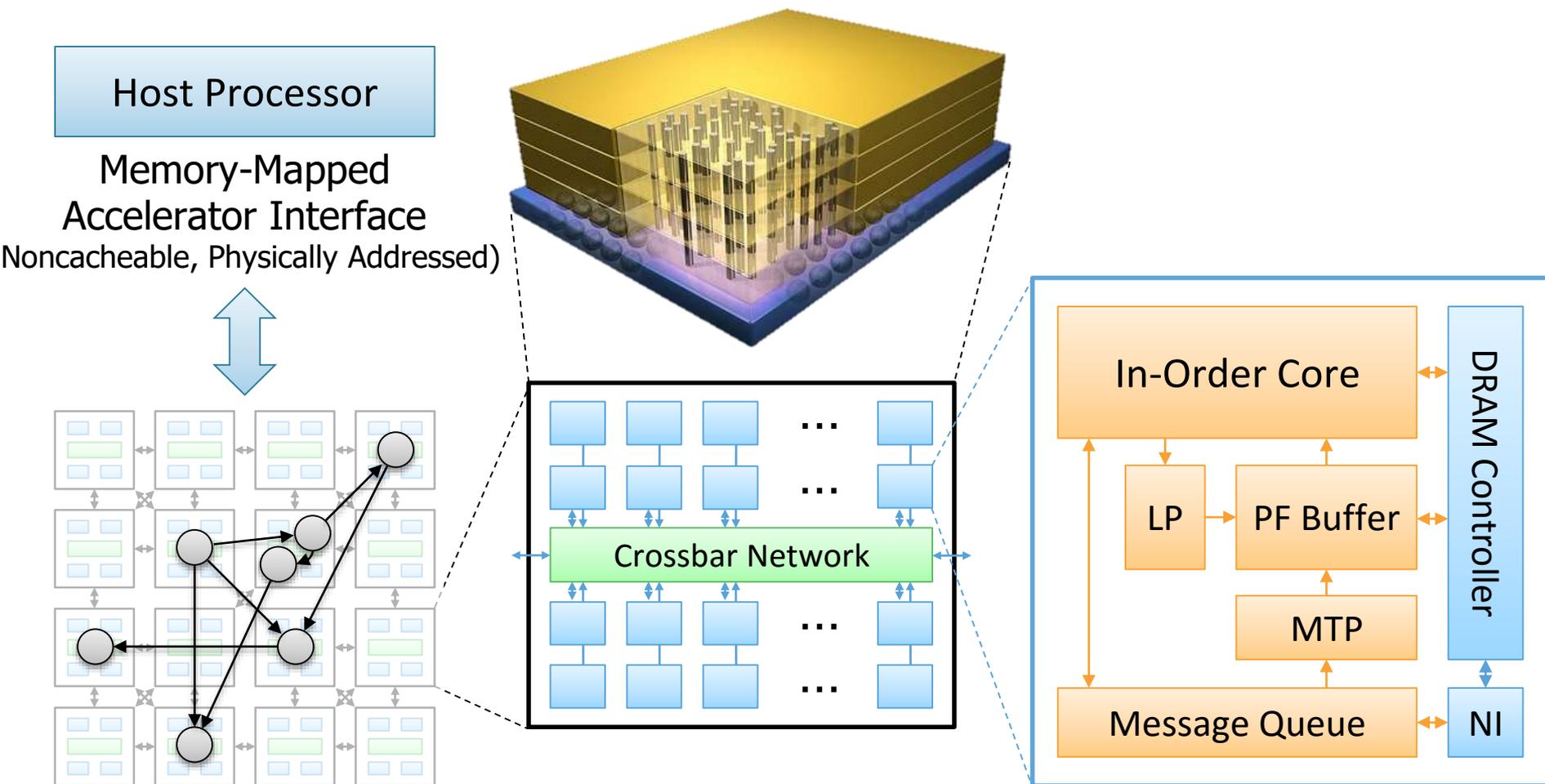
- A bulk computation model in memory
- New memory & software interfaces to enable bulk in-memory computation
- New programming models, algorithms, compilers, and system designs that can take advantage of the model



Two Approaches to In-Memory Processing

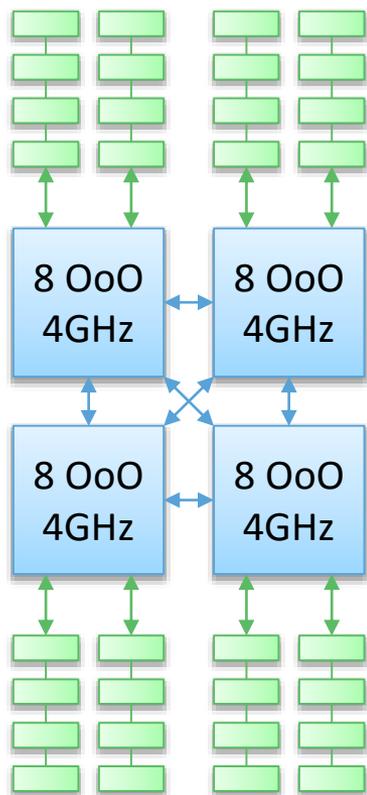
- 1. **Minimally change DRAM** to enable simple yet powerful computation primitives
 - RowClone: Fast and Efficient In-DRAM Copy and Initialization of Bulk Data (Seshadri et al., MICRO 2013)
 - Fast Bulk Bitwise AND and OR in DRAM (Seshadri et al., IEEE CAL 2015)
- 2. **Exploit the control logic in 3D-stacked memory** to enable more comprehensive computation near memory
 - PIM-Enabled Instructions: A Low-Overhead, Locality-Aware Processing-in-Memory Architecture (Ahn et al., ISCA 2015)
 - A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing (Ahn et al., ISCA 2015)

Tesseract System for Graph Processing



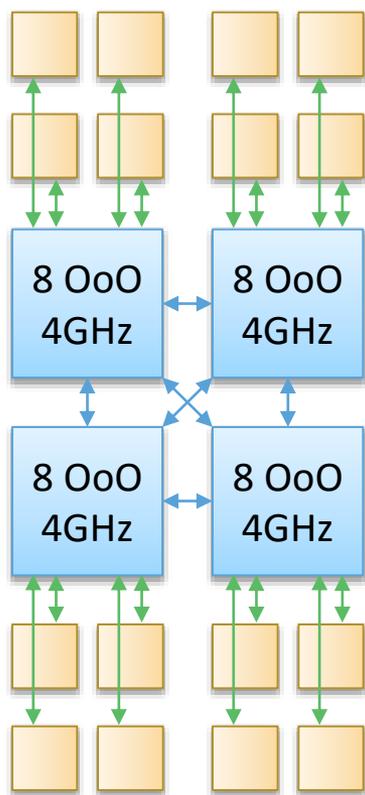
Evaluated Systems

DDR3-OoO
(with FDP)



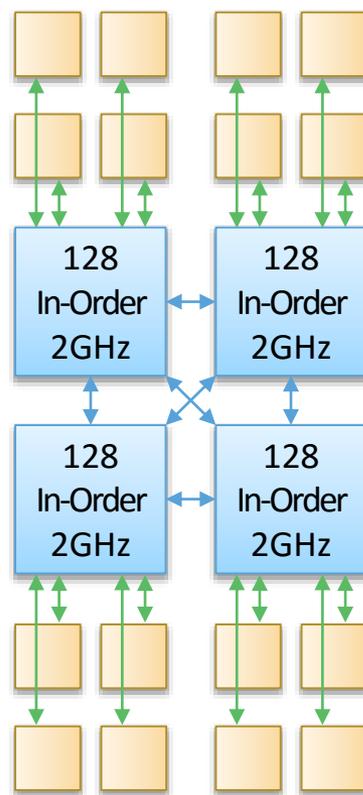
102.4GB/s

HMC-OoO
(with FDP)



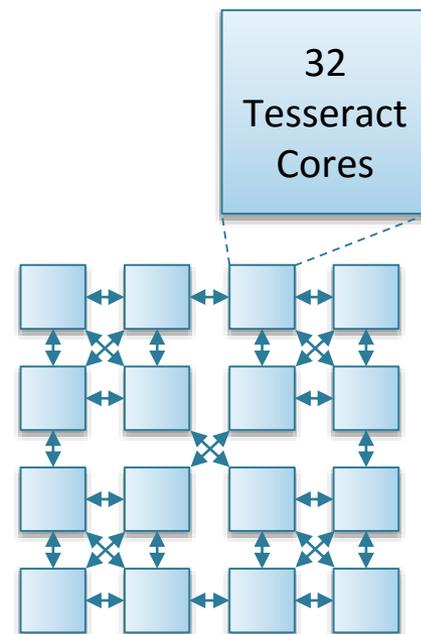
640GB/s

HMC-MC



640GB/s

Tesseract
(32-entry MQ, 4KB PF Buffer)



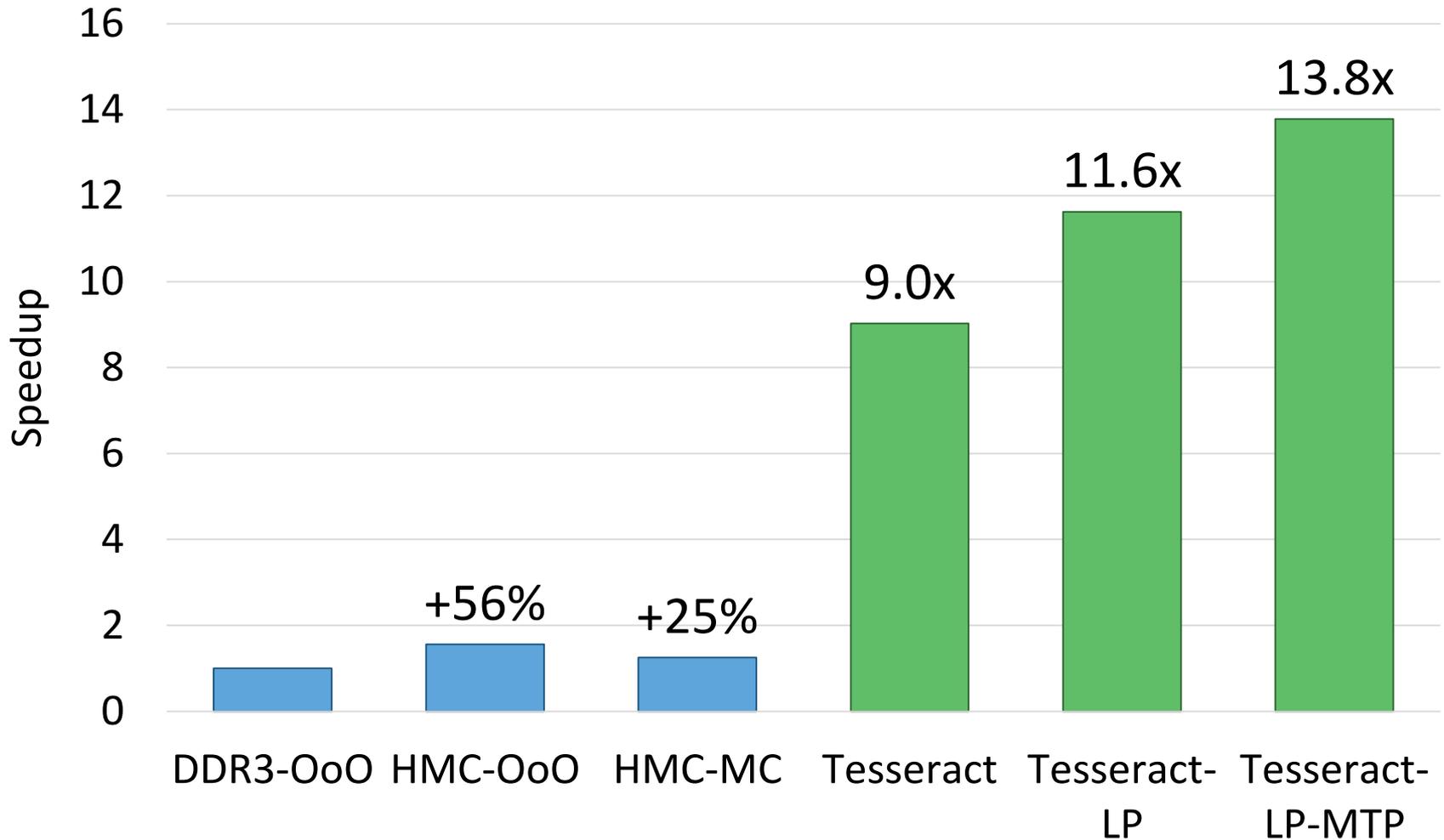
8TB/s

Workloads

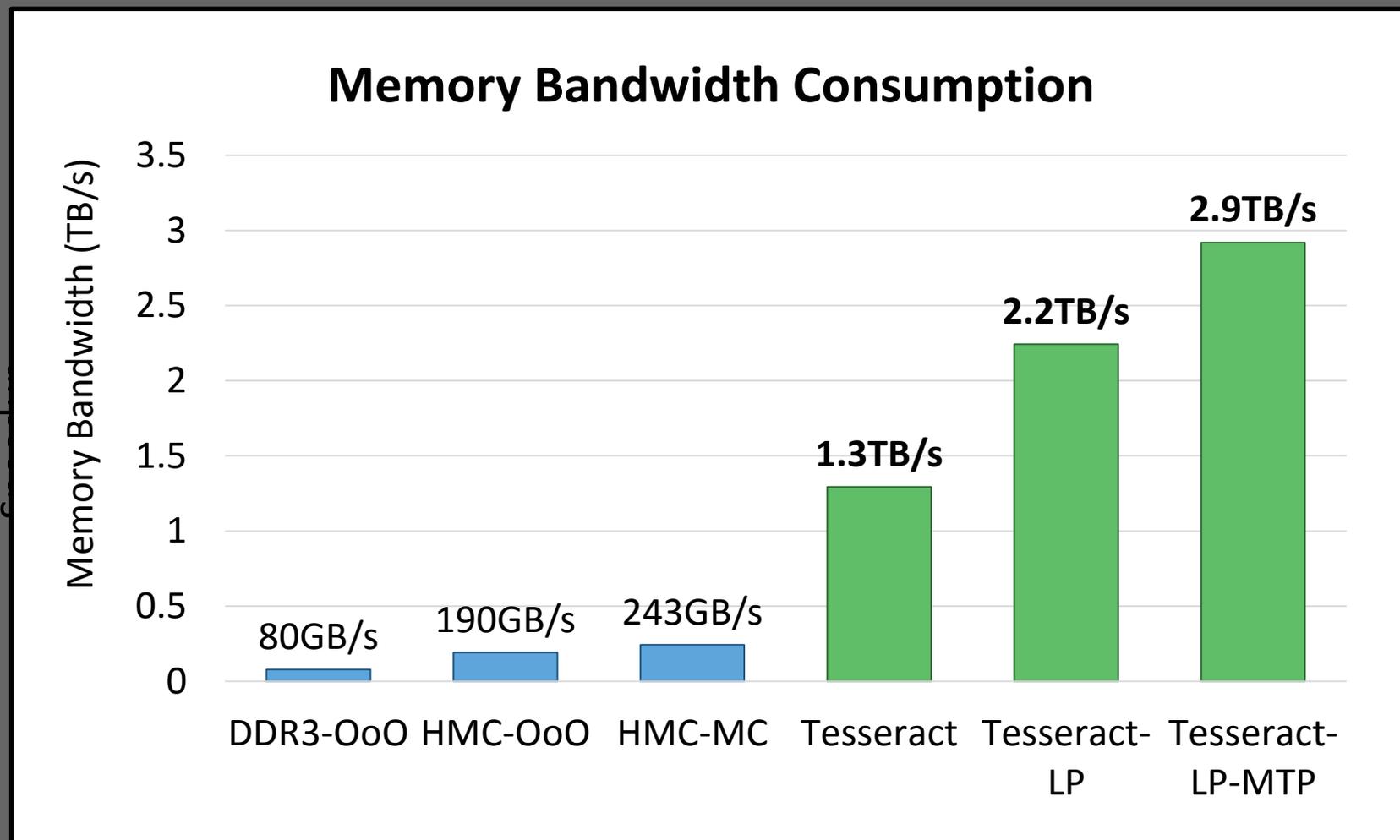
- Five graph processing algorithms
 - Average teenage follower
 - Conductance
 - PageRank
 - Single-source shortest path
 - Vertex cover

- Three real-world large graphs
 - ljournal-2008 (social network)
 - enwiki-2003 (Wikipedia)
 - indochina-0024 (web graph)
 - 4~7M vertices, 79~194M edges

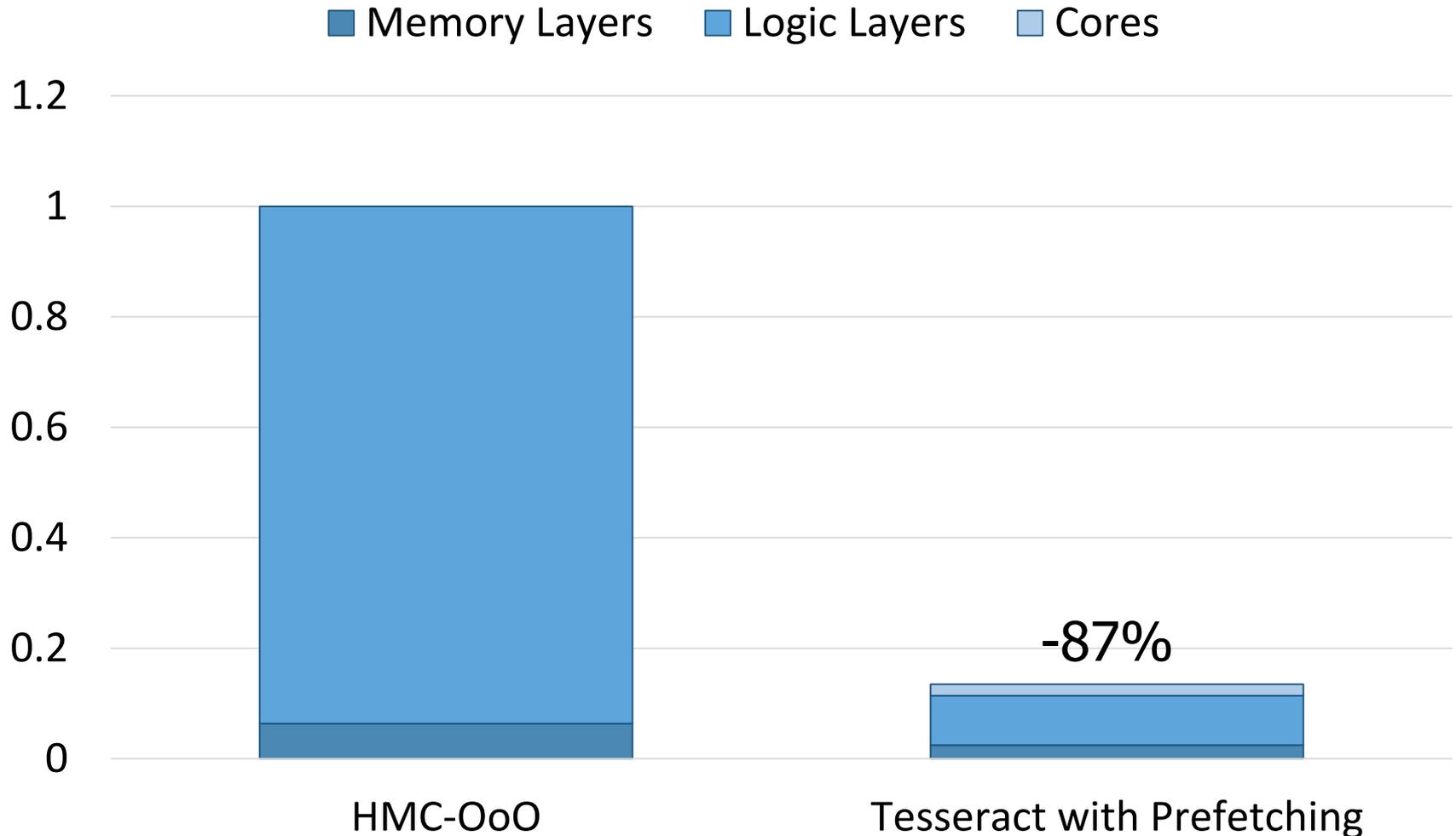
Tesseract Graph Processing Performance



Tesseract Graph Processing Performance



Memory Energy Consumption (Normalized)

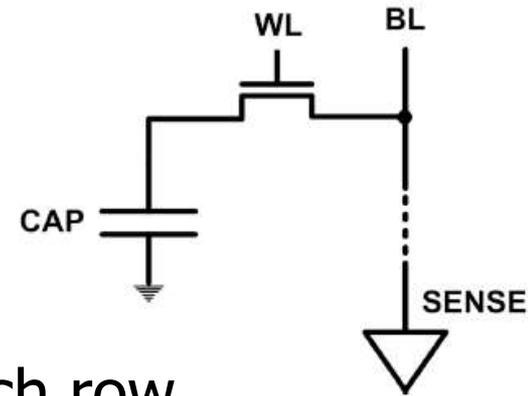


Rethinking DRAM

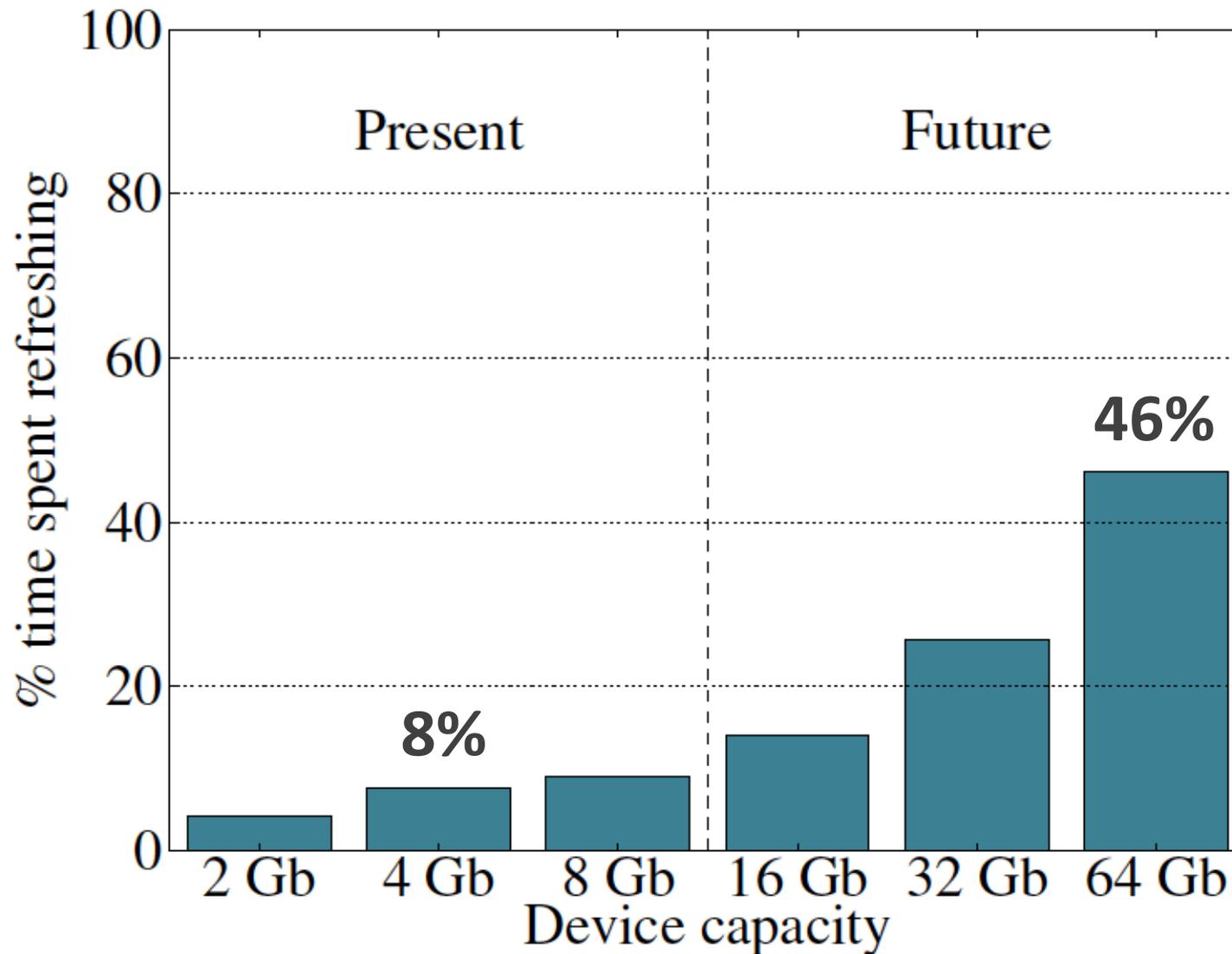
- In-Memory Computation
 - Refresh
 - Reliability
- Latency
- Bandwidth
- Energy
- Memory Compression

DRAM Refresh

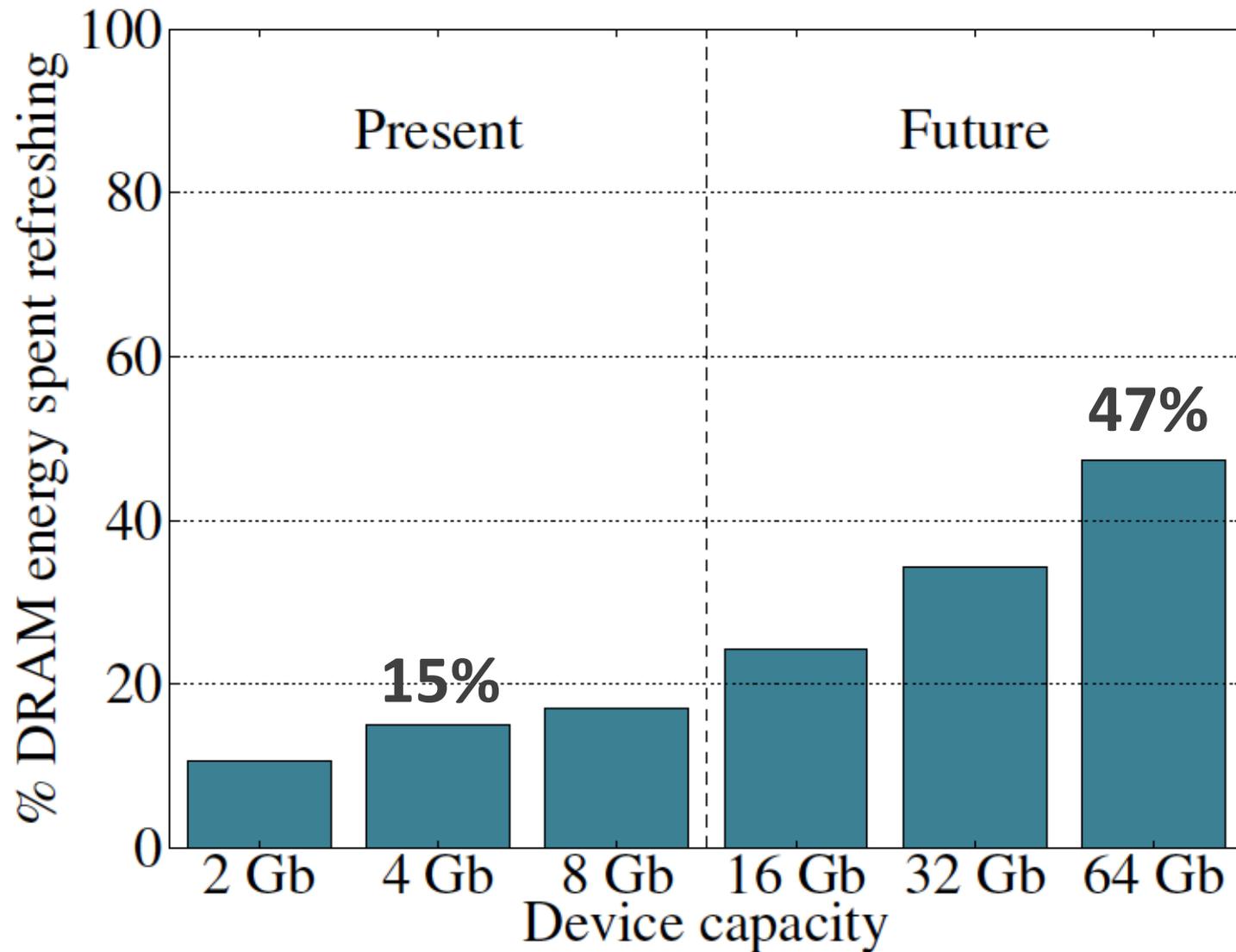
- DRAM capacitor charge leaks over time
- The memory controller needs to refresh each row periodically to restore charge
 - Activate each row every N ms
 - Typical N = 64 ms
- Downsides of refresh
 - **Energy consumption**: Each refresh consumes energy
 - **Performance degradation**: DRAM rank/bank unavailable while refreshed
 - **QoS/predictability impact**: (Long) pause times during refresh
 - **Refresh rate limits DRAM capacity scaling**



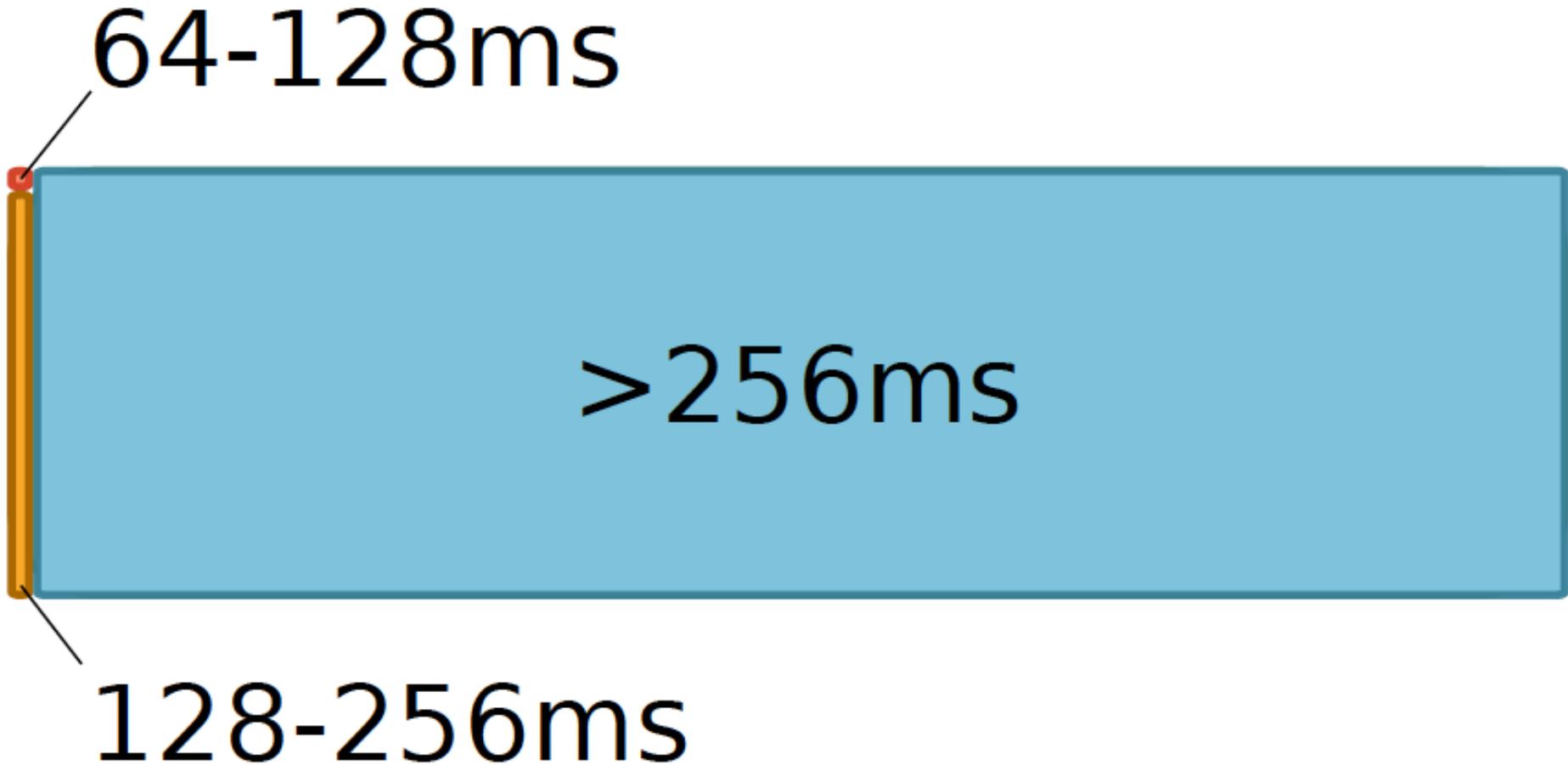
Refresh Overhead: Performance



Refresh Overhead: Energy



Retention Time Profile of DRAM



RAIDR: Eliminating Unnecessary Refreshes

Observation: Most DRAM rows can be refreshed much less often without losing data [Kim+, EDL'09][Liu+ ISCA'13]

Key idea: Refresh rows containing weak cells more frequently, other rows less frequently

1. Profiling: Profile retention time of all rows

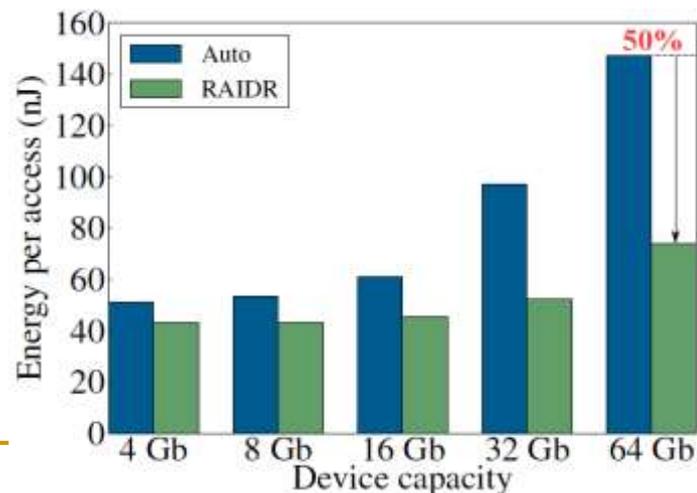
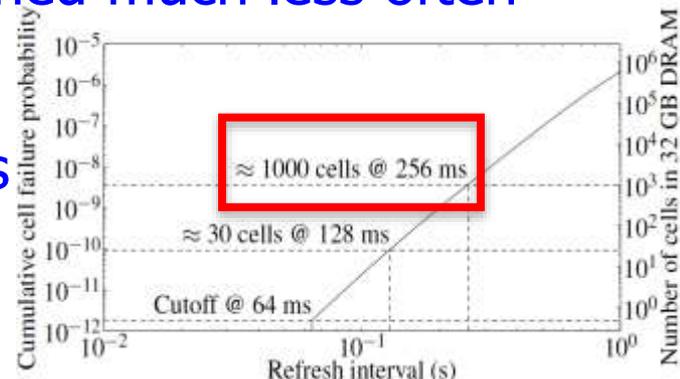
2. Binning: Store rows into bins by retention time in memory controller

Efficient storage with Bloom Filters (only 1.25KB for 32GB memory)

3. Refreshing: Memory controller refreshes rows in different bins at different rates

Results: 8-core, 32GB, SPEC, TPC-C, TPC-H

- 74.6% refresh reduction @ 1.25KB storage
- ~16%/20% DRAM dynamic/idle power reduction
- ~9% performance improvement
- Benefits increase with DRAM capacity



Going Forward (for DRAM and Flash)

■ How to find out weak memory cells/rows

- Liu+, "An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms", ISCA 2013.
- Khan+, "The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study," SIGMETRICS 2014.

■ Low-cost system-level tolerance of memory errors

- Luo+, "Characterizing Application Memory Error Vulnerability to Optimize Data Center Cost," DSN 2014.
- Cai+, "Error Analysis and Retention-Aware Error Management for NAND Flash Memory," Intel Technology Journal 2013.
- Cai+, "Neighbor-Cell Assisted Error Correction for MLC NAND Flash Memories," SIGMETRICS 2014.

■ Tolerating cell-to-cell interference at the system level

- Kim+, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," ISCA 2014.
- Cai+, "Program Interference in MLC NAND Flash Memory: Characterization, Modeling, and Mitigation," ICCD 2013.

Experimental DRAM Testing Infrastructure



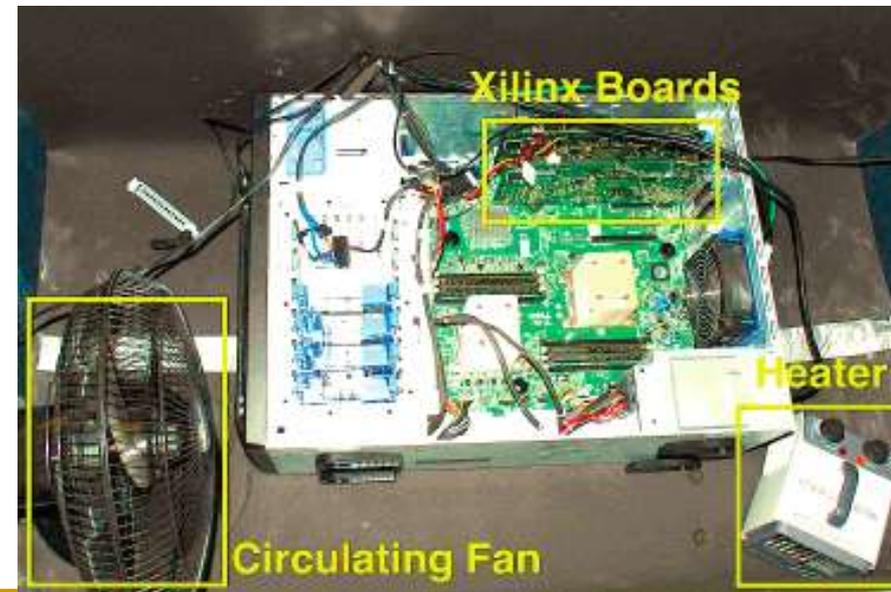
An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms (Liu et al., ISCA 2013)

The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study (Khan et al., SIGMETRICS 2014)

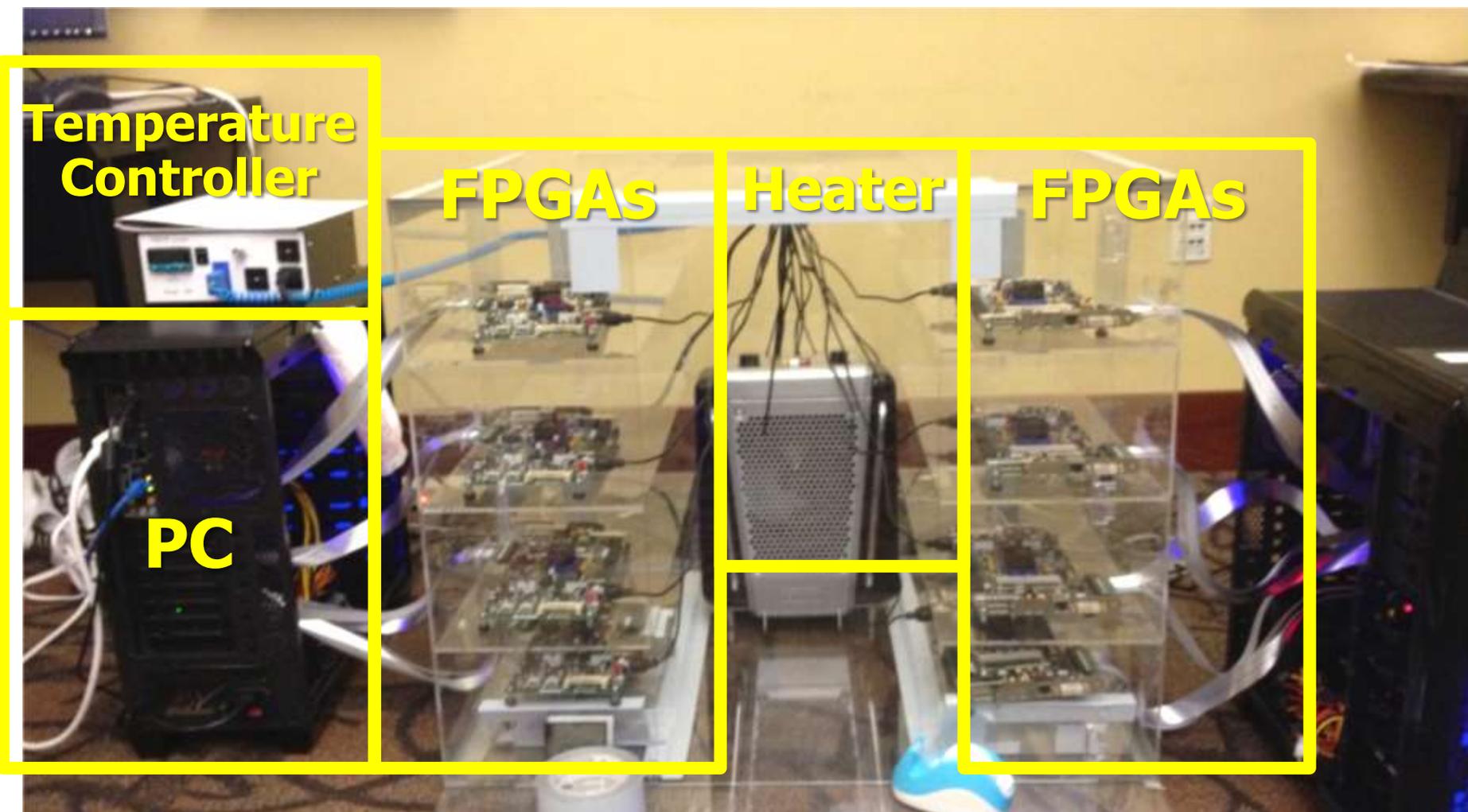
Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)

Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case (Lee et al., HPCA 2015)

AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems (Qureshi et al., DSN 2015)



Experimental Infrastructure (DRAM)



The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study

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[†]Carnegie Mellon University

^{*}Intel Labs

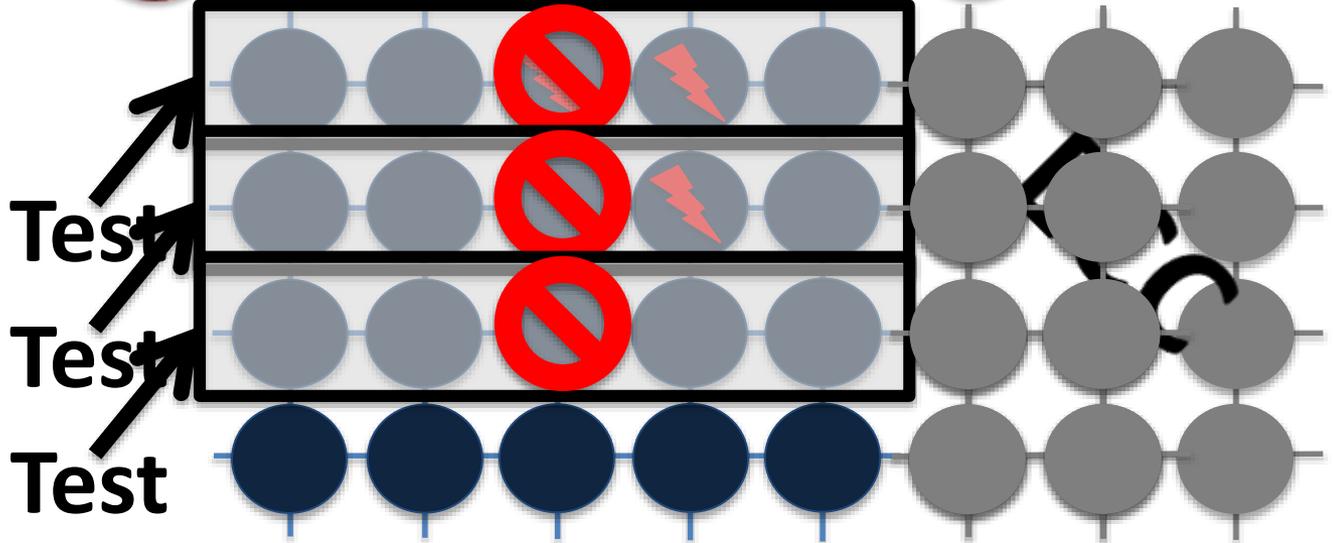
Online Profiling of DRAM In the Field

Initially protect DRAM with ECC

1

Periodically test parts of DRAM

2



Adjust refresh rate and reduce ECC

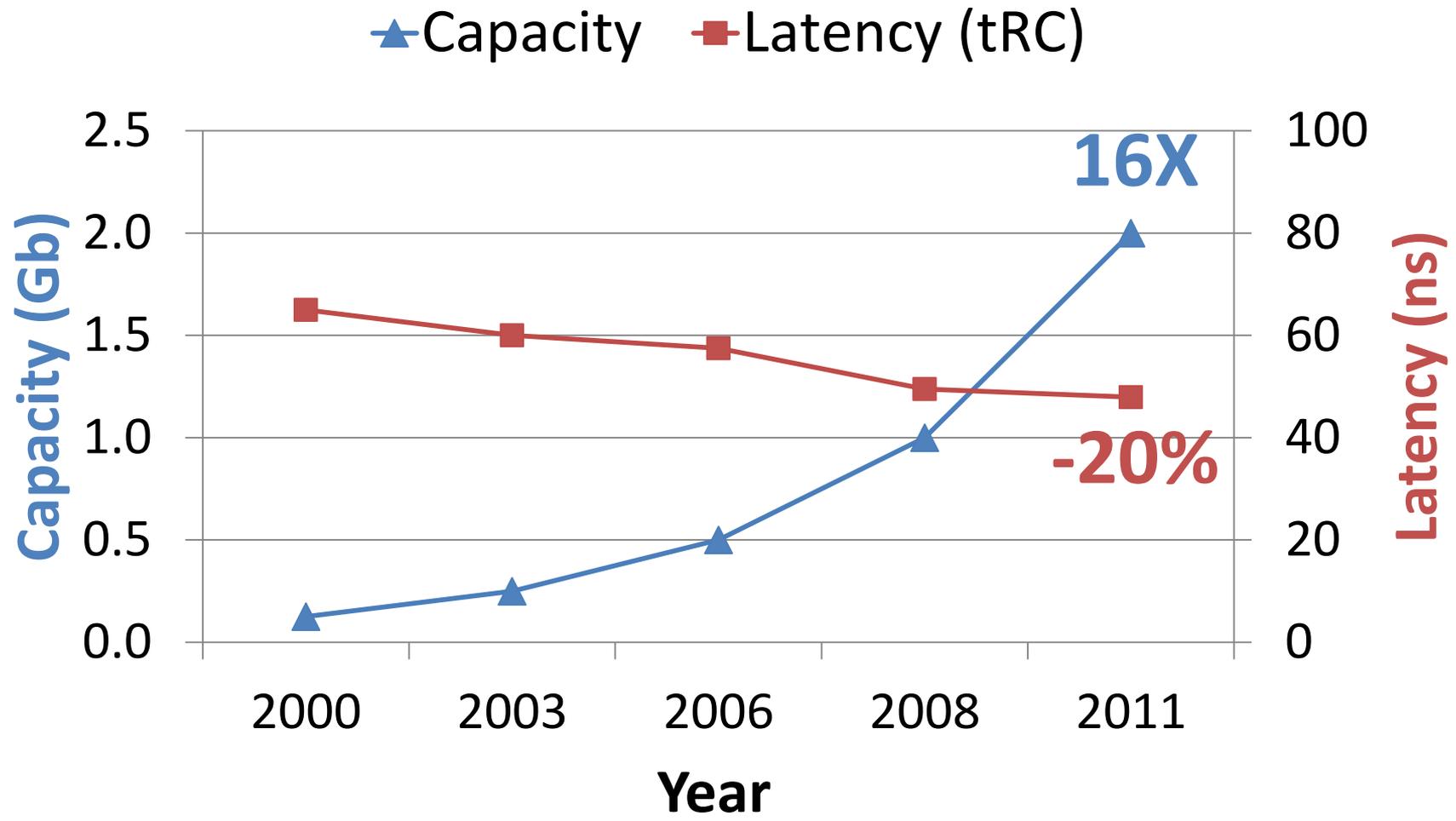
3

Optimize DRAM and mitigate errors online without disturbing the system and applications

Rethinking DRAM

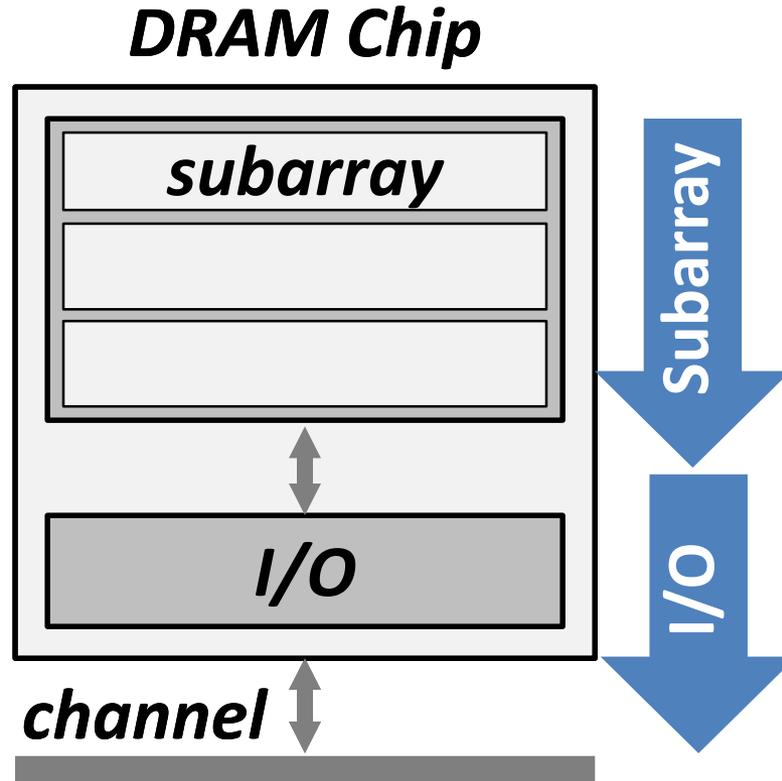
- In-Memory Computation
- Refresh
- Reliability
- Latency
- Bandwidth
- Energy
- Memory Compression

DRAM Latency-Capacity Trend



DRAM latency continues to be a critical bottleneck, especially for response time-sensitive ⁷⁸

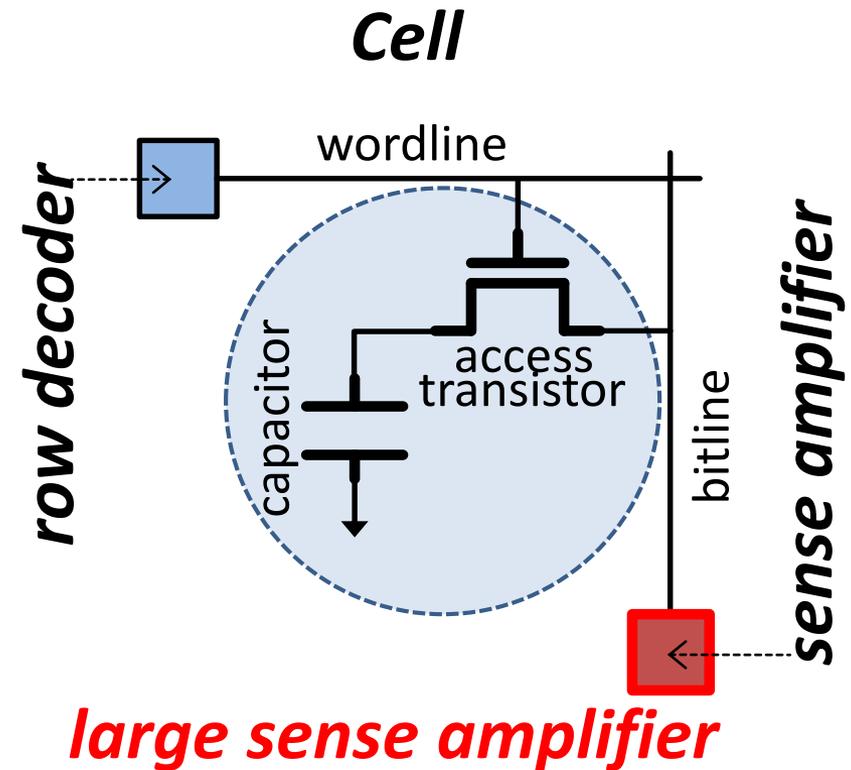
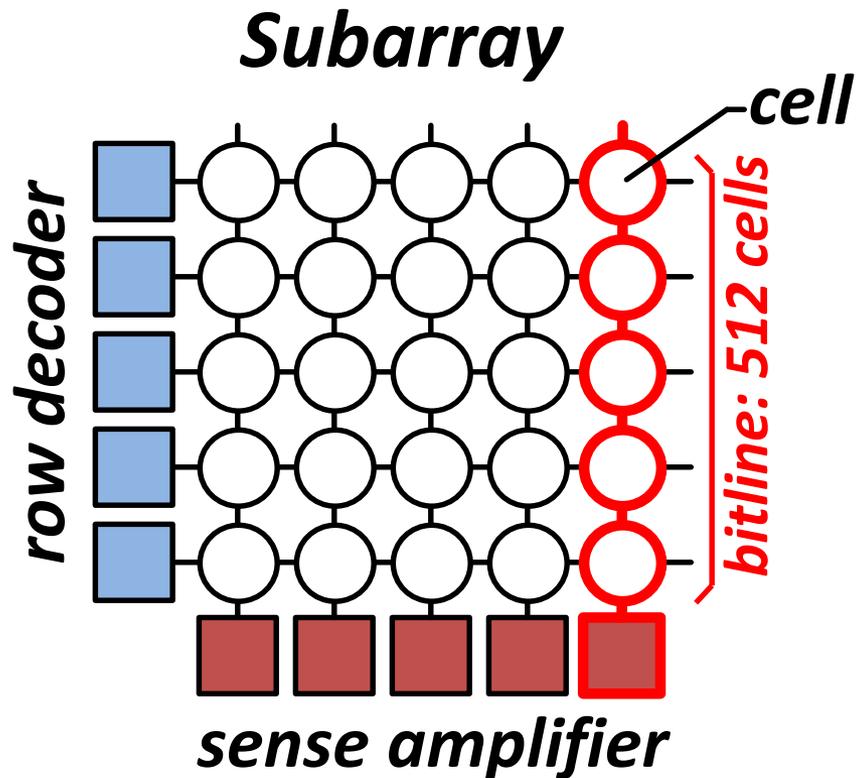
What Causes the Long Latency?



*DRAM Latency = **Subarray Latency** + I/O Latency*

Dominant

Why is the Subarray So Slow?

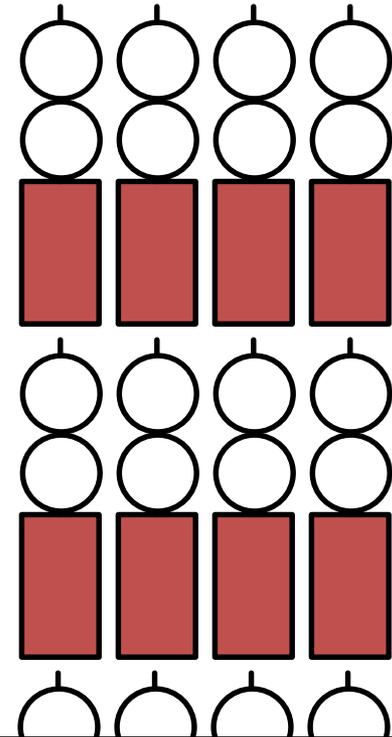
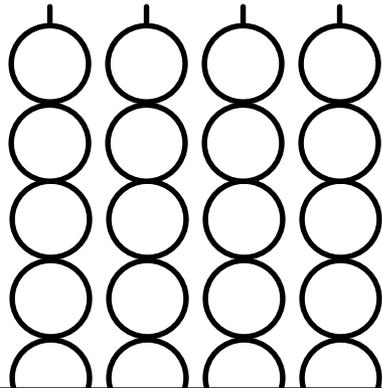


- Long bitline
 - Amortizes sense amplifier cost → Small area
 - Large bitline capacitance → High latency & power

Trade-Off: Area (Die Size) vs. Latency

Long Bitline

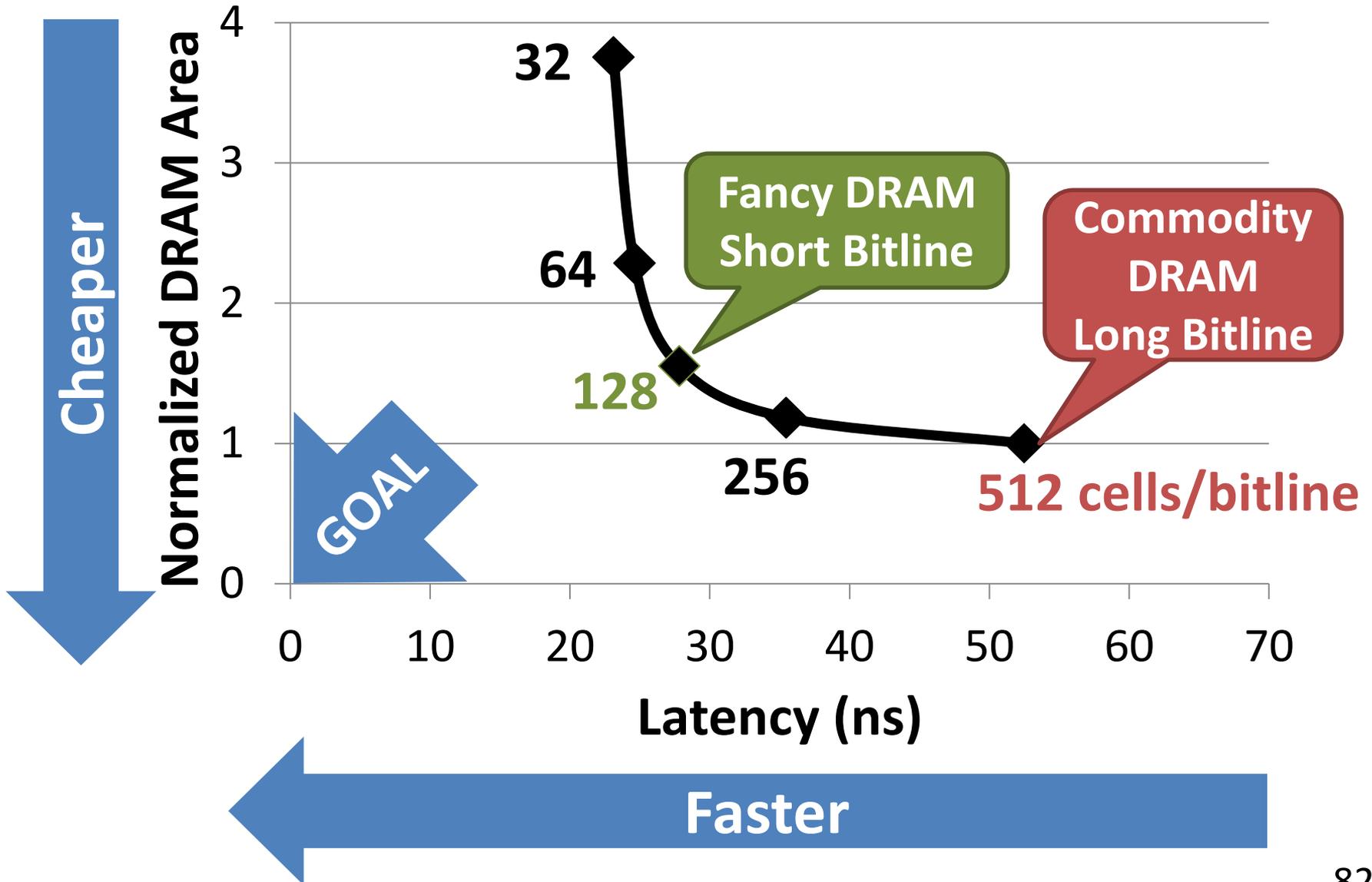
Short Bitline



Trade-Off: Area vs. Latency



Trade-Off: Area (Die Size) vs. Latency

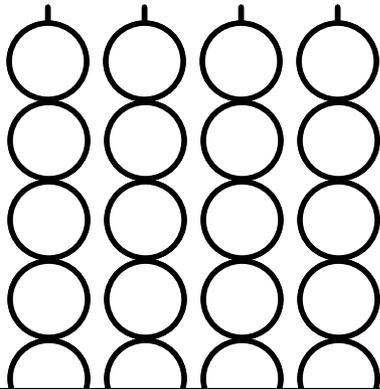


Approximating the Best of Both Worlds

Long Bitline

Small Area

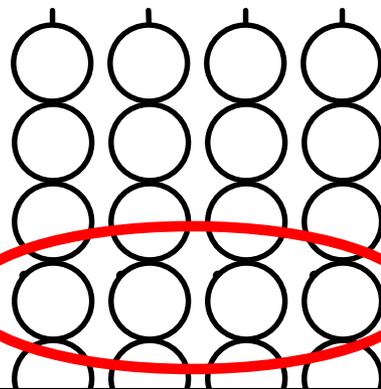
~~High Latency~~



Need Isolation

Our Proposal

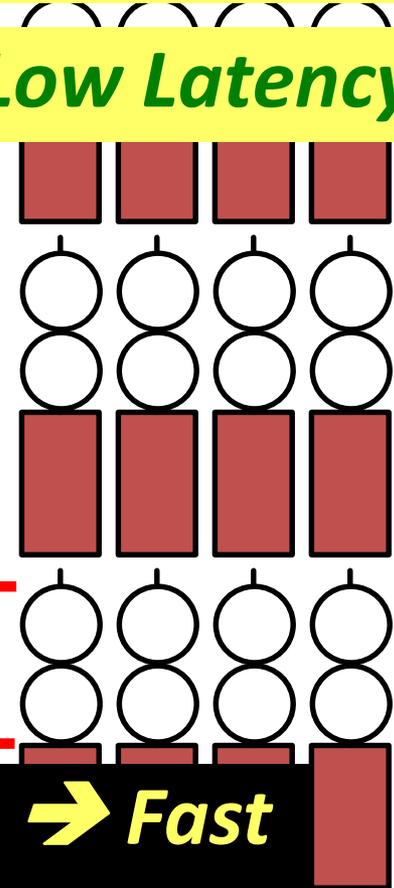
Add Isolation Transistors



Short Bitline

~~Large Area~~

Low Latency



Approximating the Best of Both Worlds

Long Bitline Tiered-Latency DRAM | **Short Bitline**

Small Area

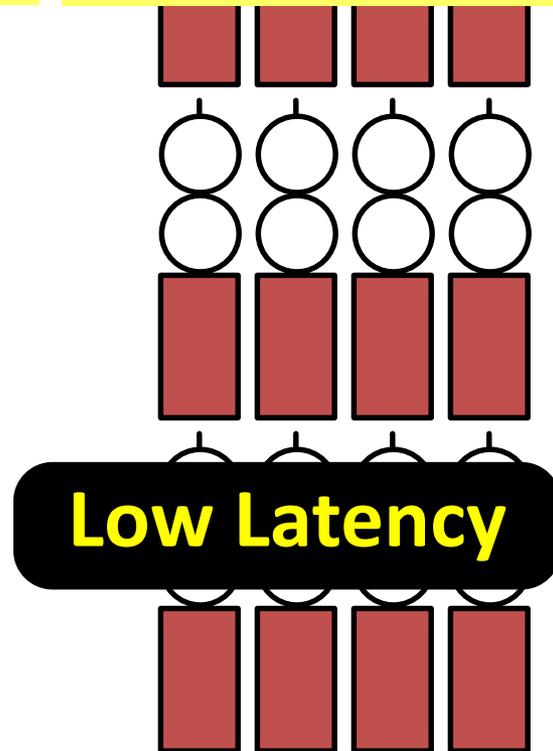
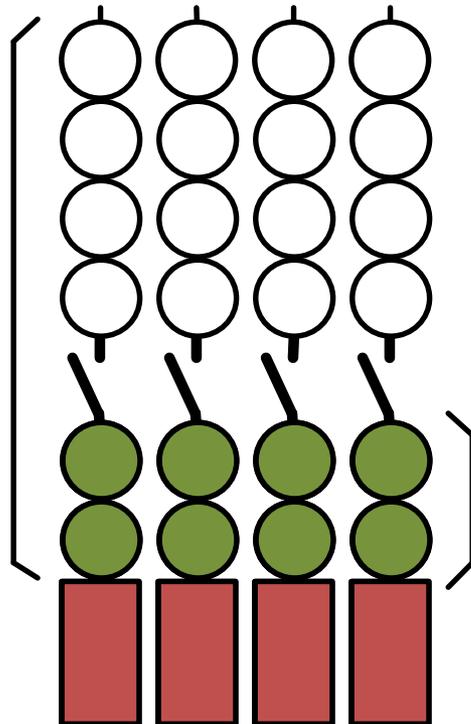
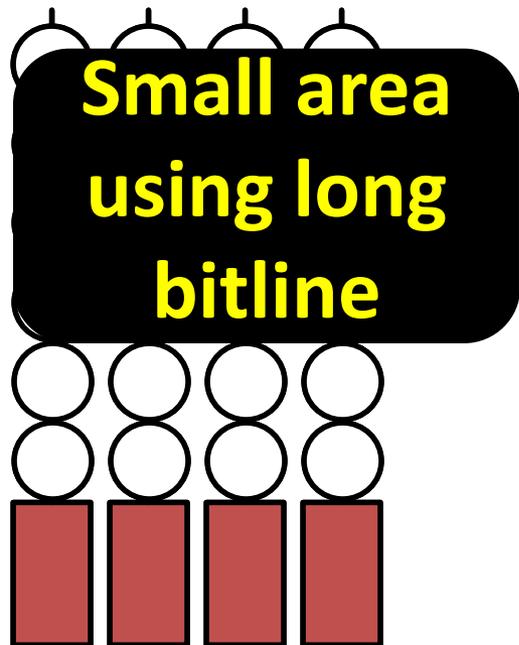
Small Area

~~*Large Area*~~

~~*High Latency*~~

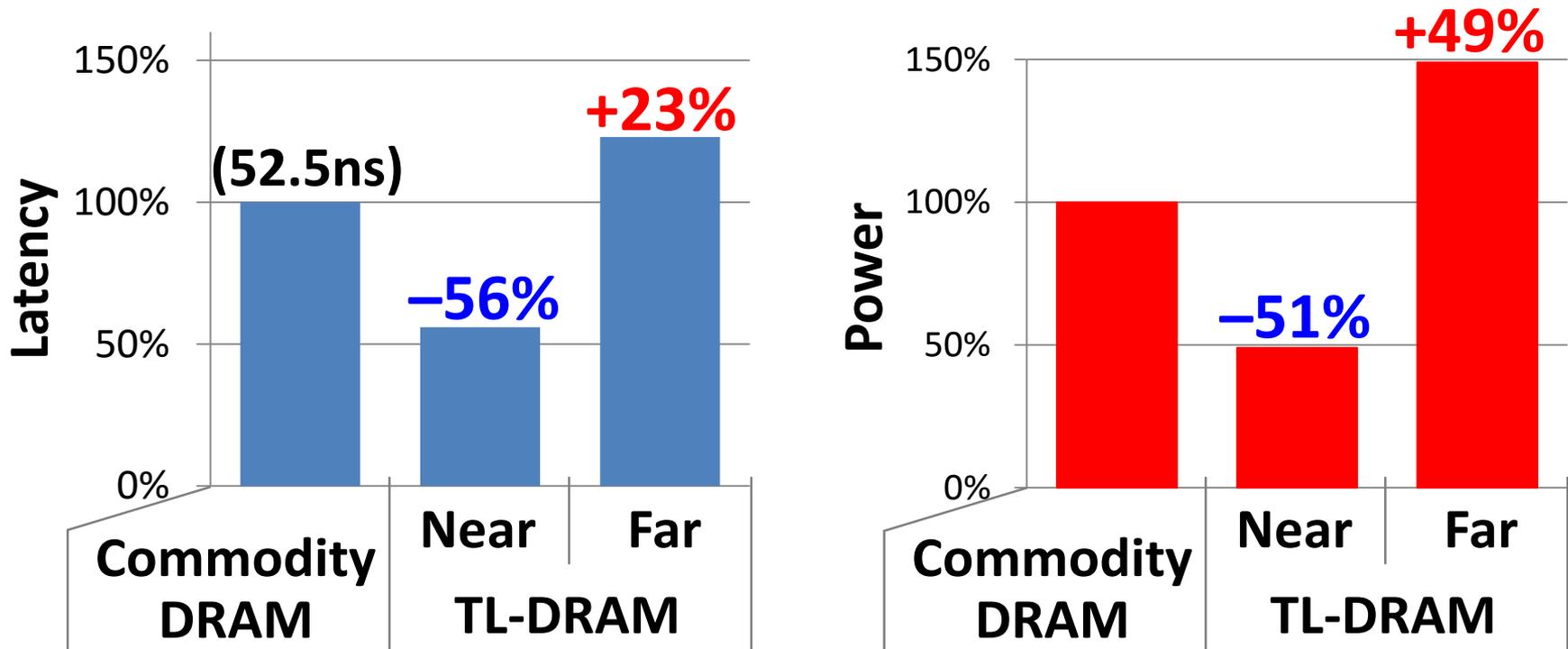
Low Latency

Low Latency



Commodity DRAM vs. TL-DRAM [HPCA 2013]

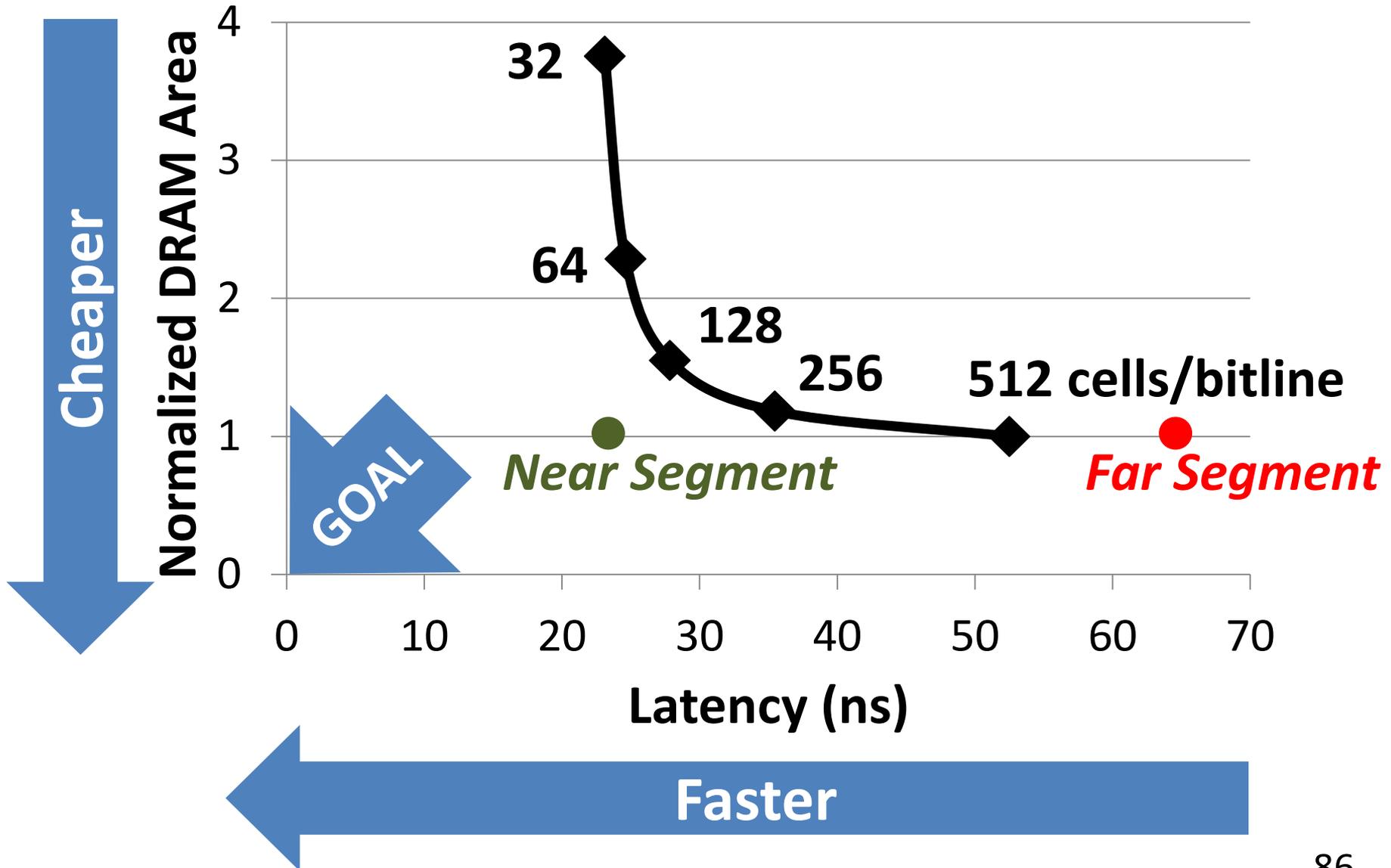
- DRAM Latency (tRC) • DRAM Power



- DRAM Area Overhead

~3%: mainly due to the isolation transistors

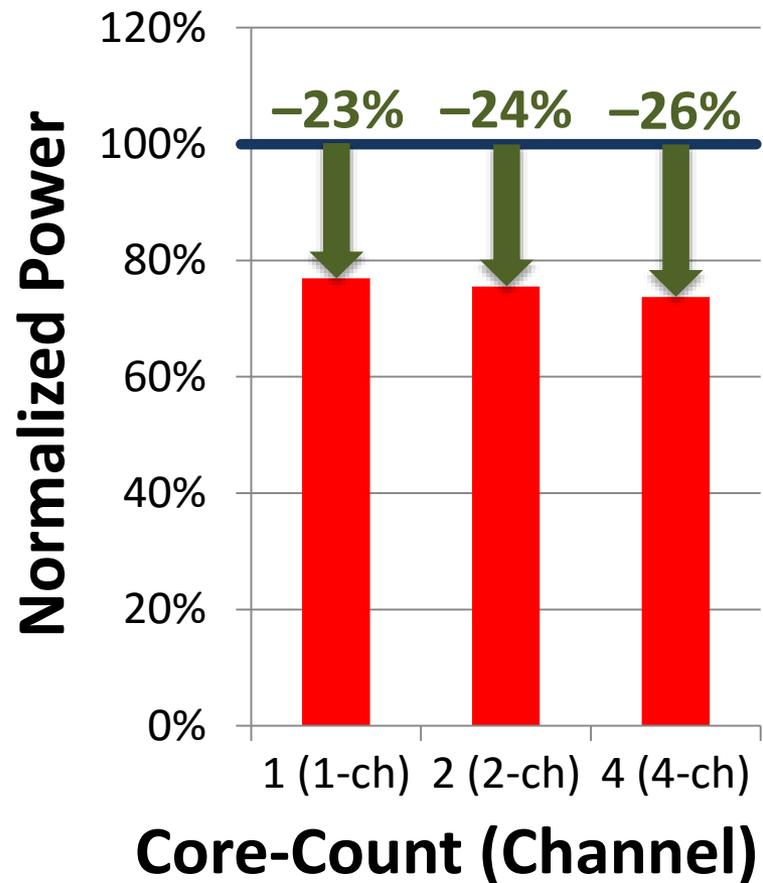
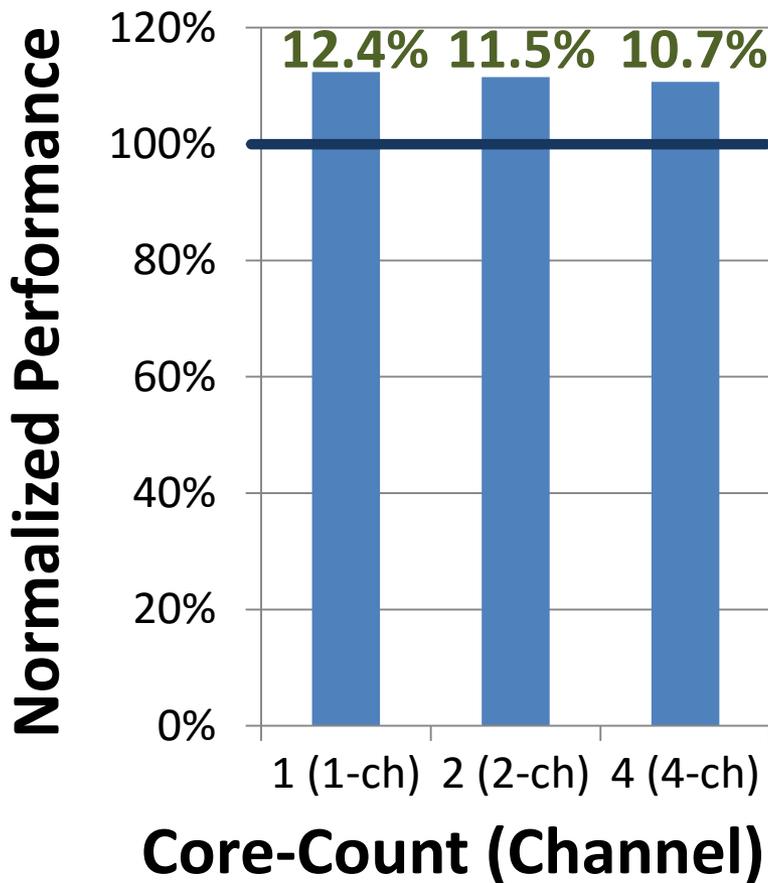
Trade-Off: Area (Die-Area) vs. Latency



Leveraging Tiered-Latency DRAM

- TL-DRAM is a *substrate* that can be leveraged by the hardware and/or software
- Many potential uses
 1. Use near segment as hardware-managed *inclusive* cache to far segment
 2. Use near segment as hardware-managed *exclusive* cache to far segment
 3. Profile-based page mapping by operating system
 4. Simply replace DRAM with TL-DRAM

Performance & Power Consumption



Using near segment as a cache improves performance and reduces power consumption

What Else Causes the Long DRAM Latency?

- **Conservative timing margins!**
- DRAM timing parameters are set to cover the worst case
- **Worst-case temperatures**
 - 85 degrees vs. common-case
 - to enable a wide range of operating conditions
- **Worst-case devices**
 - DRAM cell with smallest charge across any acceptable device
 - to tolerate process variation at acceptable yield
- This leads to large timing margins for the common case

Adaptive-Latency DRAM [HPCA 2015]

- Idea: Optimize DRAM timing for the common case
 - Current temperature
 - Current DRAM module
- Why would this reduce latency?
 - A DRAM cell can store much more charge in the common case (low temperature, strong cell) than in the worst case
 - More charge in a DRAM cell
 - Faster sensing, charge restoration, precharging
 - Faster access (read, write, refresh, ...)

AL-DRAM

- *Key idea*
 - Optimize DRAM timing parameters online
- *Two components*
 - DRAM manufacturer provides multiple sets of **reliable DRAM timing parameters** at different temperatures for each DIMM
 - System monitors **DRAM temperature** & uses appropriate DRAM timing parameters

Latency Reduction Summary of 115 DIMMs

- *Latency reduction for read & write (55°C)*
 - *Read Latency: 32.7%*
 - *Write Latency: 55.1%*
- *Latency reduction for each timing parameter (55°C)*
 - *Sensing: 17.3%*
 - *Restore: 37.3% (read), 54.8% (write)*
 - *Precharge: 35.2%*

AL-DRAM: Real System Evaluation

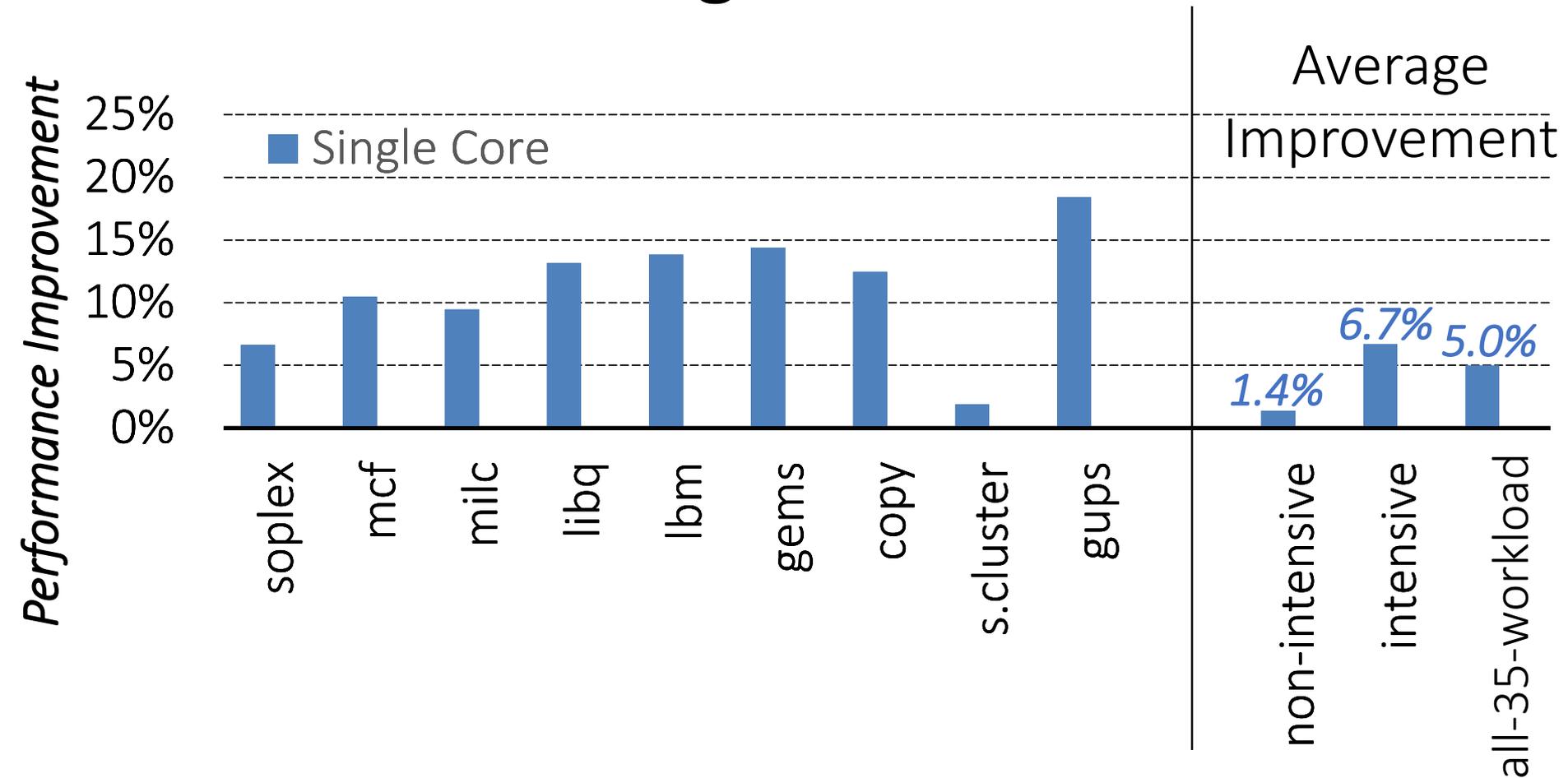
- *System*
 - CPU: AMD 4386 (8 Cores, 3.1GHz, 8MB LLC)

D18F2x200_dct[0]_mp[1:0] DDR3 DRAM Timing 0

Reset: 0F05_0505h. See 2.9.3 [DCT Configuration Registers].

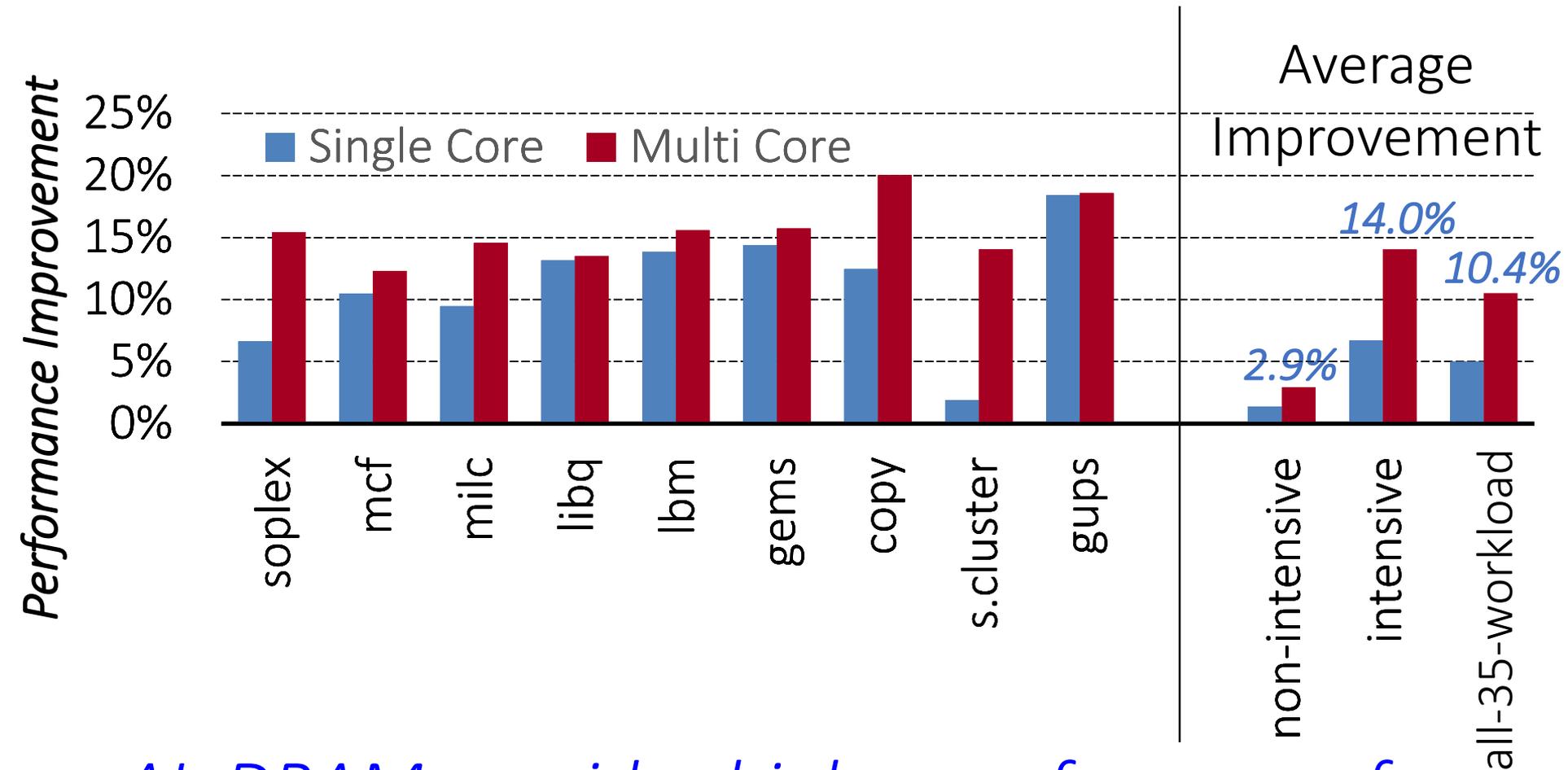
Bits	Description								
31:30	Reserved.								
29:24	Tras: row active strobe. Read-write. BIOS: See 2.9.7.5 [SPD ROM-Based Configuration]. Specifies the minimum time in memory clock cycles from an activate command to a precharge command, both to the same chip select bank. <table><thead><tr><th><u>Bits</u></th><th><u>Description</u></th></tr></thead><tbody><tr><td>07h-00h</td><td>Reserved</td></tr><tr><td>2Ah-08h</td><td><Tras> clocks</td></tr><tr><td>3Fh-2Bh</td><td>Reserved</td></tr></tbody></table>	<u>Bits</u>	<u>Description</u>	07h-00h	Reserved	2Ah-08h	<Tras> clocks	3Fh-2Bh	Reserved
<u>Bits</u>	<u>Description</u>								
07h-00h	Reserved								
2Ah-08h	<Tras> clocks								
3Fh-2Bh	Reserved								
23:21	Reserved.								
20:16	Trp: row precharge time. Read-write. BIOS: See 2.9.7.5 [SPD ROM-Based Configuration]. Specifies the minimum time in memory clock cycles from a precharge command to an activate command or auto refresh command, both to the same bank.								

AL-DRAM: Single-Core Evaluation



AL-DRAM improves performance on a real system

AL-DRAM: Multi-Core Evaluation



AL-DRAM provides higher performance for multi-programmed & multi-threaded workloads

Rethinking DRAM

- In-Memory Computation
- Refresh
- Reliability
- Latency
- Bandwidth
- Energy
- Memory Compression

Agenda

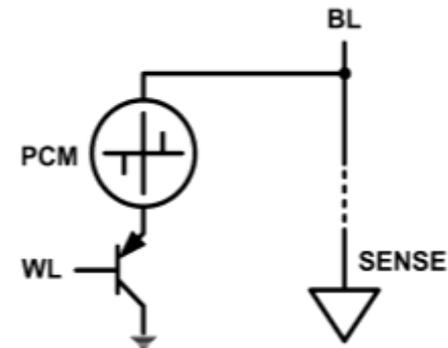
- Major Trends Affecting Main Memory
- The Memory Scaling Problem and Solution Directions
 - New Memory Architectures
 - Enabling Emerging Technologies
- How Can We Do Better?
- Summary

Solution 2: Emerging Memory Technologies

- Some emerging resistive memory technologies seem more scalable than DRAM (and they are non-volatile)

- Example: Phase Change Memory

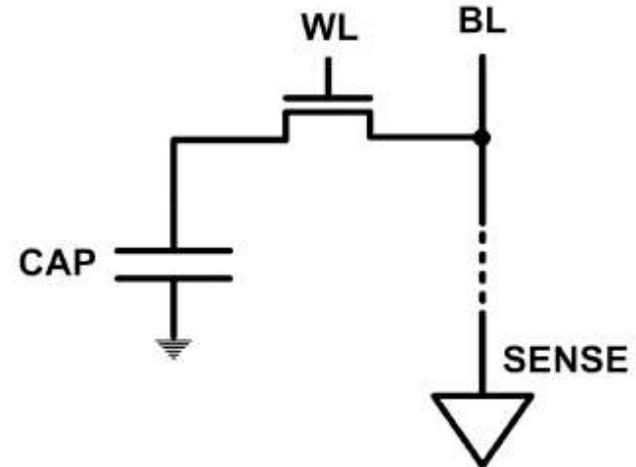
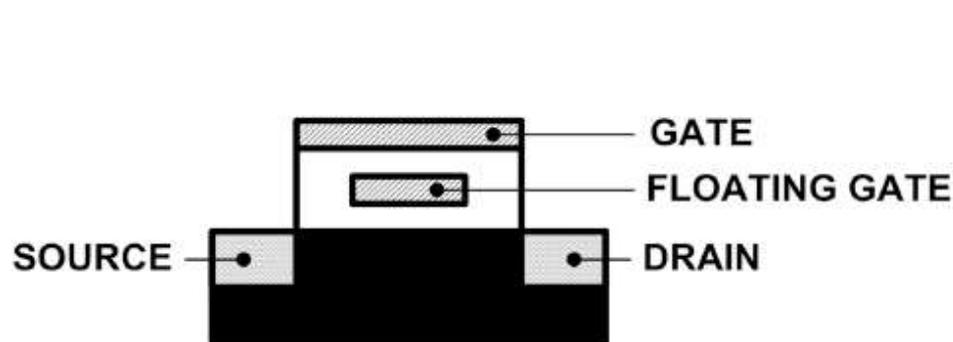
- Data stored by changing phase of material
- Data read by detecting material's resistance
- Expected to scale to 9nm (2022 [ITRS])
- Prototyped at 20nm (Raoux+, IBM JRD 2008)
- Expected to be denser than DRAM: can store multiple bits/cell



- But, emerging technologies have (many) shortcomings
 - Can they be enabled to replace/augment/surpass DRAM?

Limits of Charge Memory

- Difficult charge placement and control
 - Flash: floating gate charge
 - DRAM: capacitor charge, transistor leakage
- Reliable sensing becomes difficult as charge storage unit size reduces



Promising Resistive Memory Technologies

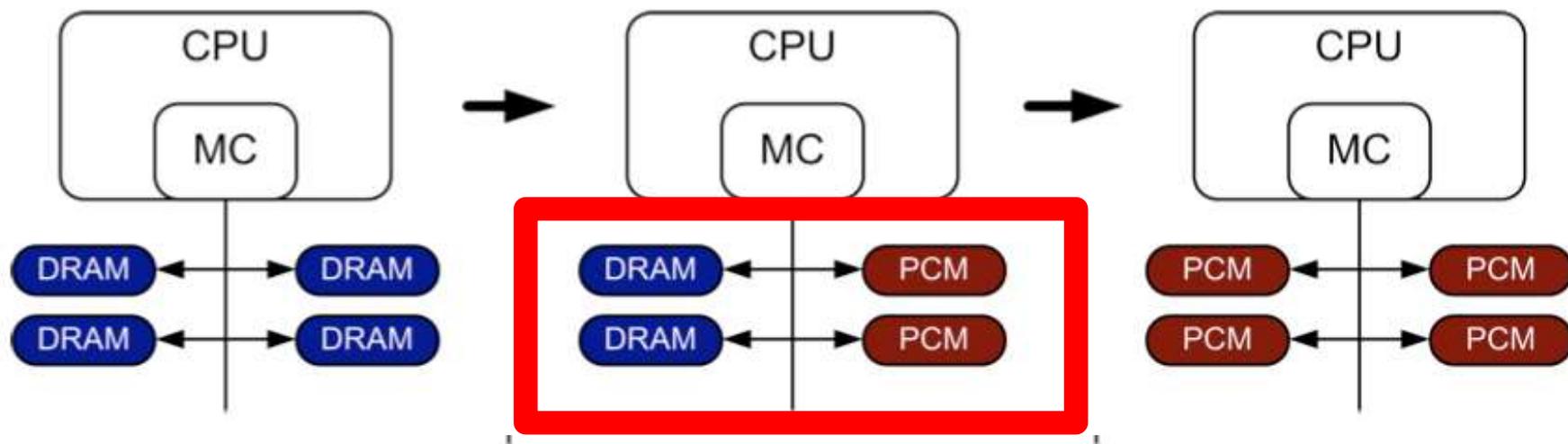
- PCM
 - Inject current to change **material phase**
 - Resistance determined by phase
- STT-MRAM
 - Inject current to change **magnet polarity**
 - Resistance determined by polarity
- Memristors/RRAM/ReRAM
 - Inject current to change **atomic structure**
 - Resistance determined by atom distance

Phase Change Memory: Pros and Cons

- Pros over DRAM
 - Better technology scaling (capacity and cost)
 - Non volatility
 - Low idle power (no refresh)
- Cons
 - Higher latencies: $\sim 4\text{-}15\times$ DRAM (especially write)
 - Higher active energy: $\sim 2\text{-}50\times$ DRAM (especially write)
 - Lower endurance (a cell dies after $\sim 10^8$ writes)
 - Reliability issues (resistance drift)
- Challenges in enabling PCM as DRAM replacement/helper:
 - Mitigate PCM shortcomings
 - Find the right way to place PCM in the system

PCM-based Main Memory (I)

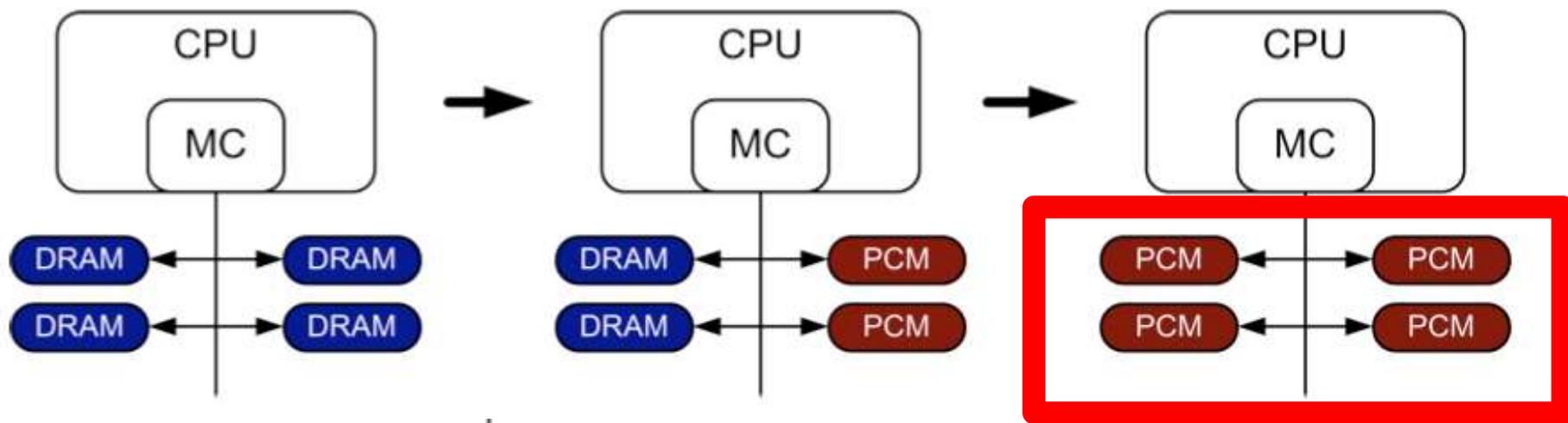
- How should PCM-based (main) memory be organized?



- **Hybrid PCM+DRAM** [Qureshi+ ISCA'09, Dhiman+ DAC'09]:
 - How to partition/migrate data between PCM and DRAM

PCM-based Main Memory (II)

- How should PCM-based (main) memory be organized?



- **Pure PCM main memory** [Lee et al., ISCA'09, Top Picks'10]:
 - How to redesign entire hierarchy (and cores) to overcome PCM shortcomings

An Initial Study: Replace DRAM with PCM

- Lee, Ipek, Mutlu, Burger, “Architecting Phase Change Memory as a Scalable DRAM Alternative,” ISCA 2009.
 - Surveyed prototypes from 2003-2008 (e.g. IEDM, VLSI, ISSCC)
 - Derived “average” PCM parameters for F=90nm

Density

- ▷ 9 - 12F² using BJT
- ▷ 1.5× DRAM

Latency

- ▷ 50ns Rd, 150ns Wr
- ▷ 4×, 12× DRAM

Endurance

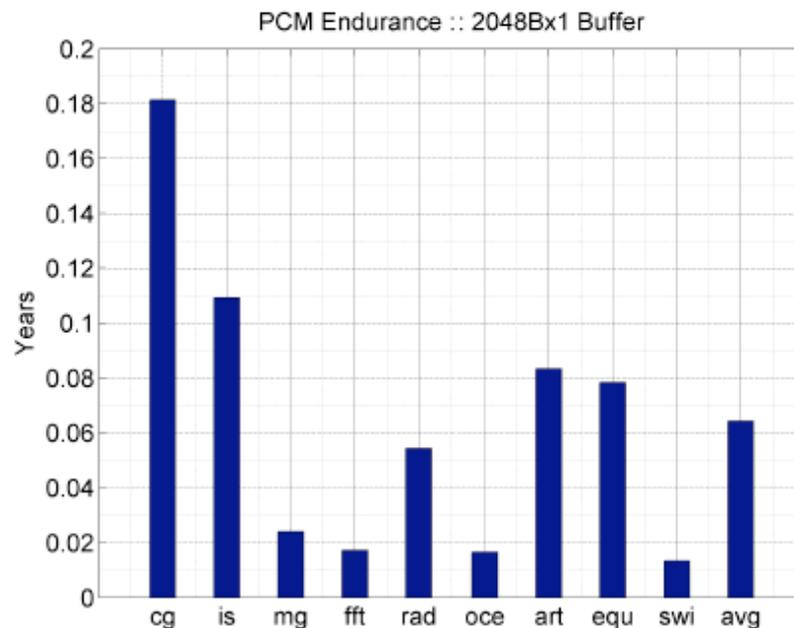
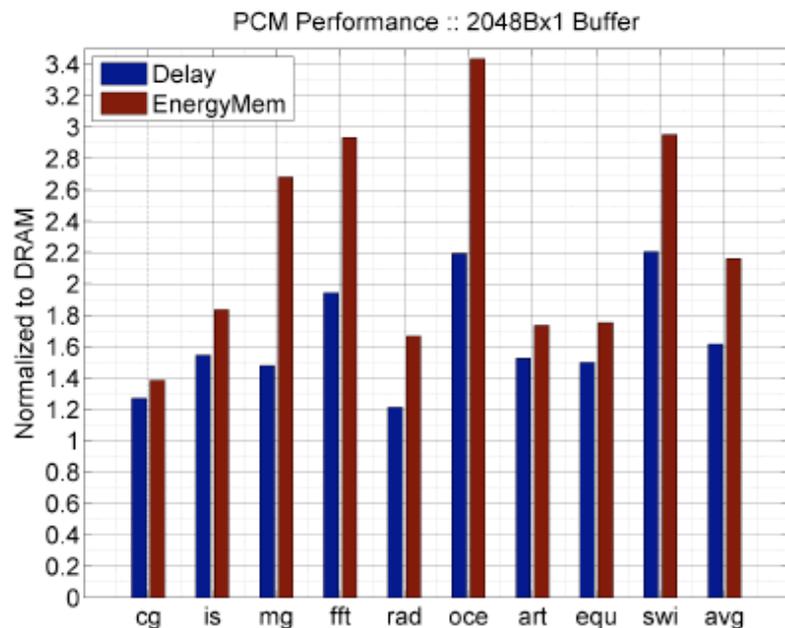
- ▷ 1E+08 writes
- ▷ 1E-08× DRAM

Energy

- ▷ 40μA Rd, 150μA Wr
- ▷ 2×, 43× DRAM

Results: Naïve Replacement of DRAM with PCM

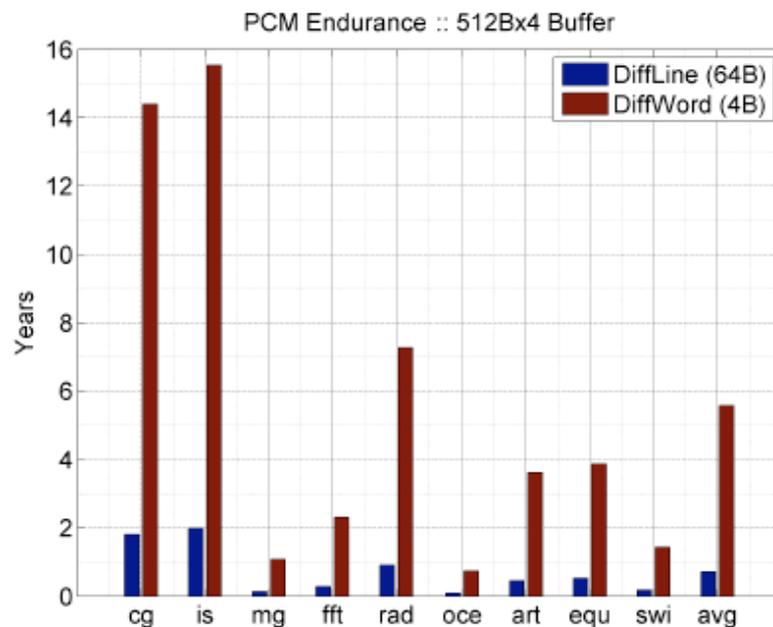
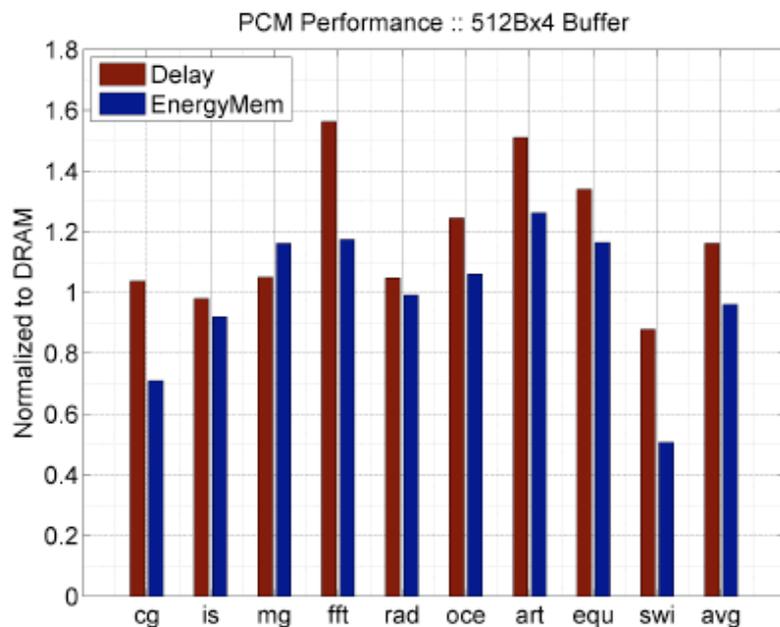
- Replace DRAM with PCM in a 4-core, 4MB L2 system
- PCM organized the same as DRAM: row buffers, banks, peripherals
- 1.6x delay, 2.2x energy, 500-hour average lifetime



- Lee, Ipek, Mutlu, Burger, “Architecting Phase Change Memory as a Scalable DRAM Alternative,” ISCA 2009.

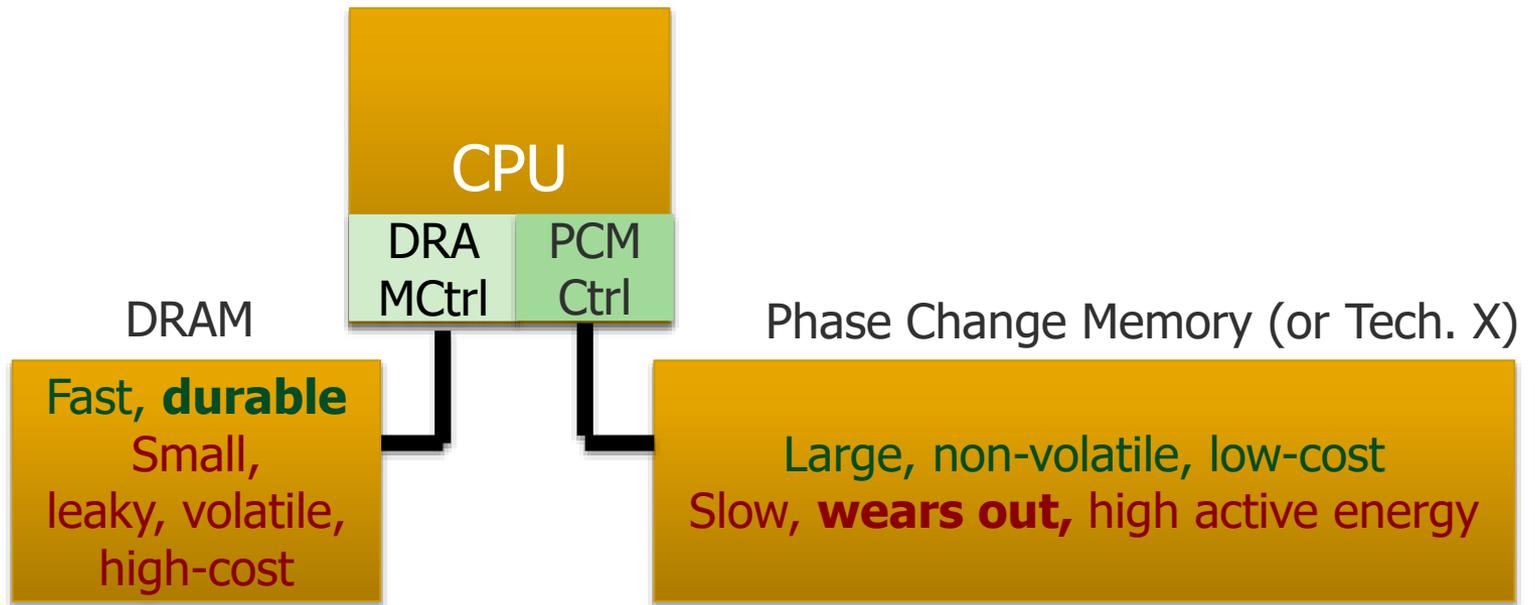
Results: Architected PCM as Main Memory

- 1.2x delay, 1.0x energy, 5.6-year average lifetime
- Scaling improves energy, endurance, density



- Caveat 1: Worst-case lifetime is much shorter (no guarantees)
- Caveat 2: Intensive applications see large performance and energy hits
- Caveat 3: Optimistic PCM parameters?

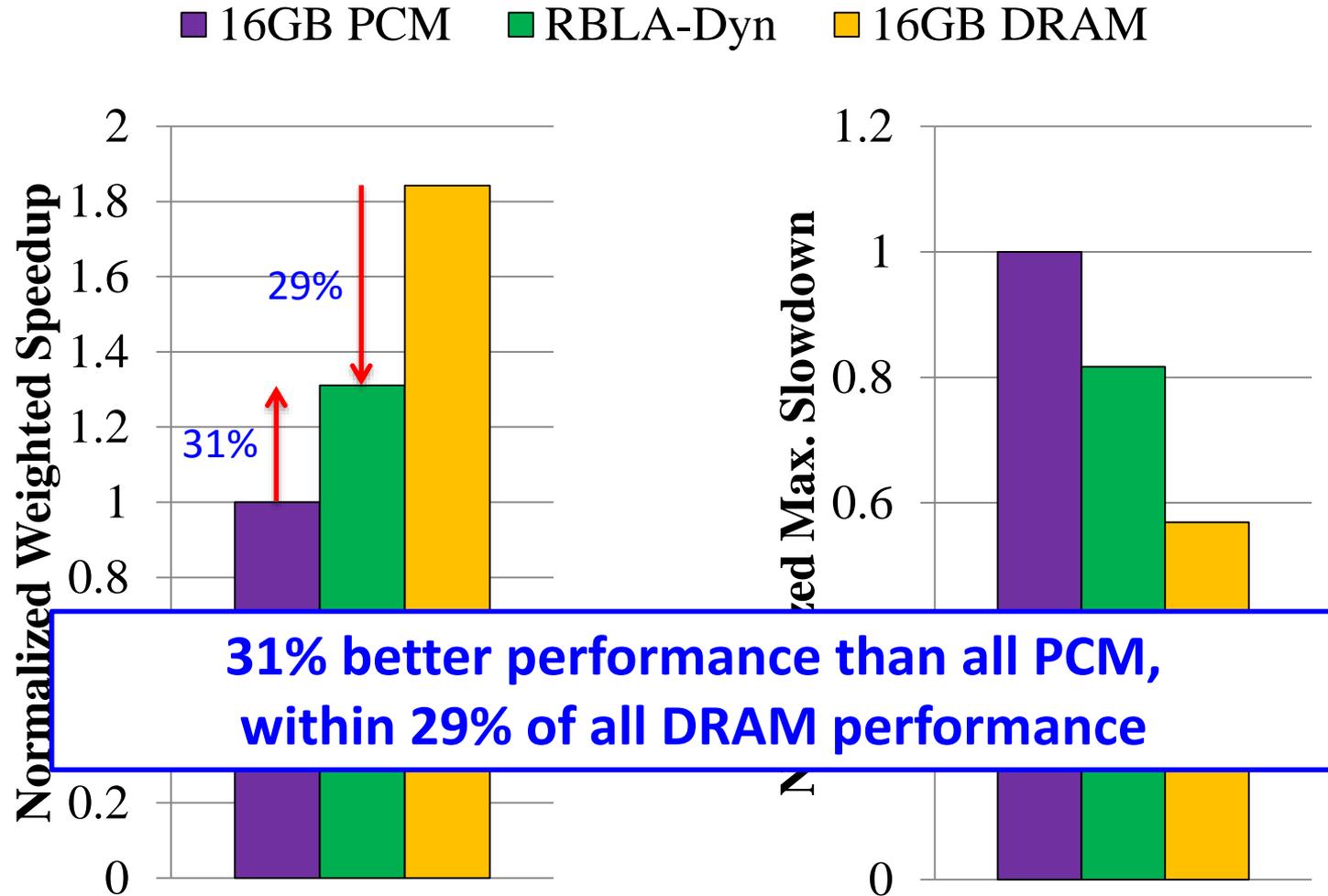
Solution 3: Hybrid Memory Systems



Hardware/software manage data allocation and movement
to achieve the best of multiple technologies

Meza+, "Enabling Efficient and Scalable Hybrid Memories," IEEE Comp. Arch. Letters, 2012.
Yoon+, "Row Buffer Locality Aware Caching Policies for Hybrid Memories," ICCD 2012 Best Paper Award.

Hybrid vs. All-PCM/DRAM [ICCD'12]



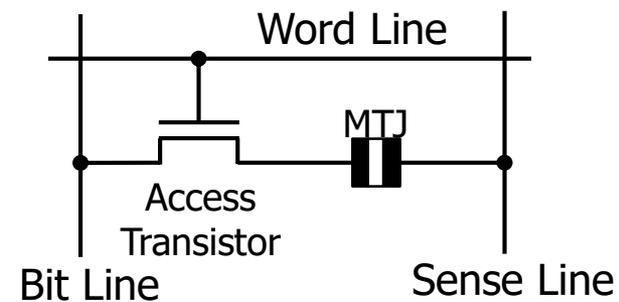
STT-MRAM as Main Memory

- Magnetic Tunnel Junction (MTJ) device
 - Reference layer: Fixed magnetic orientation
 - Free layer: Parallel or anti-parallel
- Magnetic orientation of the free layer determines logical state of device
 - High vs. low resistance
- Write: Push large current through MTJ to change orientation of free layer
- Read: Sense current flow
- Kultursay et al., "Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative," ISPASS 2013.

Logical 0



Logical 1

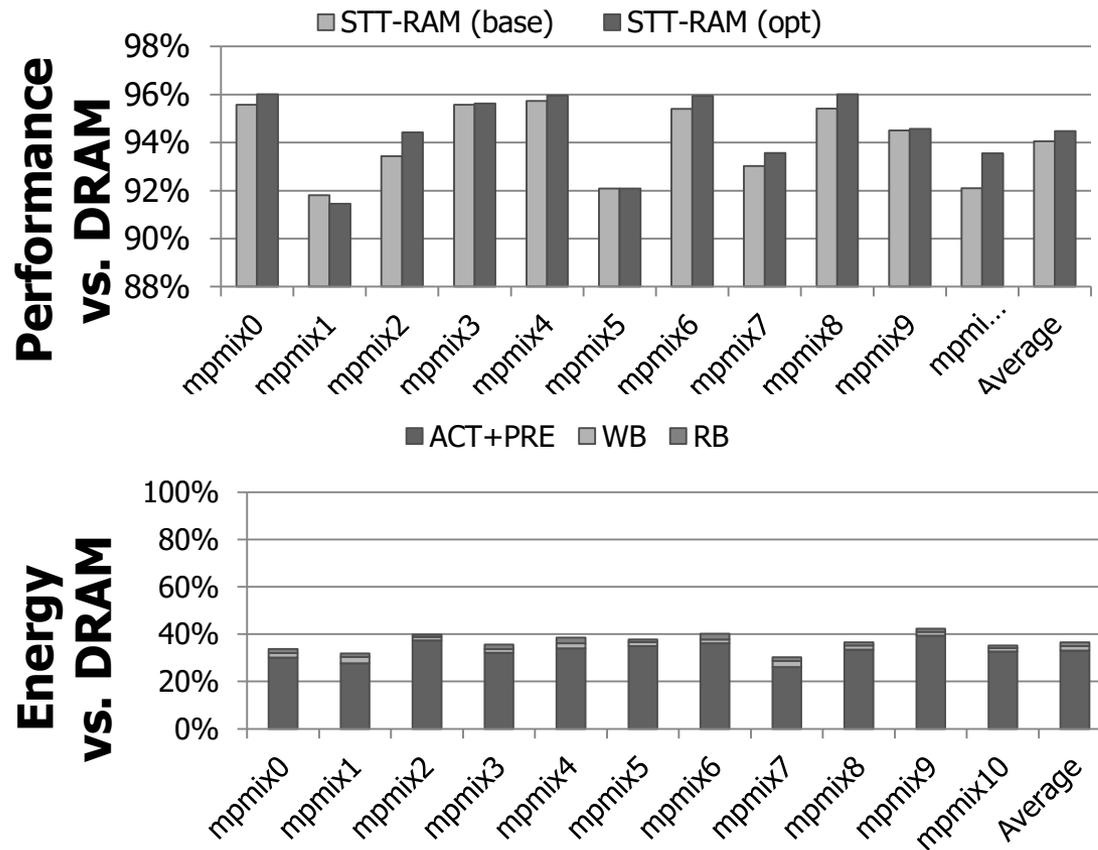


STT-MRAM: Pros and Cons

- Pros over DRAM
 - Better technology scaling
 - Non volatility
 - Low idle power (no refresh)
- Cons
 - Higher write latency
 - Higher write energy
 - Reliability?
- Another level of freedom
 - Can trade off non-volatility for lower write latency/energy (by reducing the size of the MTJ)

Architected STT-MRAM as Main Memory

- 4-core, 4GB main memory, multiprogrammed workloads
- ~6% performance loss, ~60% energy savings vs. DRAM



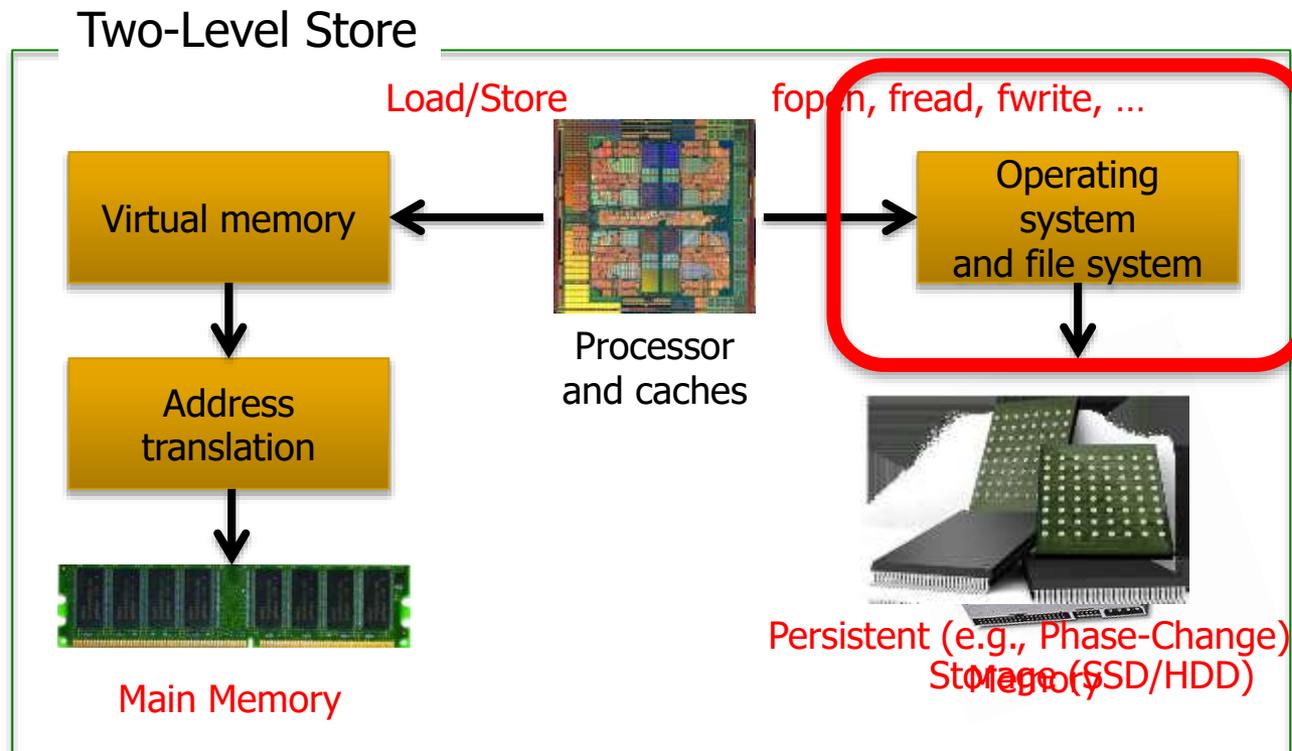
Kultursay+, "Evaluating STT-RAM as an Energy-Efficient Main Memory Alternative," ISPASS 2013.

Other Opportunities with Emerging Technologies

- **Merging of memory and storage**
 - e.g., a single interface to manage all data
- **New applications**
 - e.g., ultra-fast checkpoint and restore
- **More robust system design**
 - e.g., reducing data loss
- **Processing tightly-coupled with memory**
 - e.g., enabling efficient search and filtering

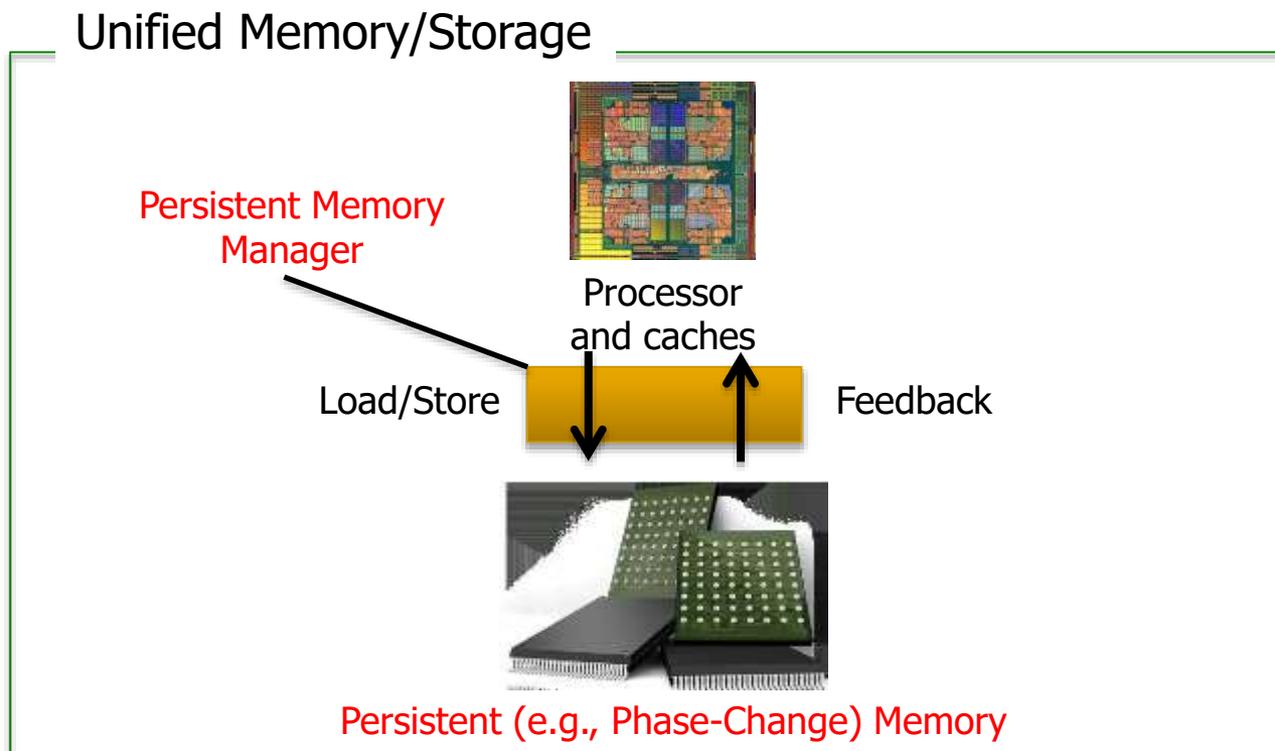
Coordinated Memory and Storage with NVM (I)

- The traditional two-level storage model is a bottleneck with NVM
 - **Volatile** data in memory → a **load/store** interface
 - **Persistent** data in storage → a **file system** interface
 - Problem: Operating system (OS) and file system (FS) code to locate, translate, buffer data become performance and energy bottlenecks with fast NVM stores



Coordinated Memory and Storage with NVM (II)

- Goal: Unify memory and storage management in a single unit to eliminate wasted work to locate, transfer, and translate data
 - Improves both energy and performance
 - Simplifies programming model as well



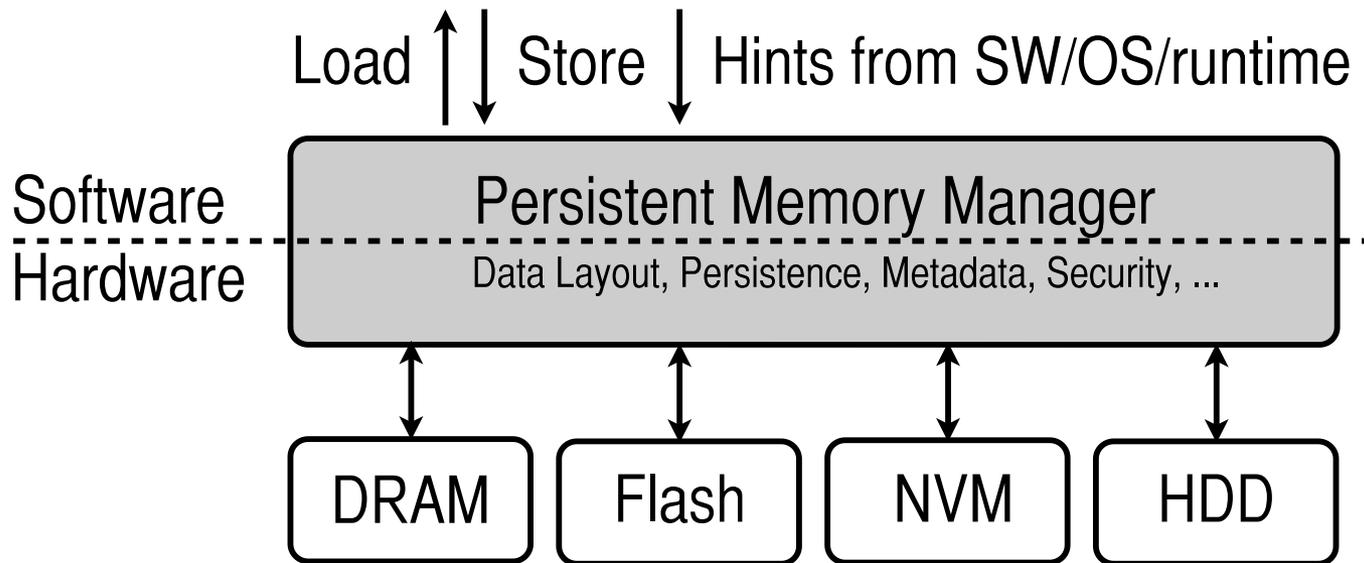
The Persistent Memory Manager (PMM)

- Exposes a load/store interface to access persistent data
 - Applications can directly access persistent memory → no conversion, translation, location overhead for persistent data
- Manages data placement, location, persistence, security
 - To get the best of multiple forms of storage
- Manages metadata storage and retrieval
 - This can lead to overheads that need to be managed
- Exposes hooks and interfaces for system software
 - To enable better data placement and management decisions
- Meza+, “A Case for Efficient Hardware-Software Cooperative Management of Storage and Memory,” WEED 2013.

The Persistent Memory Manager (PMM)

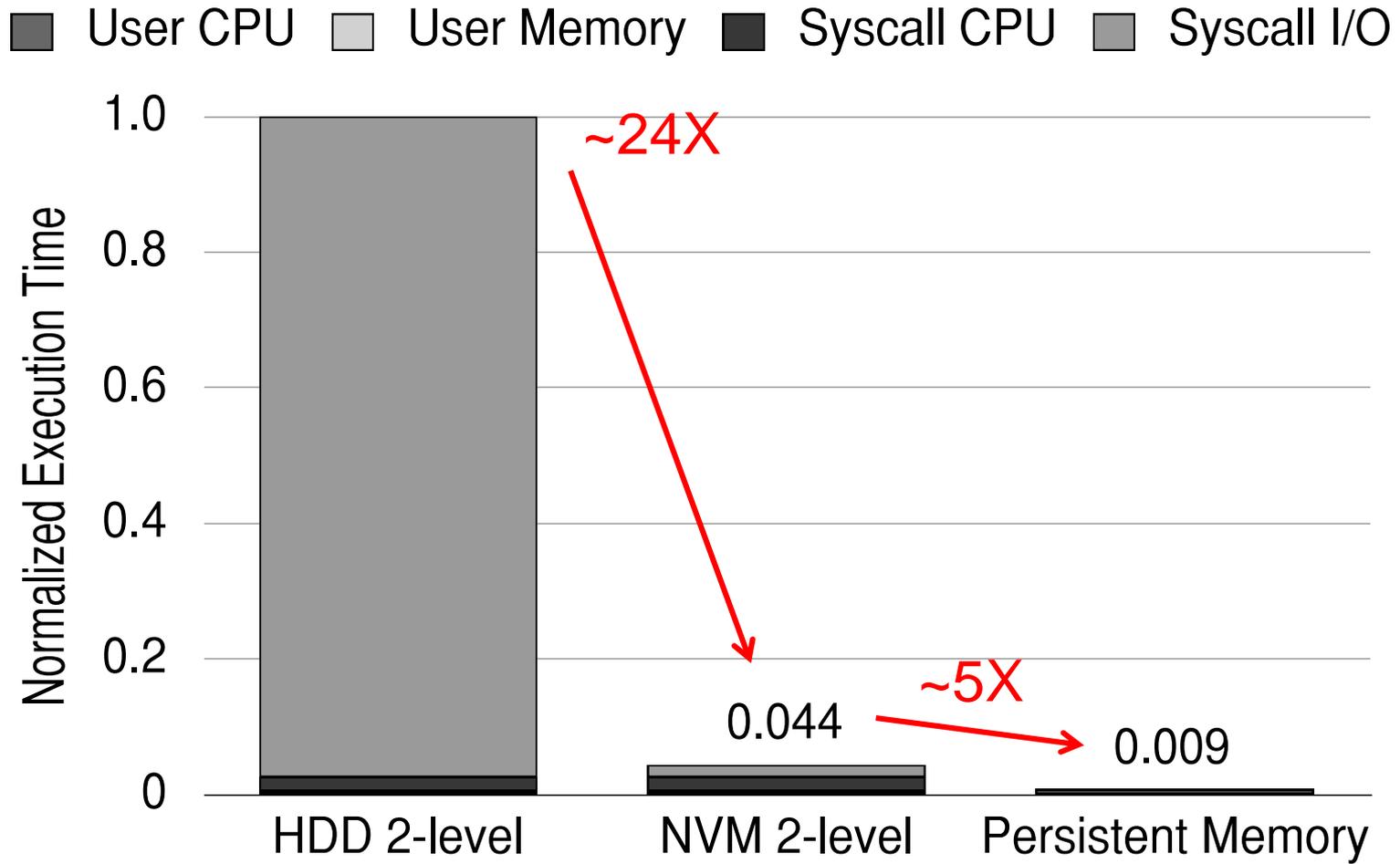
```
1 int main(void) {  
2     // data in file.dat is persistent  
3     FILE myData = "file.dat";  
4     myData = new int[64];  
5 }  
6 void updateValue(int n, int value) {  
7     FILE myData = "file.dat";  
8     myData[n] = value; // value is persistent  
9 }
```

Persistent objects

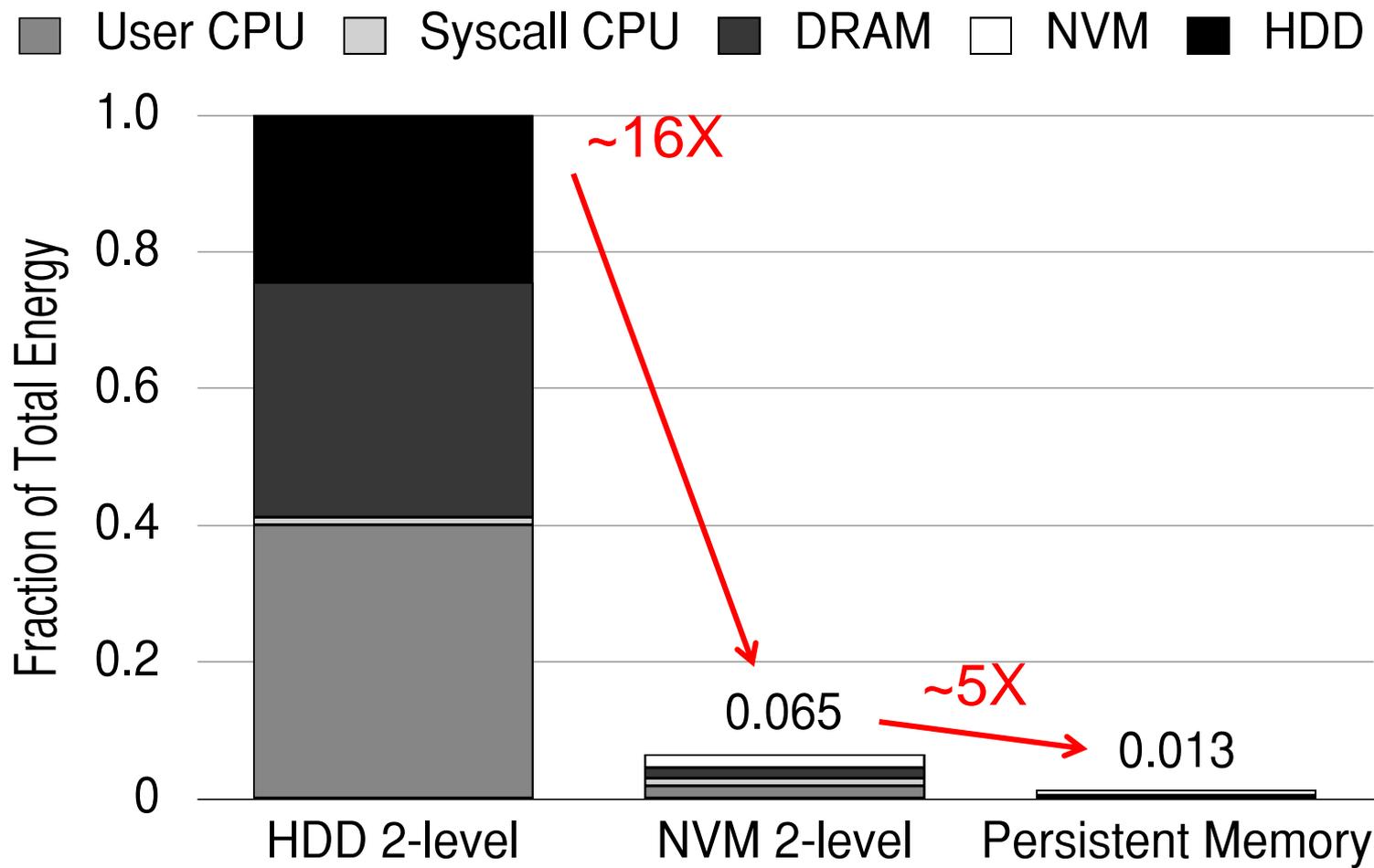


PMM uses access and hint information to allocate, locate, migrate and access data in the heterogeneous array of devices

Performance Benefits of a Single-Level Store



Energy Benefits of a Single-Level Store



Agenda

- Major Trends Affecting Main Memory
- The Memory Scaling Problem and Solution Directions
 - New Memory Architectures
 - Enabling Emerging Technologies
- How Can We Do Better?
- Summary

Principles (So Far)

- Better cooperation between devices and the system
 - Expose more information about devices to upper layers
 - More flexible interfaces
- Better-than-worst-case design
 - Do not optimize for the worst case
 - Worst case should not determine the common case
- Heterogeneity in design (specialization, asymmetry)
 - Enables a more efficient design (No one size fits all)
- These principles are coupled

Agenda

- Major Trends Affecting Main Memory
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 - New Memory Architectures
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- How Can We Do Better?
- Summary

Summary: Memory Scaling

- Memory scaling problems are a critical bottleneck for system performance, efficiency, and usability
- New memory architectures
 - **A lot of hope in fixing DRAM**
- Enabling emerging NVM technologies
 - **A lot of hope in hybrid memory systems and single-level stores**
- System-level memory/storage QoS
 - **A lot of hope in designing a predictable system**
- Three principles are essential for scaling
 - Software/hardware/device cooperation
 - Better-than-worst-case design
 - Heterogeneity (specialization, asymmetry)

Acknowledgments

■ My current and past students and postdocs

- Rachata Ausavarungnirun, Abhishek Bhowmick, Amirali Boroumand, Rui Cai, Yu Cai, Kevin Chang, Saugata Ghose, Kevin Hsieh, Tyler Huberty, Ben Jaiyen, Samira Khan, Jeremie Kim, Yoongu Kim, Yang Li, Jamie Liu, Lavanya Subramanian, Donghyuk Lee, Yixin Luo, Justin Meza, Gennady Pekhimenko, Vivek Seshadri, Lavanya Subramanian, Nandita Vijaykumar, HanBin Yoon, Jishen Zhao, ...

■ My collaborators at CMU

- Greg Ganger, Phil Gibbons, Mor Harchol-Balter, James Hoe, Mike Kozuch, Ken Mai, Todd Mowry, ...

■ My collaborators elsewhere

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- AMD, Google, Facebook, HP Labs, Huawei, IBM, Intel, Microsoft, Nvidia, Oracle, Qualcomm, Rambus, Samsung, Seagate, VMware

Open Source Tools

- Rowhammer

- <https://github.com/CMU-SAFARI/rowhammer>

- Ramulator

- <https://github.com/CMU-SAFARI/ramulator>

- MemSim

- <https://github.com/CMU-SAFARI/memsim>

- NOCulator

- <https://github.com/CMU-SAFARI/NOCulator>

- DRAM Error Model

- <http://www.ece.cmu.edu/~safari/tools/memerr/index.html>

- Other open-source software from my group

- <https://github.com/CMU-SAFARI/>

- <http://www.ece.cmu.edu/~safari/tools.html>

Referenced Papers

- All are available at
<http://users.ece.cmu.edu/~omutlu/projects.htm>
<http://scholar.google.com/citations?user=7XyGUGkAAAAJ&hl=en>
- A detailed accompanying overview paper
 - Onur Mutlu and Lavanya Subramanian,
"Research Problems and Opportunities in Memory Systems"
Invited Article in Supercomputing Frontiers and Innovations (SUPERFRI), 2015.

Related Videos and Course Materials

- **Undergraduate Computer Architecture Course Lecture Videos (2013, 2014, 2015)**
- **Undergraduate Computer Architecture Course Materials (2013, 2014, 2015)**
- **Graduate Computer Architecture Course Materials (Lecture Videos)**
- **Parallel Computer Architecture Course Materials (Lecture Videos)**
- **Memory Systems Short Course Materials (Lecture Video on Main Memory and DRAM Basics)**

Thank you.

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Rethinking Memory System Design (for Data-Intensive Computing)

Onur Mutlu

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<http://users.ece.cmu.edu/~omutlu/>

October 21, 2015

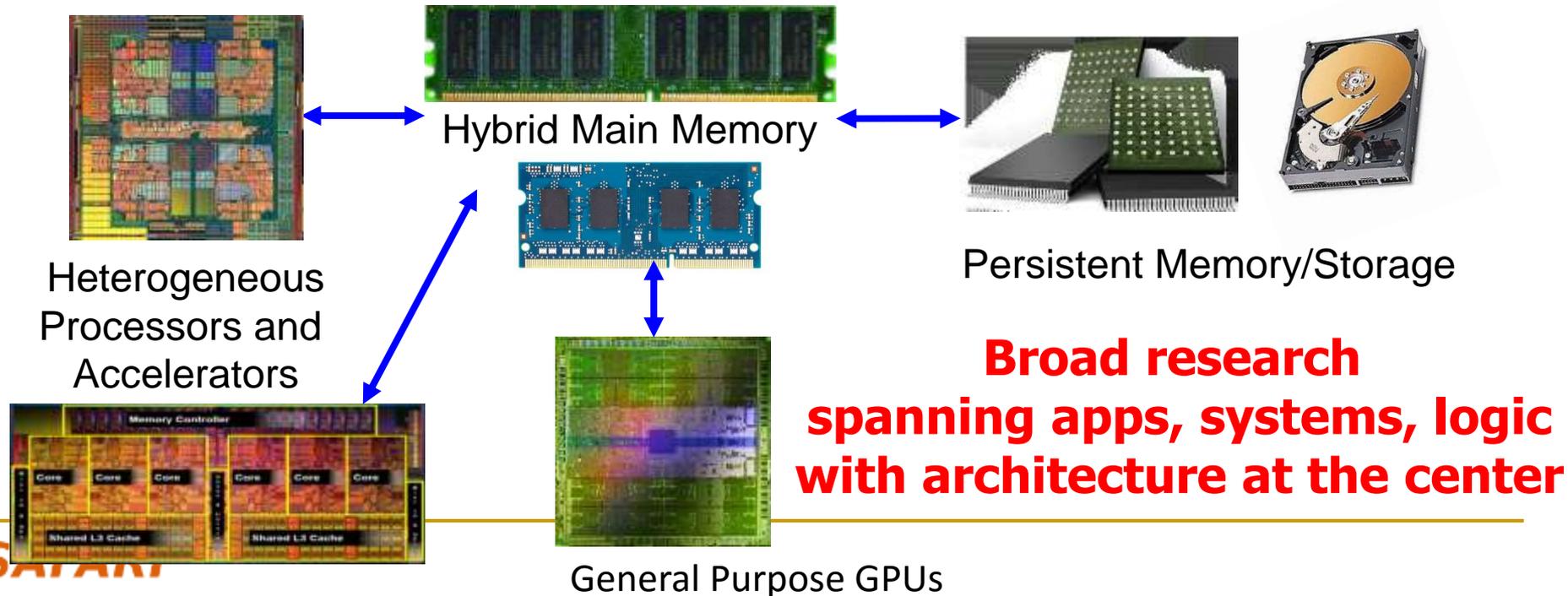
SBAC-PAD 2015 Keynote

Carnegie Mellon

Current Research Focus Areas

Research Focus: Computer architecture, HW/SW, bioinformatics

- **Memory, memory, memory, storage, interconnects**
- Parallel architectures, heterogeneous architectures, GP-GPUs
- System/architecture interaction, new execution models
- Energy efficiency, fault tolerance, hardware security
- Genome sequence analysis & assembly algorithms and architectures



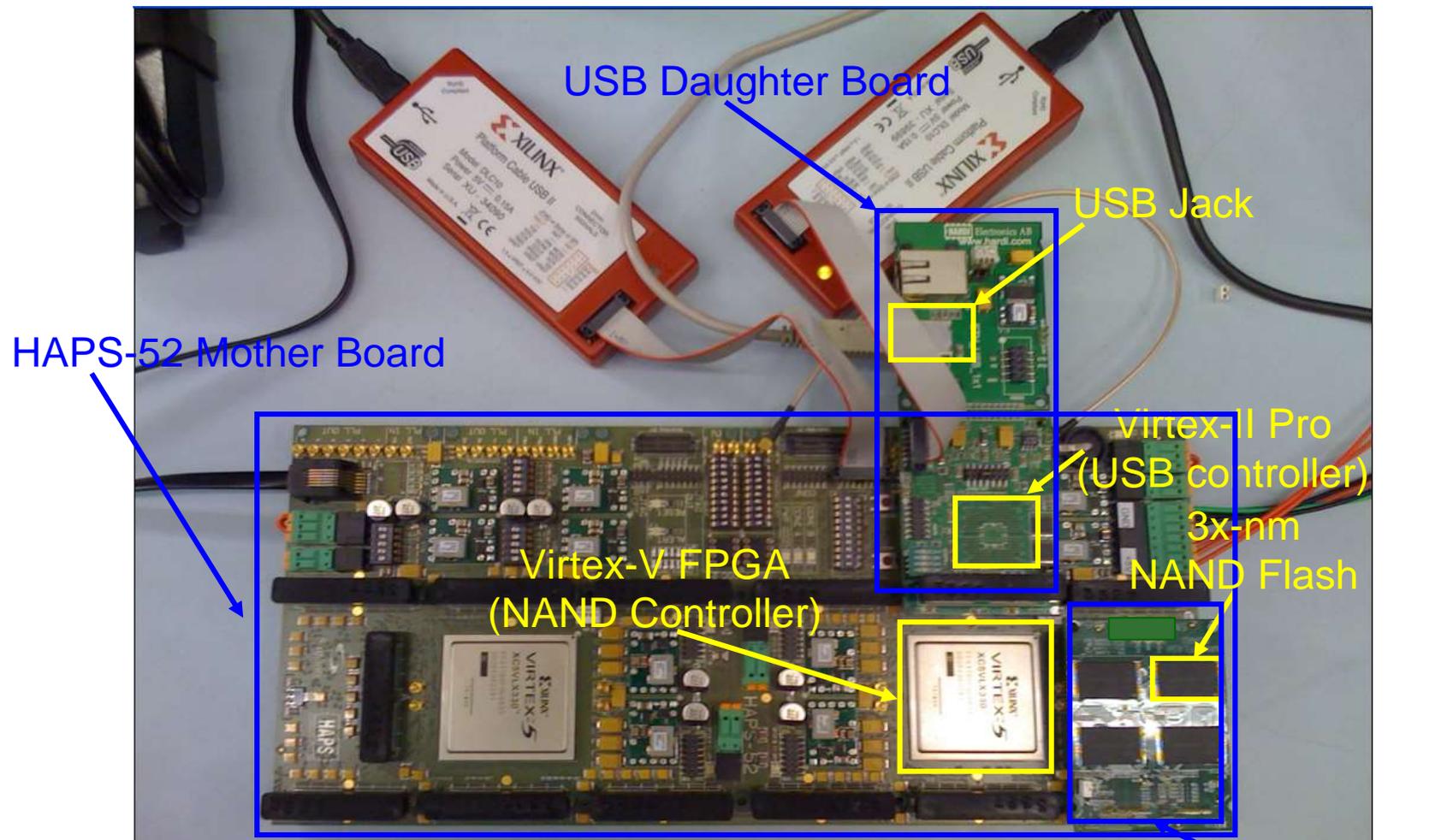
Backup Slides

NAND Flash Memory Scaling

Another Talk: NAND Flash Scaling Challenges

- Onur Mutlu,
"Error Analysis and Management for MLC NAND Flash Memory"
Technical talk at Flash Memory Summit 2014 (FMS), Santa Clara, CA, August 2014. Slides (ppt) (pdf)
- Cai+, "Error Patterns in MLC NAND Flash Memory: Measurement, Characterization, and Analysis," DATE 2012.
- Cai+, "Flash Correct-and-Refresh: Retention-Aware Error Management for Increased Flash Memory Lifetime," ICCD 2012.
- Cai+, "Threshold Voltage Distribution in MLC NAND Flash Memory: Characterization, Analysis and Modeling," DATE 2013.
- Cai+, "Error Analysis and Retention-Aware Error Management for NAND Flash Memory," Intel Technology Journal 2013.
- Cai+, "Program Interference in MLC NAND Flash Memory: Characterization, Modeling, and Mitigation," ICCD 2013.
- Cai+, "Neighbor-Cell Assisted Error Correction for MLC NAND Flash Memories," SIGMETRICS 2014.
- Cai+, "Data Retention in MLC NAND Flash Memory: Characterization, Optimization and Recovery," HPCA 2015.
- Cai+, "Read Disturb Errors in MLC NAND Flash Memory: Characterization and Mitigation," DSN 2015.
- Luo+, "WARM: Improving NAND Flash Memory Lifetime with Write-hotness Aware Retention Management," MSST 2015.
- Meza+, "A Large-Scale Study of Flash Memory Errors in the Field," SIGMETRICS 2015.

Experimental Infrastructure (Flash)



[Cai+, DATE 2012, ICCD 2012, DATE 2013, ITJ 2013, ICCD 2013, SIGMETRICS 2014, HPCA 2015, DSN 2015, MSST 2015]

NAND Daughter Board

- Problem: MLC NAND flash memory reliability/endurance is a key challenge for satisfying future storage systems' requirements
- Our Goals: (1) Build reliable error models for NAND flash memory via experimental characterization, (2) Develop efficient techniques to improve reliability and endurance
- This talk provides a “flash” summary of our recent results published in the past 3 years:
 - Experimental error and threshold voltage characterization [DATE'12&13]
 - Retention-aware error management [ICCD'12]
 - Program interference analysis and read reference V prediction [ICCD'13]
 - Neighbor-assisted error correction [SIGMETRICS'14]

Ramulator: A Fast and Extensible DRAM Simulator

[IEEE Comp Arch Letters'15]

Ramulator Motivation

- DRAM and Memory Controller landscape is changing
- Many new and upcoming standards
- Many new controller designs
- A fast and easy-to-extend simulator is very much needed

<i>Segment</i>	<i>DRAM Standards & Architectures</i>
Commodity	DDR3 (2007) [14]; DDR4 (2012) [18]
Low-Power	LPDDR3 (2012) [17]; LPDDR4 (2014) [20]
Graphics	GDDR5 (2009) [15]
Performance	eDRAM [28], [32]; RLD RAM3 (2011) [29]
3D-Stacked	WIO (2011) [16]; WIO2 (2014) [21]; MCDRAM (2015) [13]; HBM (2013) [19]; HMC1.0 (2013) [10]; HMC1.1 (2014) [11]
Academic	SBA/SSA (2010) [38]; Staged Reads (2012) [8]; RAIDR (2012) [27]; SALP (2012) [24]; TL-DRAM (2013) [26]; RowClone (2013) [37]; Half-DRAM (2014) [39]; Row-Buffer Decoupling (2014) [33]; SARP (2014) [6]; AL-DRAM (2015) [25]

Table 1. Landscape of DRAM-based memory

Ramulator

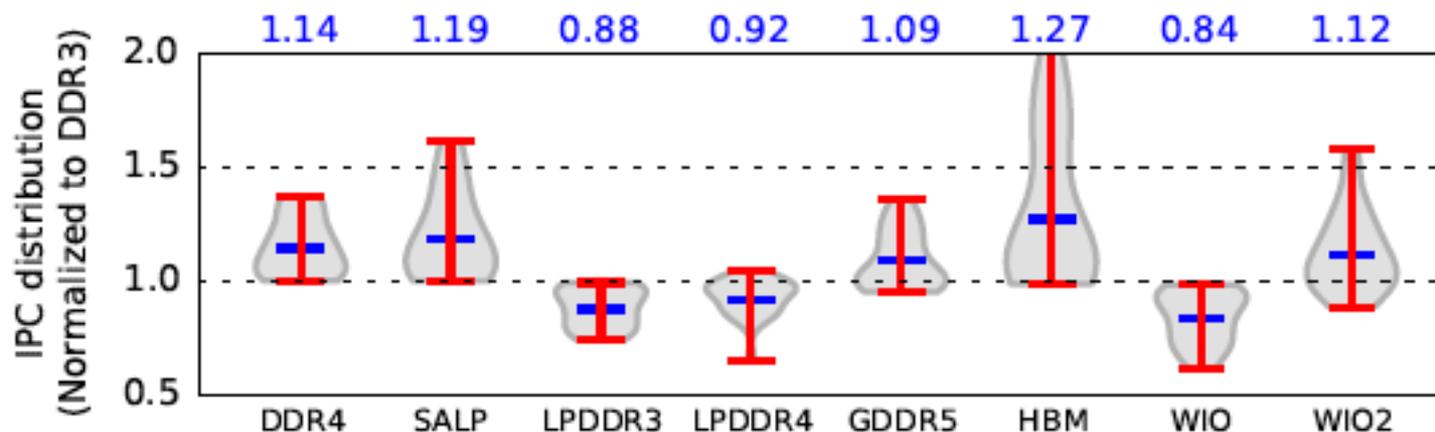
- Provides out-of-the box support for many DRAM standards:
 - DDR3/4, LPDDR3/4, GDDR5, WIO1/2, HBM, plus new proposals (SALP, AL-DRAM, TLDRAM, RowClone, and SARP)
- ~2.5X faster than fastest open-source simulator
- Modular and extensible to different standards

<i>Simulator</i> (<i>clang -O3</i>)	<i>Cycles (10⁶)</i>		<i>Runtime (sec.)</i>		<i>Req/sec (10³)</i>		<i>Memory</i> (<i>MB</i>)
	<i>Random</i>	<i>Stream</i>	<i>Random</i>	<i>Stream</i>	<i>Random</i>	<i>Stream</i>	
Ramulator	652	411	752	249	133	402	2.1
DRAMSim2	645	413	2,030	876	49	114	1.2
USIMM	661	409	1,880	750	53	133	4.5
DrSim	647	406	18,109	12,984	6	8	1.6
NVMain	666	413	6,881	5,023	15	20	4,230.0

Table 3. Comparison of five simulators using two traces

Case Study: Comparison of DRAM Standards

Standard	Rate (MT/s)	Timing (CL-RCD-RP)	Data-Bus (Width×Chan.)	Rank-per-Chan	BW (GB/s)
DDR3	1,600	11-11-11	64-bit × 1	1	11.9
DDR4	2,400	16-16-16	64-bit × 1	1	17.9
SALP [†]	1,600	11-11-11	64-bit × 1	1	11.9
LPDDR3	1,600	12-15-15	64-bit × 1	1	11.9
LPDDR4	2,400	22-22-22	32-bit × 2*	1	17.9
GDDR5 [12]	6,000	18-18-18	64-bit × 1	1	44.7
HBM	1,000	7-7-7	128-bit × 8*	1	119.2
WIO	266	7-7-7	128-bit × 4*	1	15.9
WIO2	1,066	9-10-10	128-bit × 8*	1	127.2



Across 22 workloads, simple CPU model

Figure 2. Performance comparison of DRAM standards

Ramulator Paper and Source Code

- Yoongu Kim, Weikun Yang, and Onur Mutlu,
"Ramulator: A Fast and Extensible DRAM Simulator"
IEEE Computer Architecture Letters (CAL), March 2015.
[Source Code]
- Source code is released under the liberal MIT License
 - <https://github.com/CMU-SAFARI/ramulator>

DRAM Infrastructure

Experimental DRAM Testing Infrastructure



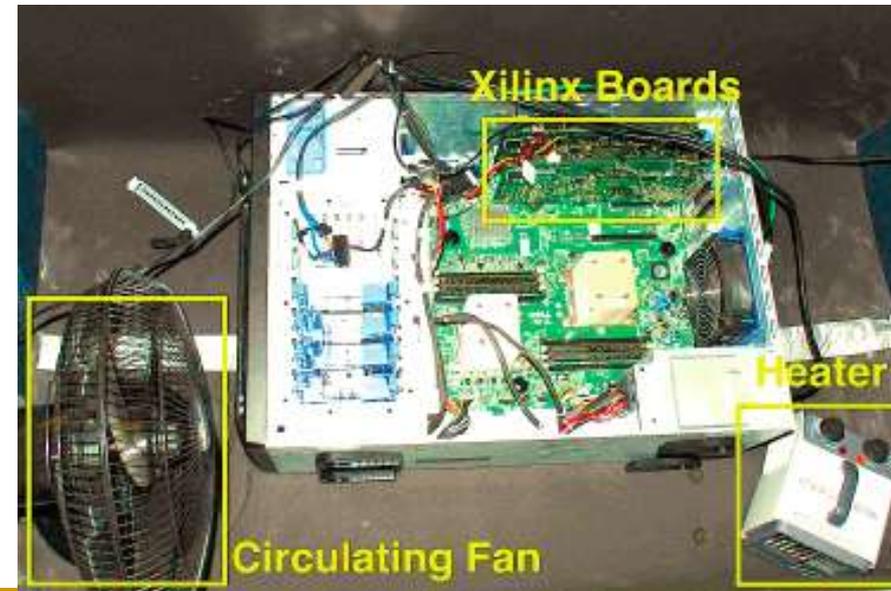
An Experimental Study of Data Retention Behavior in Modern DRAM Devices: Implications for Retention Time Profiling Mechanisms (Liu et al., ISCA 2013)

The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study (Khan et al., SIGMETRICS 2014)

Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors (Kim et al., ISCA 2014)

Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case (Lee et al., HPCA 2015)

AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems (Qureshi et al., DSN 2015)



Experimental Infrastructure (DRAM)

